

Ferroelectricity and ferroelectric materials

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 - Basis of Piezoresponse Force Microscopy
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 - Size effects
 - Ferroelectrics confined at the nanoscale : curled polarization, vortices, skyrmions, hopfions...



NATURE MATERIALS | VOL 19 | FEBRUARY 2020 | 129 |

editorial

A century of ferroelectricity

Ferroelectricity was experimentally discovered one hundred years ago, spurring research on its fundamental properties and potential applications.

1920 – 2020: 100th anniversary

Ferroelectricity was first discovered by Joseph Valasek in **1920** in Rochelle salt
($\text{KNaC}_4\text{H}_4\text{O}_6 \cdot 4\text{H}_2\text{O}$ = potassium sodium tartrate)

Phys. Rev. 15, 537(1920)



Rochelle salt under polarized light, showing evidence of different ferroelectric domains.
Credit: Sciencephotos/Alamy Stock Photo

It is interesting to note that ferroelectricity was discovered well after other phenomena such as pyroelectricity, piezoelectricity...

- **Pyroelectricity** first observed in Tourmaline (Theophrastus ~300 BC, Aepinus 1756)
- **Piezoelectricity** discovered in 1880 by the Curie brothers
- **Pockels effect** (anomalous dielectric response - E.O. effect) in 1893 in Rochelle Salt
- **Ferroelectricity**: term coined by E. Schrödinger in 1912

first discovered by J. Valasek in **1920** in Rochelle salt ($\text{KNaC}_4\text{H}_4\text{O}_6 \cdot 4\text{H}_2\text{O}$ = potassium sodium tartrate)

Phys. Rev. 15, 537(1920); *Phys. Rev.* 17, 475 (1921)

History

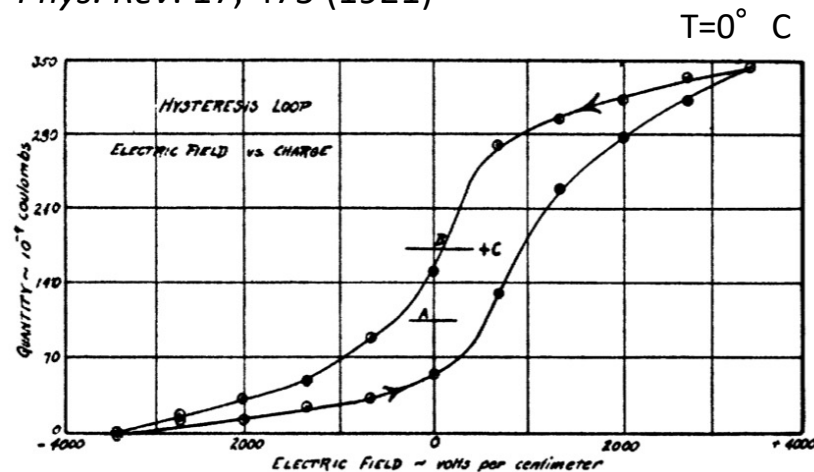
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First discovered by J. Valasek in 1920 in Rochelle salt ($\text{KNaC}_4\text{H}_4\text{O}_6 \cdot 4\text{H}_2\text{O}$ = potassium sodium tartrate tetrahydrate)

Phys. Rev. 15, 537(1920)

Permanent polarization and hysteretic switching are observed

Phys. Rev. 17, 475 (1921)



Joseph Valasek, 1922
University Minnesota

"...is due to a hysteresis in P analogous to magnetic hysteresis. This would suggest a parallelism between the behavior of Rochelle salt as a dielectric and steel, for example, as a ferromagnetic substance."

About Rochelle salt $\text{KNaC}_4\text{H}_4\text{O}_6 \cdot 4\text{H}_2\text{O}$

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Elie Seignette, a pharmacist in La Rochelle, synthesized Rochelle salt (or Seignette salt) in ~1665 (“sel polychreste”)

It was used for its mild medicinal purgative properties

Now:

- food additive (E337)
- antioxidant and pH regulation



How did Seignette prepare this potassium sodium tartrate salt ?

→ It is a natural salt of potassium hydrogen tartrate that is found at the bottom of Bordeaux wine bottles + soda

The first ferroelectric to be discovered (in 1920) is a byproduct of Bordeaux wine !

Ferroelectricity was also called “Seignette electricity”



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What is a ferroelectric?

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What is a ferroelectric?

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- A ferroelectric possesses, along at least one direction, a spontaneous macroscopic dipole moment i.e. non-zero spontaneous electric polarization in the absence of an applied electric field

$$P_S \neq 0 \text{ when } E = 0$$

- The polarization can be switched in the opposite direction by application of an electric field

Switchable polar state: $+\vec{P}_S$ and $-\vec{P}_S$ by application of $\vec{E}_{ext}$

- There is a **phase transition at a temperature T_c above which the phase is paraelectric ($P_s = 0$)**



What is a ferroelectric?

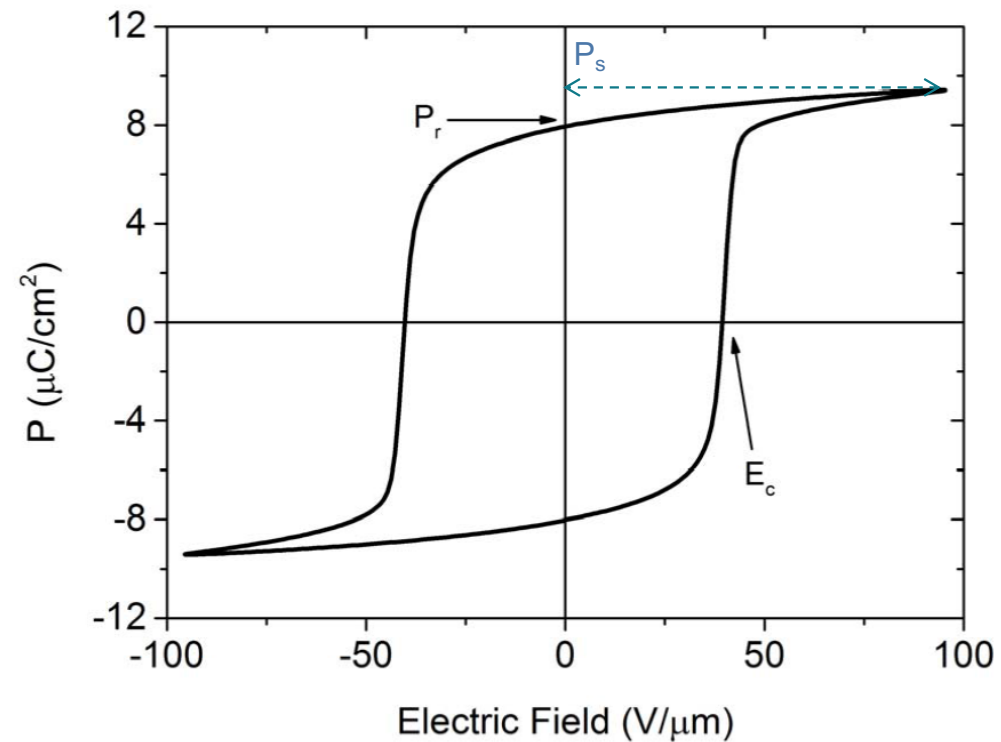
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Ferroelectric hysteresis

P_s : spontaneous polarization

P_r : remanent polarization

E_c : coercive field



Adapted from DOI: [10.1109/TRANSDUCERS.2015.7181322](https://doi.org/10.1109/TRANSDUCERS.2015.7181322)

- Ferroelectric crystal structures are **non-centrosymmetric**. The point group does not possess the *inversion operation*.

Otherwise, by Neumann's principle, P_s would vanish.

Note: Neumann's principle, or principle of symmetry, states that, if a crystal is invariant with respect to certain symmetry operations, any of its physical properties must also be invariant with respect to the same symmetry operations, or otherwise stated, the symmetry operations of any physical property of a crystal must include the symmetry operations of the point group of the crystal.

(https://dictionary.iucr.org/Neumann%27s_principle)

- To support a non-zero P_s , **the point group of the crystal must be polar**

Polar point group: Those point groups for which every symmetry operation leaves more than one common point unmoved are known as the polar point groups (<http://pd.chem.ucl.ac.uk/pdnn/symm2/polar1.htm>)

In a point group, the unmoved points will constitute a line, a plane, or all of space.

- A polar direction is one for which there is no symmetry operation that makes one end of the direction equivalent to the other.

Note: a point group can be non-centrosymmetric but non-polar (e.g. point group 32, the point group of alpha-quartz)

- There are 10 polar point groups, which all of them have a „built in“ unique polar direction. These are the only one that can support a spontaneous polarization.
- All crystals belonging to these 10 crystal classes (corresponding to the 10 polar point) are **pyroelectrics**.
- All ferroelectrics are pyroelectrics
- But all pyroelectrics are not ferroelectrics: when the electric polarization of a pyroelectric crystal can not be switched , it is by definition not a ferroelectric.

Crystal System	Polar Point Groups	
Triclinic	1	
Monoclinic	2	<i>m</i>
Orthorhombic	<i>mm2</i>	
Tetragonal	4	<i>4mm</i>
Trigonal	3	<i>3m</i>
Hexagonal	6	<i>6mm</i>
Cubic	(None)	

<http://pd.chem.ucl.ac.uk/pdnn/symm2/polar1.htm>

Ferroelectric compounds

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- 1920: **Rochelle salt** (synthesized by Elie Seignette)
 - 1933: **Potassium dihydrogen phosphate** (KDP) by Paul Scherrer and Georg Busch
 KH_2PO_4 „Eine neue seignette-elektrische Substanz“ (1935)
- } Fragile and water soluble materials
→ Limited applications

In the early 1940's, intensive search for high dielectric materials

- 1945-1946: **BaTiO₃** first inorganic ferroelectric discovered (first ferroelectric that did not contain H-bonds)
 - (6) A. Von Hippel, R.G. Breckenridge, F.G. Chesley, and L. Tisza, Ind. Eng. Chem. 38 1097 (1946).
 - (7) B. Wul and J.M. Goldman, C.R. Acad. Sci. URSS 51 21 (1946).

Ferroelectrics, 1987, Vol. 74, pp. 267–284

https://ieee-uffc.org/wp-content/uploads/2016/11/cross_newnham.pdf

Ferroelectric compounds

Table V. Period of Proliferation

1949 to 1960	20 Perovskite compounds	WO ₃ to Pb ₃ MgNb ₂ O ₉	Matthias (Refs. 43–45) Smolenskii (Refs. 46–48)
1949	LiNbO ₃ family		Matthias (Ref. 49)
1951	LiTiC ₄ H ₄ O ₆ ·H ₂ O		Matthias (Ref. 50)
1952	Cd ₂ Nb ₂ O ₇ pyrochlore family		Cook, Jaffe (Ref. 51)
1953	PbNb ₂ O ₆ tungsten bronze		Goodman (Ref. 52)
1955	G.A.S.H. family		Holden (Ref. 53)
1956	Sn(NH ₂) ₂ thiourea		Soloman (Ref. 54)
1956	TGS family		Matthias (Ref. 55)
1956	(NH ₄) ₂ SO ₄ family		Matthias (Ref. 56)
1956	Colemanite		Goldsmith (Ref. 57)
1956	(NH ₄) ₂ Cd ₂ (SO ₄) ₃ family		Jona, Pepinsky (Ref. 58)
1957	Alums		Jona (Ref. 59)
1957	Dicalcium strontium propionate		Matthias (Ref. 60)
1957	Boracite family		Le Corre (Ref. 61)
1958	(NH ₄)HSO ₄		Pepinsky (Ref. 62)
1958	NaNO ₂ family		Sawada (Ref. 63)
1958	KNO ₃		Sawada (Ref. 64)
1959	LiH ₃ (SeO ₃) ₂ family		Pepinsky (Ref. 65)
1959	(NH ₄)NaSO ₄		Pepinsky (Ref. 66)
1960	N(CH ₃) ₄ HgCl ₃ family		Fatuzzo, Merz (Ref. 67)
1960	K ₄ Fe(CN) ₆ ·3H ₂ O family		Waku (Ref. 68)
1962	SbSI family		Fatuzzo (Ref. 69)
1963	YMnO ₃ family		Bertaut (Ref. 70)

PbTiO₃
Pb_{1-x}Zr_xTiO₃ (PZT)

2008: HfO₂ compounds – Breakthrough discovery for integration

https://ieee-uffc.org/wp-content/uploads/2016/11/cross_newnham.pdf

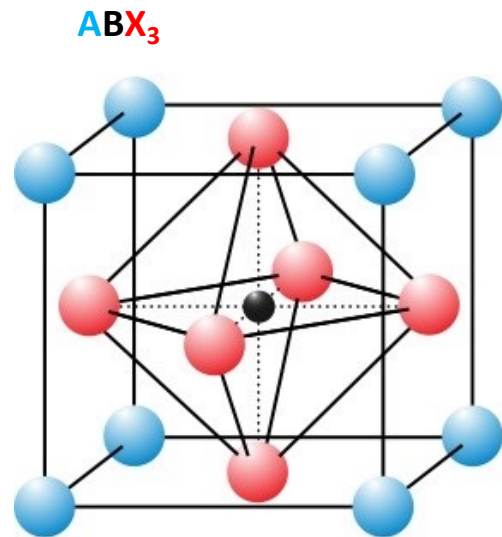
Perovskite ferroelectrics

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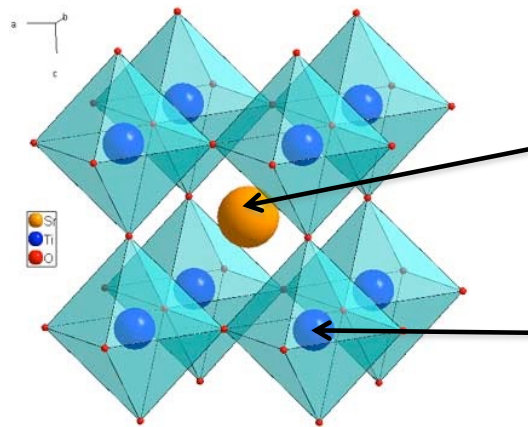
Perovskite structure ABX_3 : cubic structure

X=Oxygen **ABO_3** (e.g. $CaTiO_3$)

Space group $Pm3m$



One formula unit/unit cell



B site atom inside oxygen octahedra

Transition metal oxide (at RT) such as Ti, Mn, Cu
(polarization, magnetic character...)

A site atom in-between oxygen octahedra

Alkali metal, alkaline earth metal, rare earth

3D oxygen octahedra network sharing corners

<https://www.princeton.edu/~cavalab/tutorials/public/structures/perovskites.html>

Perovskite ferroelectrics

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Perovskite structure

The original perovskite compound is **CaTiO₃**.

However, it was later found that CaTiO₃ is not cubic but orthorhombic!



Discovered by:



Gustav Rose
1798 - 1873

Named after:



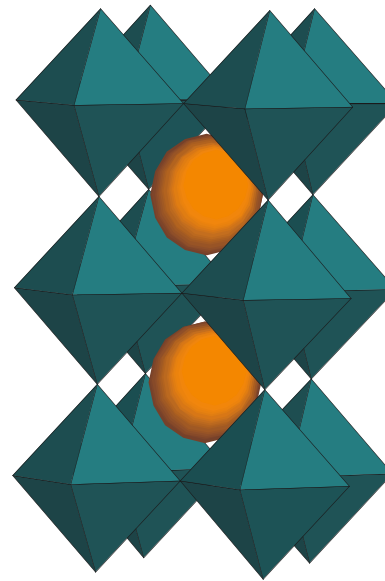
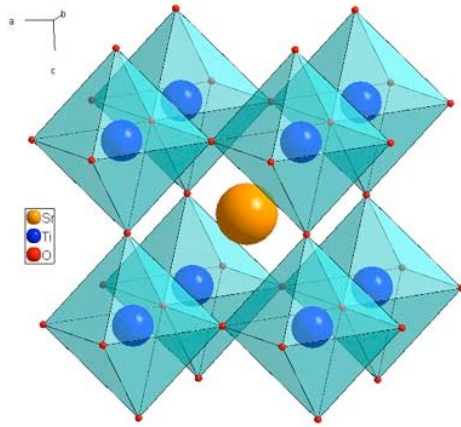
Lev Perovski
1792 - 1856

In CaTiO₃, Ca is slightly too small for 12 coordination with O . In order to reduce the size of the cavity, **the octahedra rotates and the unit cell becomes orthorhombic**

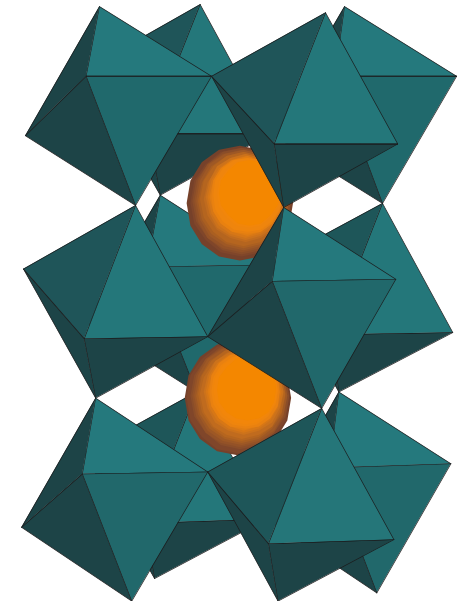
Perovskite ferroelectrics

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Perovskite structure



Cubic unit cell



Orthorhombic unit cell

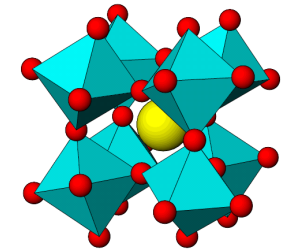
Perovskite ferroelectrics

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Perovskite structure ABO_3

A large variety of possible distortions of the cubic cell (which becomes “pseudo-cubic”)

- Possible tilt of the octahedra, depending on the size of the cation A
- Possible Jahn-Teller distortion
- Possible B cation displacement (ferroelectricity)



Playing with chemical substitution for a given compound often give rise to multiple different structures and, in turn, to different physical properties

Perovskite structure compounds

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Perovskites exhibit a large variety of properties, among them are:

Dielectric

Piezoelectric

Pyroelectric

Ferroelectric

Semiconductive

Superconductive

Magnetic

Colossal magnetoresistive

Multiferroic

Charge ordering

Thermoelectrics

Photoelectric

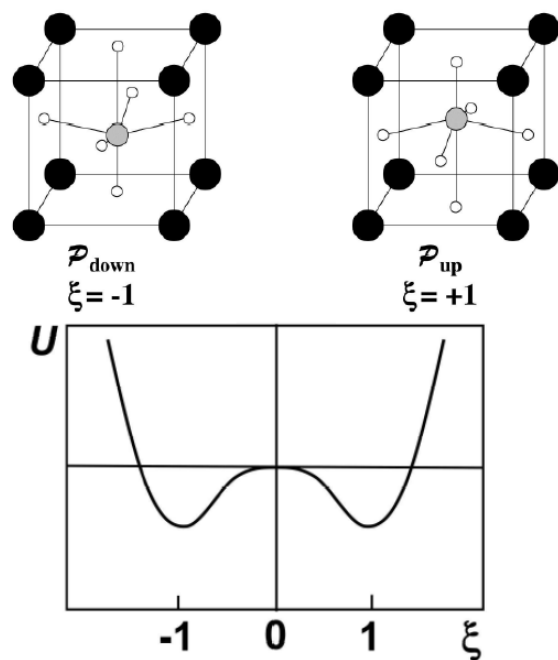
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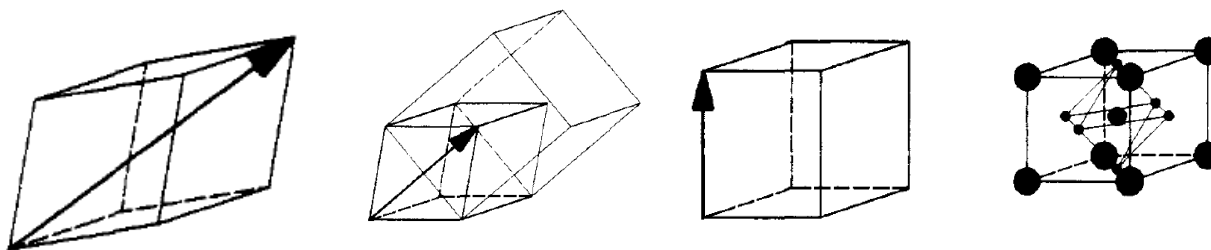
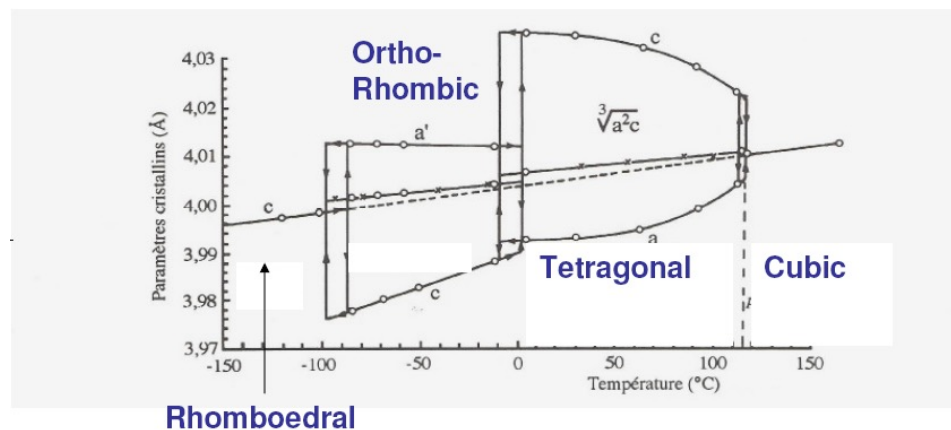
Perovskite ferroelectrics: BaTiO₃

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$T_c \sim 120^\circ\text{C}$

Kay and Vousden, Phil. Mag. 40, 1019 (1943)



G.H. Kwei et al., J. Phys. Chem. 97, 2368 (1993)

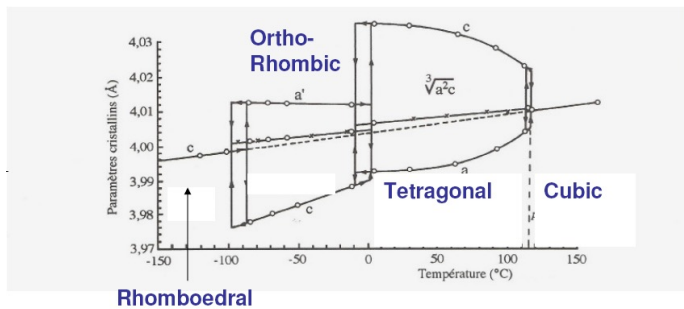
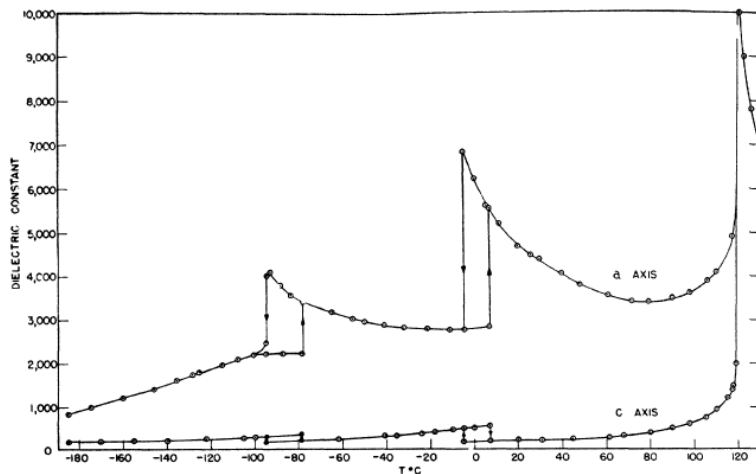


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Perovskite ferroelectrics: BaTiO₃

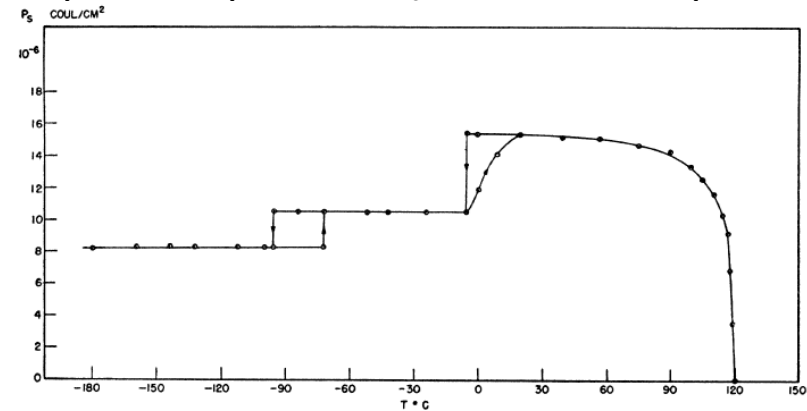
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Dielectric constants as a function of temperature



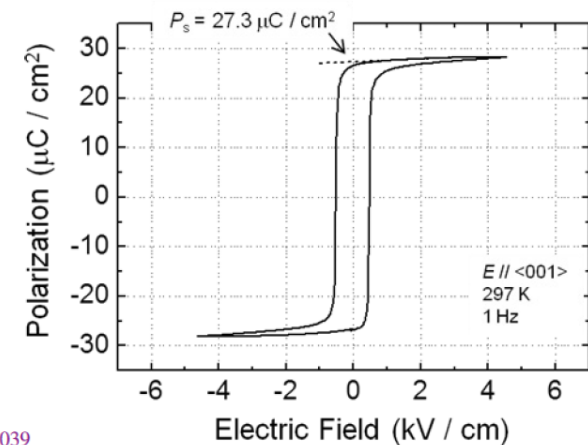
Kay and Vousden, Phil. Mag. 40, 1019 (1943)

Spontaneous polarization P_s as a function of temperature



W.J. Merz, Phys. Rev. 76, 1221 (1949)

$$P_s \sim 26-27 \mu\text{C}/\text{cm}^2$$



R. Imura *et al.*, [10.1142/S2010135X14500039](https://doi.org/10.1142/S2010135X14500039)

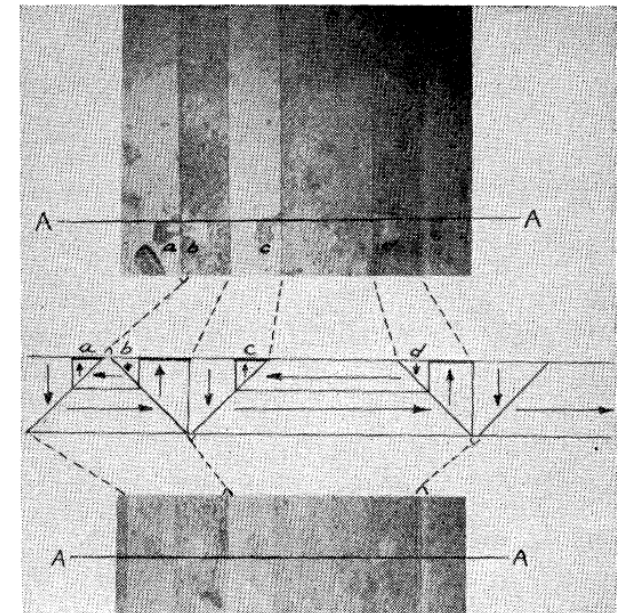
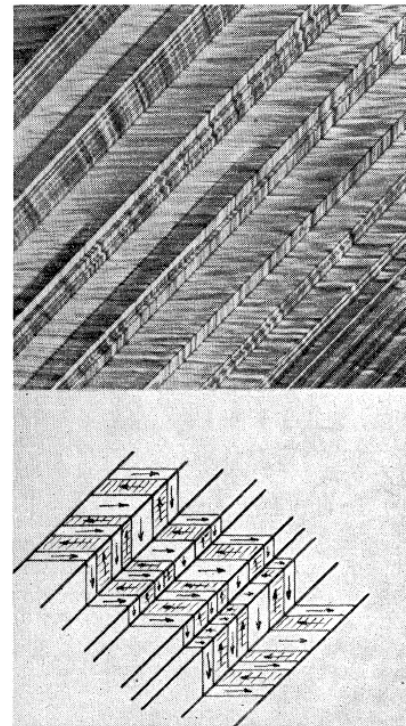
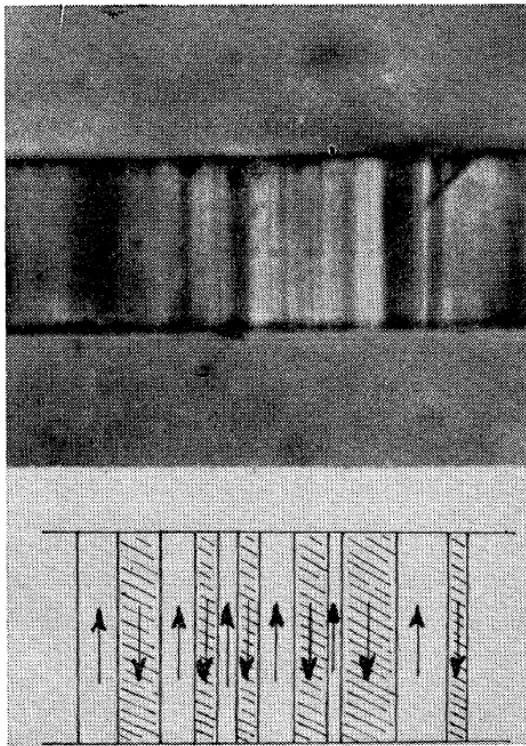


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Perovskite ferroelectrics: BaTiO₃

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Domains imaged on etched BaTiO₃ single crystals



J.A. Hooton and W.J. Merz, Phys. Rev. 98, 409 (1955)



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Perovskite ferroelectrics

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	T_c (K)	P_s ($\mu\text{C}/\text{cm}^2$)
BaTiO₃	393	27
PbTiO₃	768	60 [1]
KNbO₃	708 [2]	30
LaTiO₃	1773 [3]	5 [3, 4]
LiNbO₃	1476 [5]	78 [5]
BiFeO₃	1083 [6]	6.1 [7]

[1] Nishino, Ryutaro, et al. "Evolution of ferroelectricity in ultrathin PbTiO₃ films as revealed by electric double layer gating." *Scientific reports* 10.1 (2020): 1-8.

[2] Rani, Jyoti, et al. "Mo⁶⁺ modified (K_{0.5}Na_{0.5})NbO₃ lead free ceramics: structural, electrical and optical properties." *Journal of Materials Science & Technology* 30.5 (2014): 459-465.

[3] Herrera, G., J. Jiménez-Mier, and E. Chavira. "Layered-structural monoclinic–orthorhombic perovskite La₂Ti₂O₇ to orthorhombic LaTiO₃ phase transition and their microstructure characterization." *Materials characterization* 89 (2014): 13-22.

[4] Nanamatsu, S., et al. "A new ferroelectric: La₂Ti₂O₇." *Ferroelectrics* 8.1 (1974): 511-513.

[5] Ganesamoorthy, S., et al. "A comparative study on the domain switching characteristics of near stoichiometric lithium niobate and lithium tantalate single crystals." *Materials Science and Engineering: B* 120.1-3 (2005): 125-129.

[6] Shvartsman, V. V., et al. "Large bulk polarization and regular domain structure in ceramic BiFeO₃." *Applied physics letters* 90.17 (2007): 172115.

[7] Kadomtseva, A. M., et al. "Phase transitions in multiferroic BiFeO₃ crystals, thin-layers, and ceramics: enduring potential for a single phase, room-temperature magnetoelectric 'holy grail'." *Phase Transitions* 79.12 (2006): 1019-1042.

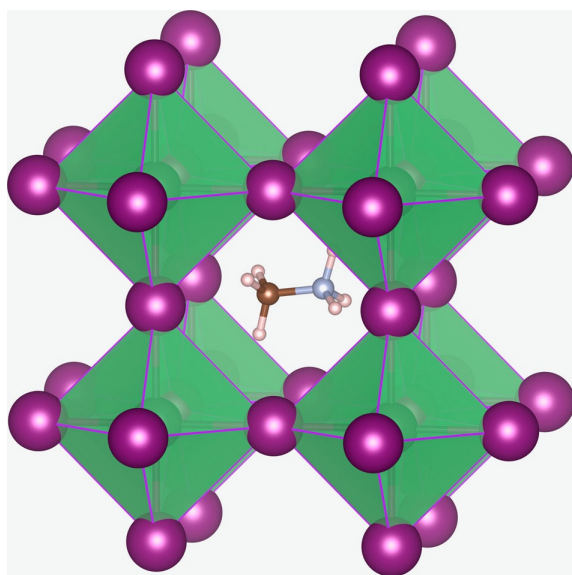


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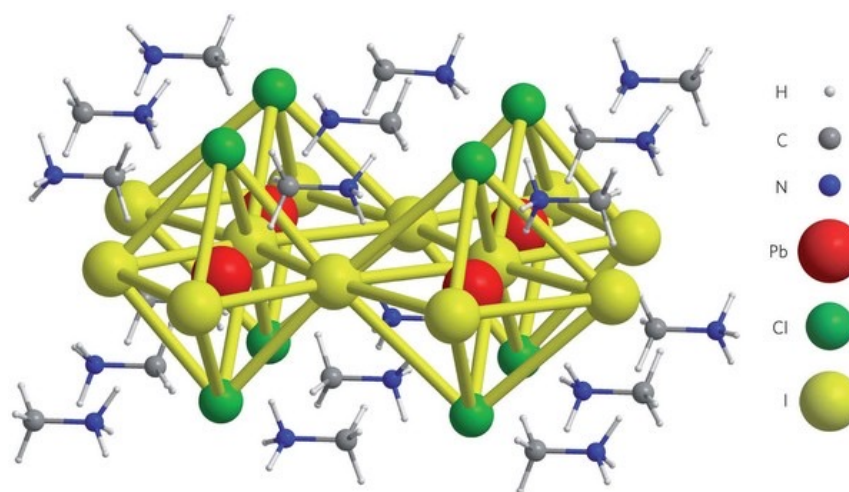
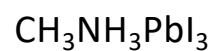
Perovskite ferroelectrics

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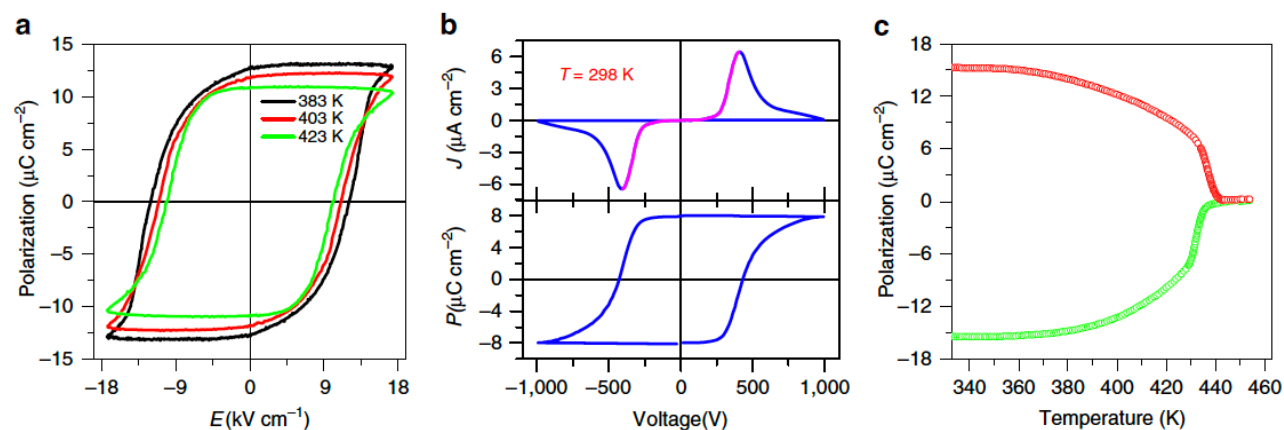
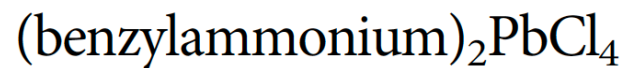
Organic / Inorganic Perovskite



Photovoltaics



Hybrid perovskite ferroelectrics



$P_s = 13 \mu\text{C}/\text{cm}^2$ and Curie temperature $T_c = 438\text{K}$

W.Q. Liao et al, Nat. Comm. 6, 7338 (2015)

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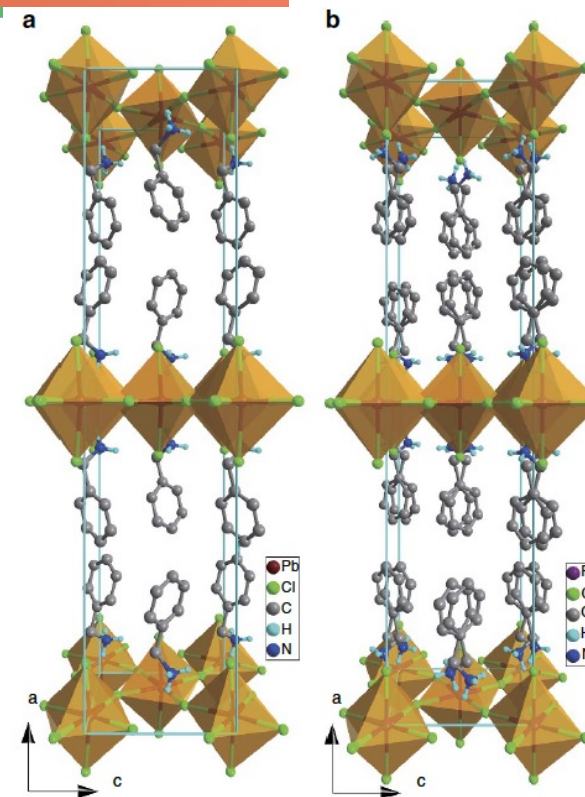


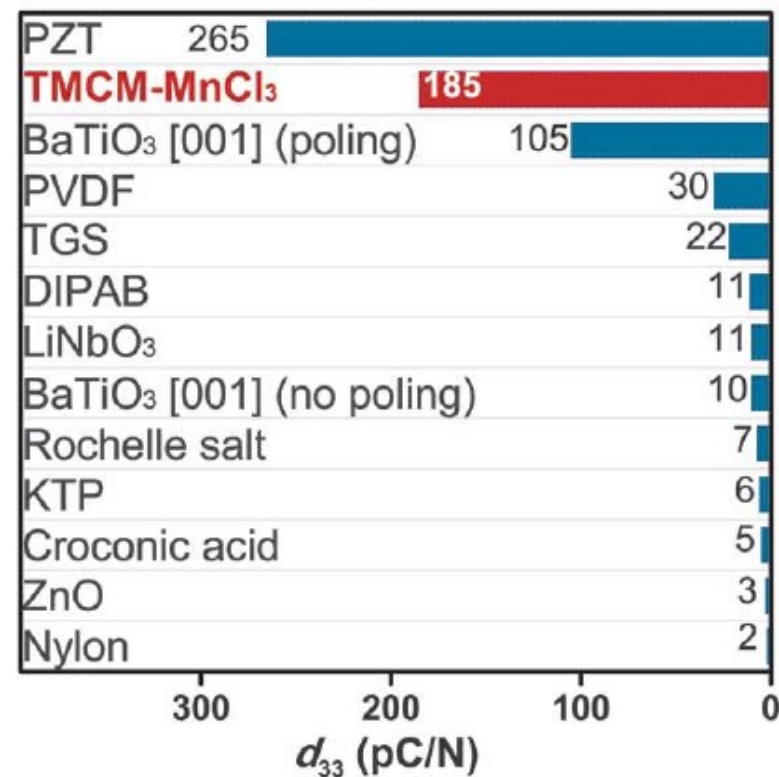
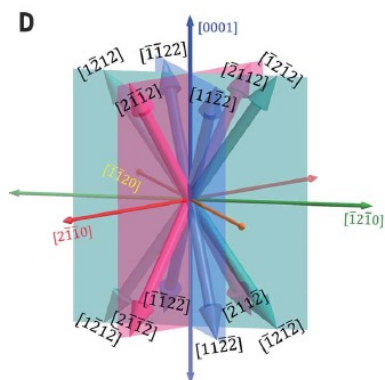
Figure 1 | Comparison of the crystal structures between the paraelectric and ferroelectric phases. (a) Perspective view of **1** at 293 K. (b) Perspective view of **1** at 453 K. Hydrogen atoms bonded to the C atoms were omitted for clarity.

PIEZOELECTRICS

An organic-inorganic perovskite ferroelectric with large piezoelectric response

Yu-Meng You,^{1*} Wei-Qian Qionghua Zhou,³ Xianghong Zheming Wang,⁴ Song Gao,⁵ Kunlun Yang,⁶ Jun-Ming Liu,⁶ Jiangyu Li,^{6,7*} Yanfa Yan,^{2*} Ren-Gen Xiong^{1*}

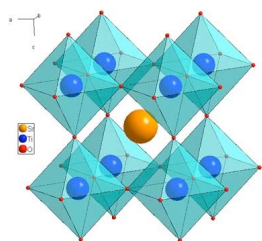
Science **357**, 306–309 (2017)¹



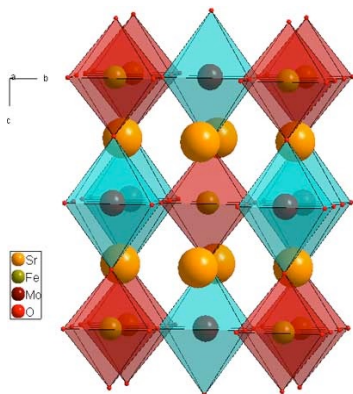
Perovskite ferroelectrics

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Perovskite (ABO_3 : $CaTiO_3$)



Double Perovskite



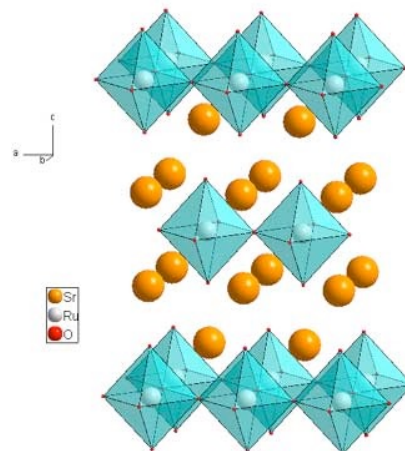
Ex: $CaMnTi_2O_6$

Layered Perovskites:

Ruddlesden-Popper phases $A_{(n+1)}B_nO_{(3n+1)}$

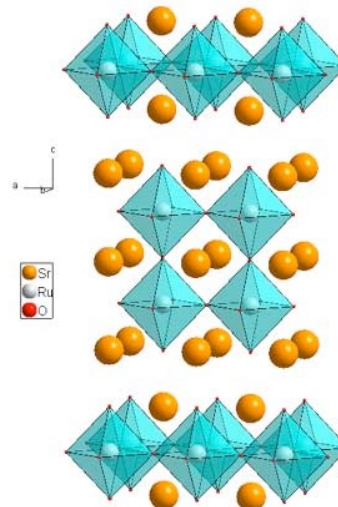
$n = 1$

Sr_2RuO_4



$n = 2$

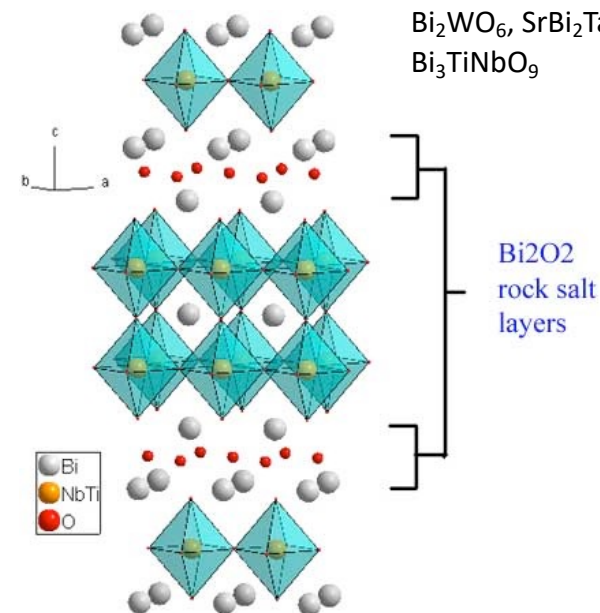
$Sr_3Ru_2O_7$



Ex: $Ca_3Ti_2O_7$, $Li_2CaTa_2O_7$ (hybrid improper ferroelectrics)
See - N.A. Benedek, C.J. Fennie, PRL 106, 107204 (2011))

Aurivillius phases $(Bi_2O_2)(A_{n-1}B_nO_{3n+1})$

Bi_2WO_6 , $SrBi_2Ta_2O_9$
 Bi_3TiNbO_9



Ex: $PbBi_2Nb_2O_9$, $SrBi_2Ta_2O_9$, $SrBi_2Nb_2O_9$

Hexagonal manganites

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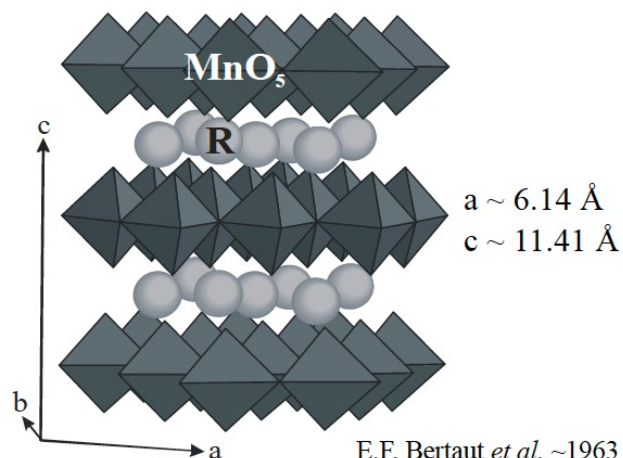
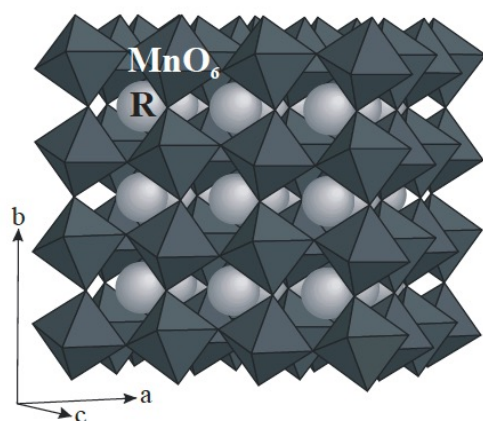
RMnO₃ : "perovskite structure" (Pnma)

RMnO₃ : hexagonal structure

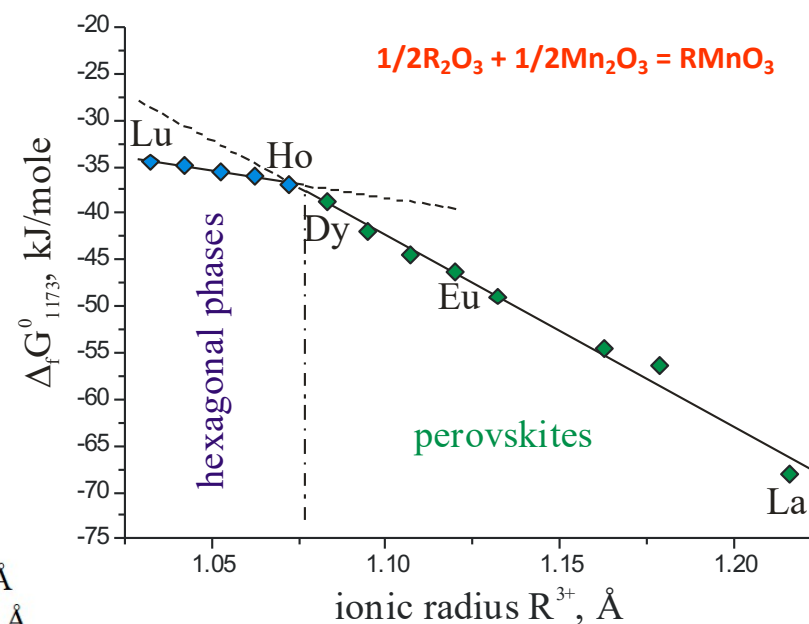
Ce	Pr	Nd	Pm	Sm	Eu	Gd	Tb	Dy	Ho	Er	Tm	Yb	Lu
La									Y				

perovskite

hexagonal



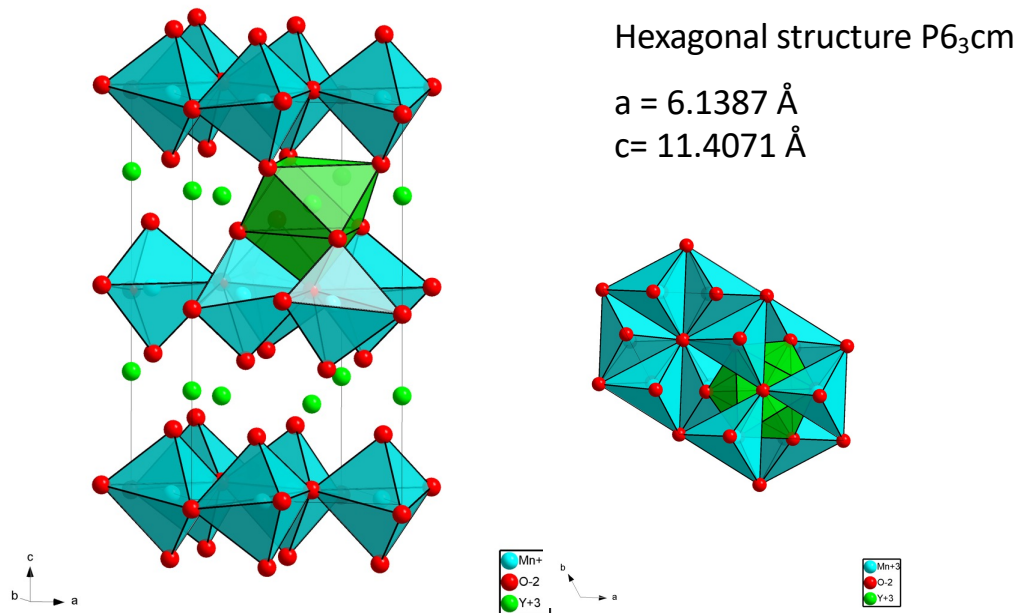
E.F. Bertaut *et al.* ~1963



T. Atsumi, T. Oghushi, N. Kamegashira
J. of Alloys and Compounds 238 (1996) 35

Hexagonal manganites

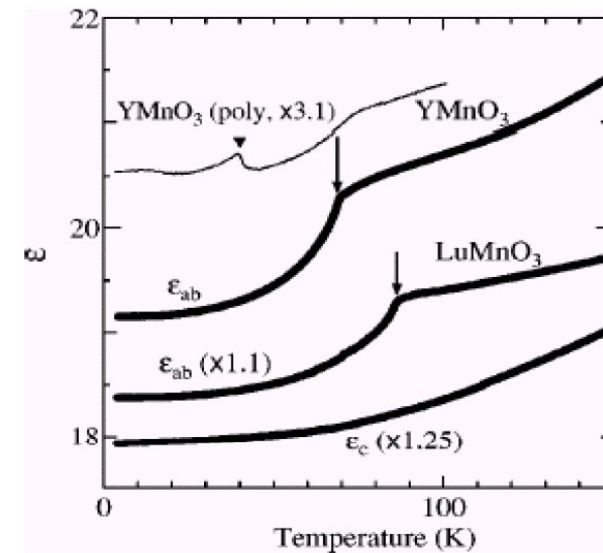
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- **Ferroelectric** ($T_c \sim 800 - 1000 \text{ K}$)

polarisation **along c axis** with $P_s \sim 5.5 \mu\text{C}/\text{cm}^2$
 improper ferroelectric

- **Antiferromagnetic** ($T_N \sim 70 - 100 \text{ K}$)

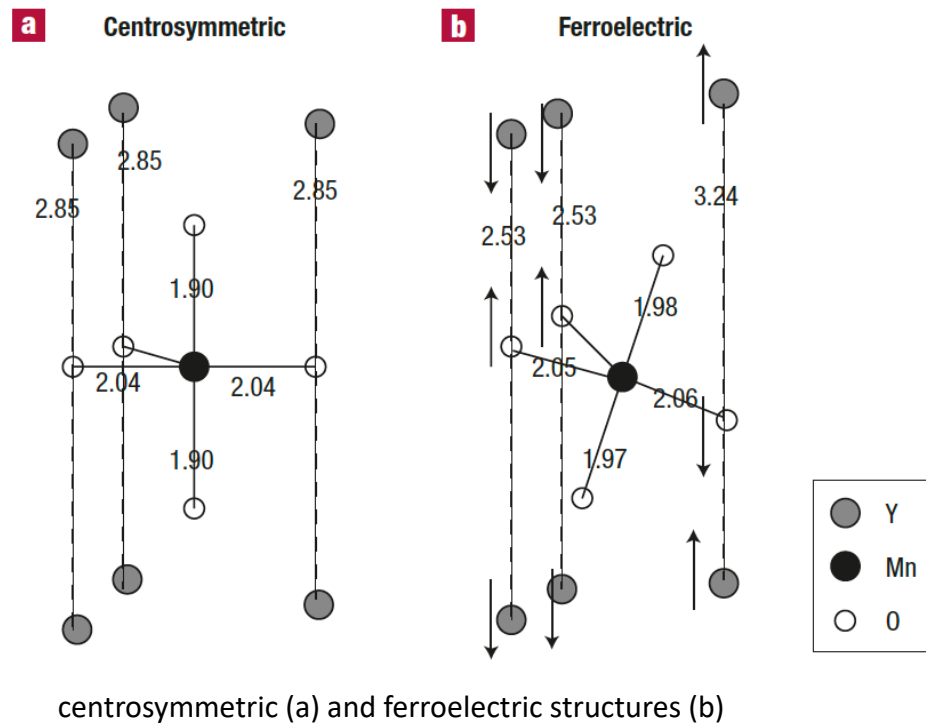


Katsufuji et al., *PRB* 64, 104419 (2001)

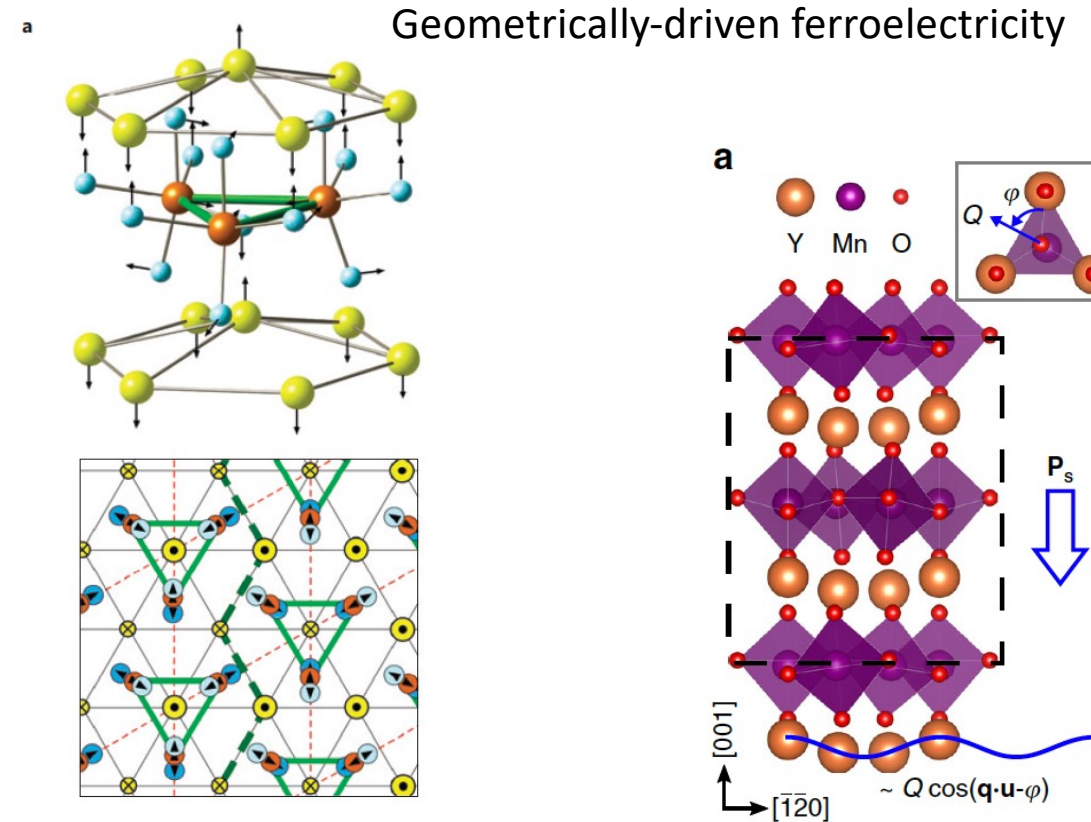
Huang et al., *PRB* 56, 2623 (1997)

Hexagonal manganites

FIXIT



Van A., Bas B., et al., *Nature materials* 3, 164 (2004).



T. Choi et al., *Nat. Mater.* 9, 253 (2010)

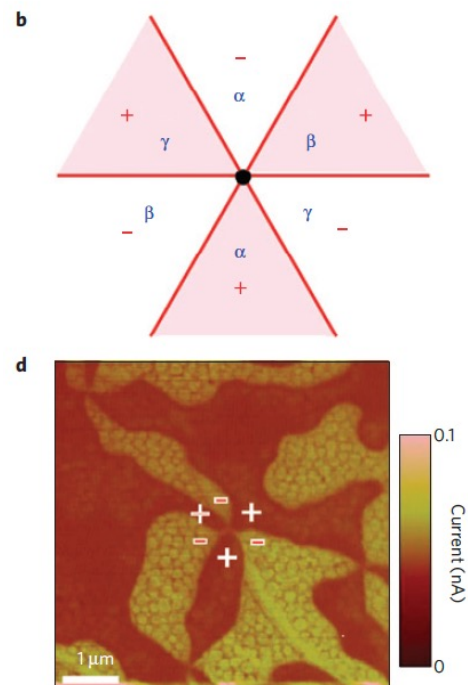


Hexagonal manganites

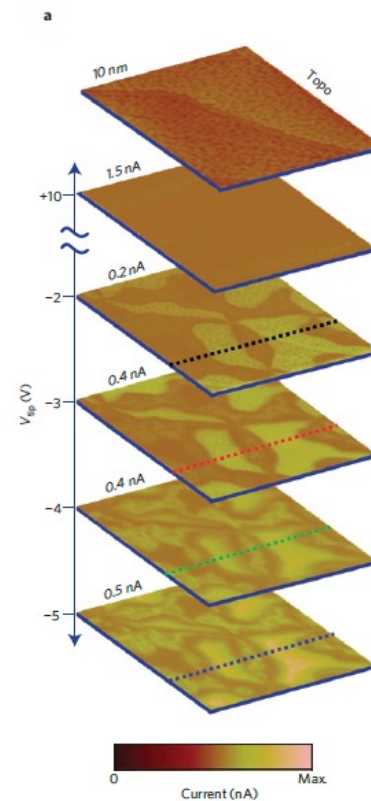
FIXIT

Peculiar domain configuration

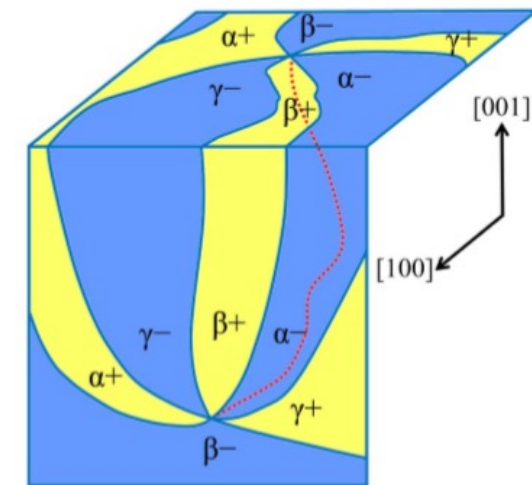
6 domains with vortex line at center



Change of domain configuration with applied voltage



Vortex-antivortex structure (V-AV)



T. Choi et al., Nat. Mater. 9, 253 (2010)

Zhang, Qinghua, et al., *Scientific reports* 3 (2013): 2741

Hexagonal rare earth manganites

FIXIT

Material	Space group	Crystal structure	Magnetic ordering	Electrical ordering	T_N or T_M (K)	T_C (K)
YMnO ₃	$P6_3cm$	Hexagonal	AFM	FE	70–80	914
YbMnO ₃	$P6_3cm$	Hexagonal	AFM	FE	87	983–993
HoMnO ₃	$P6_3cm$	Hexagonal	AFM	FE	72	875
TmMnO ₃	$P6_3cm$	Hexagonal	AFM	FE	~49 86	>573

Critical Reviews in Solid State and Materials Sciences 34, 179 (2009)



Improper ferroelectrics in magnetic systems

FIXIT

Type-II multiferroics ferroelectricity occurs only in the magnetically ordered state: **ferroelectricity sets in at the same temperature as a certain type of magnetic ordering and is driven by it.**

- TbMnO_3 (perovskite structure)
- $\text{Ni}_3\text{V}_2\text{O}_8$
- MnWO_4
- $\text{Ca}_3\text{CoMnO}_6$
- RMn_2O_5 , where R is a rare earth ion
- ...

J. Phys.: Condens. Matter **20** (2008) 434217 (12pp)

[doi:10.1088/0953-898](https://doi.org/10.1088/0953-898)

REVIEW ARTICLE

Multiferroicity due to charge ordering

Jeroen van den Brink^{1,2} and Daniel I Khomskii³

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² Institute for Molecules and Materials, Radboud Universiteit Nijmegen, PO Box 9010, 6500 GL Nijmegen, The Netherlands

³ II Physikalisches Institut, Universität zu Köln, 50937 Köln, Germany



Many more...

FIXIT

Material	Space group	Crystal structure	Magnetic ordering	Electrical ordering	T_N or T_M (K)	T_C (K)
YMnO ₃	<i>P6₃cm</i>	Hexagonal	AFM	FE	70–80	914
YbMnO ₃	<i>P6₃cm</i>	Hexagonal	AFM	FE	87	983–993
HoMnO ₃	<i>P6₃cm</i>	Hexagonal	AFM	FE	72	875
					~49	
TmMnO ₃	<i>P6₃cm</i>	Hexagonal	AFM	FE	86	>573
						348
TbMnO ₃	<i>Pbnm</i>	Orthorombic	AFM	FE	41	28
DyMnO ₃	<i>Pbnm</i>	Orthorombic	AFM	FE	~40	~19
LaMnO ₃	<i>Pbnm</i>	Orthorombic	AFM		140	
BiMnO ₃	<i>C2</i>	Monoclinic	FM	AFE	105	723
BiFeO ₃	<i>R3c</i>	Rhombohedral	AFM	FE	643	1,100
BiCrO ₃	<i>C2/c</i>	Monoclinic	AFM	AFE	109	420
HoMn ₂ O ₅	<i>Pbam</i>	Orthorombic	AFM	FE	~45	~39
ErMn ₂ O ₅	<i>Pbam</i>	Orthorombic	AFM	FE	~45	~39
TmMn ₂ O ₅	<i>Pbam</i>	Orthorombic	AFM	FE	~45	~36
TbMn ₂ O ₅	<i>Pbam</i>	Orthorombic	AFM	FE	~45	~38
DyMn ₂ O ₅	<i>Pbam</i>	Orthorombic	AFM	FE	~42	~38
YMn ₂ O ₅	<i>Pbam</i>	Orthorombic	AFM	FE	~45	~41

N. Izyskaya et al., Critical Reviews in Solid State and Materials Sciences 34, 179 (2009)



HfO₂-based compounds

FIXIT

Ferroelectricity in HfO₂ discovered in 2008 (first published in 2011)

APPLIED PHYSICS LETTERS **99**, 102903 (2011)

Ferroelectricity in hafnium oxide thin films

T. S. Böске,^{1,a),b)} J. Müller,² D. Bräuhäus,³ U. Schröder,^{4,b)} and U. Böttger³

¹Löberwallgraben 2, 99096 Erfurt, Germany

²Fraunhofer CNT, 01099 Dresden, Germany

³RWTH Aachen, Institut für Werkstoffe der Elektrotechnik, 52062 Aachen, Germany

⁴NamLab gGmbH, 01187 Dresden, Germany

APPLIED PHYSICS LETTERS **99**, 112904 (2011)

Phase transitions in ferroelectric silicon doped hafnium oxide

T. S. Böске,^{1,2,a),b)} St. Teichert,^{3,b)} D. Bräuhäus,⁴ J. Müller,⁵ U. Schröder,^{2,b)} U. Böttger,⁴ and T. Mikolajick^{2,6}

¹Löberwallgraben 2, 99096 Erfurt, Germany

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³UAS Jena, Department of SciTec, 07745 Jena, Germany

⁴RWTH Aachen, Institut für Werkstoffe der Elektrotechnik, 52062 Aachen, Germany

⁵Fraunhofer Center Nanoelectronic Technologies (CNT), 01099 Dresden, Germany

⁶Department of Nanoelectronic Materials, University of Technology Dresden, 01062 Dresden, Germany

APPLIED PHYSICS LETTERS **99**, 112901 (2011)

Ferroelectric Zr_{0.5}Hf_{0.5}O₂ thin films for nonvolatile memory applications

J. Müller,^{1,a)} T. S. Böске,^{2,b)} D. Bräuhäus,³ U. Schröder,^{4,b)} U. Böttger,³ J. Sundqvist,^{1,b)}

P. Kücher,¹ T. Mikolajick,^{4,5} and L. Frey⁶

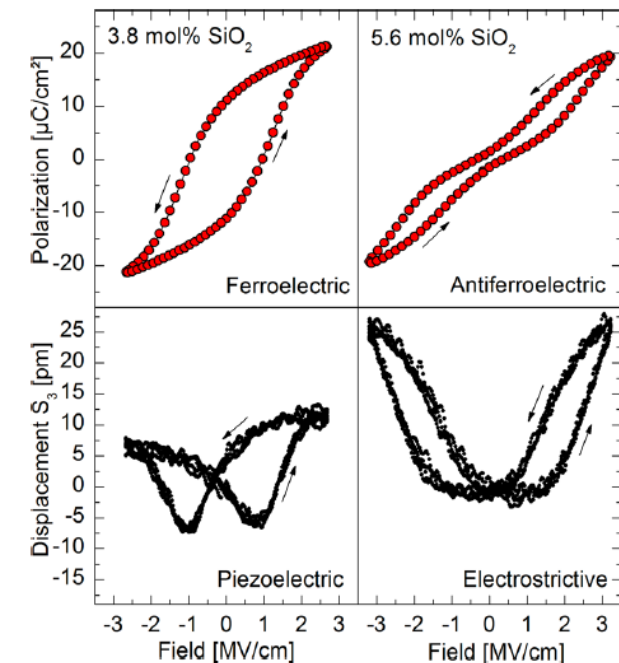
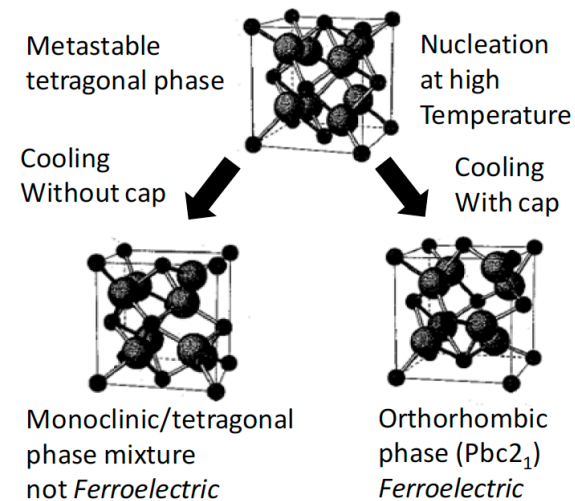
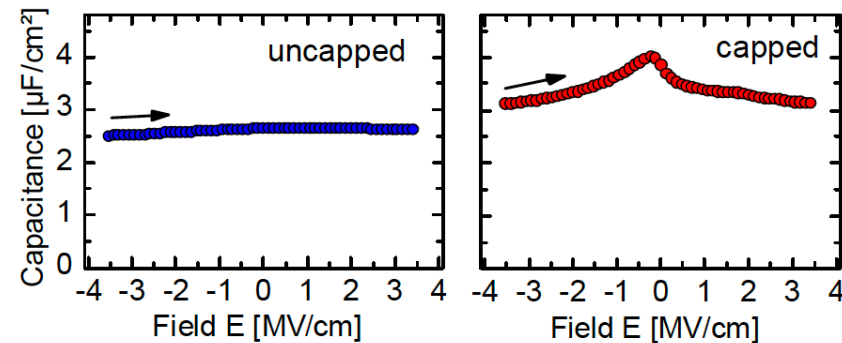
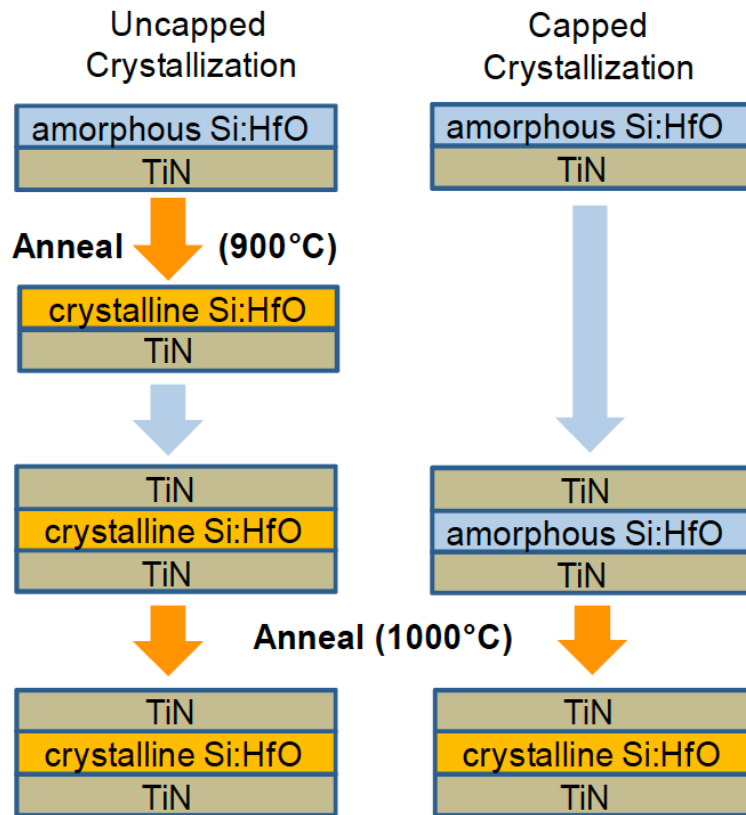


FIG. 3. (Color online) Polarization (top row) and piezoelectric displacement (bottom row) measurement of MIM capacitor samples with ferroelectric (left column) and antiferroelectric (right column) Si:HfO₂ insulators.

HfO₂-based compounds

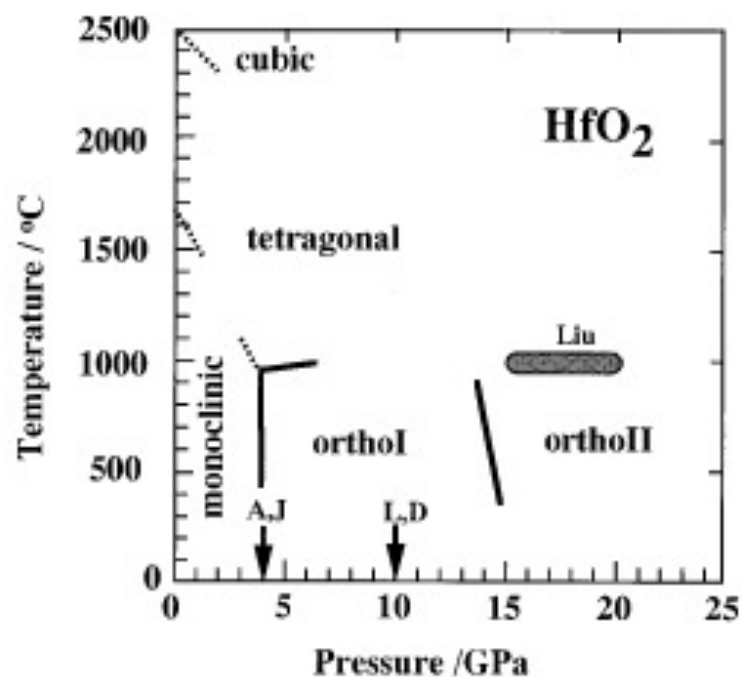
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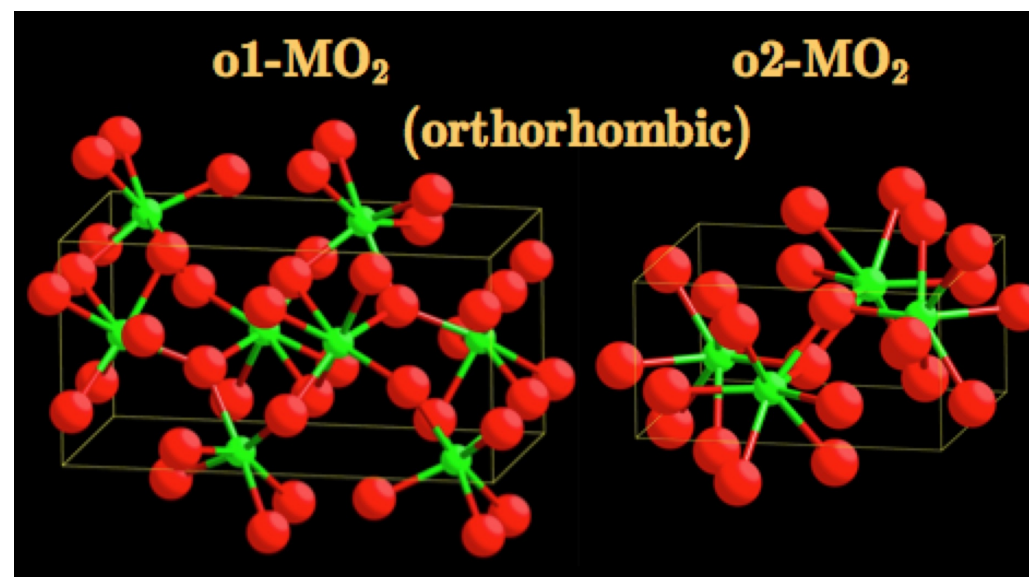
T. S. Böске et al., IEDM (2011)

HfO₂-based compounds

FIXIT



O. Ohtaka *et al.*, J. Am. Cer. Soc. 84(6), 1369 (2001)



From G.M. Rignanese, Louvain

Orthorhombic

Space group Pbca
Hf 7-fold coordinated
O_I 3-fold coordinated
O_{II} 4-fold coordinated

Orthorhombic

Space group Pnam (cotunnite)
Hf 9-fold coordinated
O_I 4-fold coordinated
O_{II} 5-fold coordinated

HfO₂-based compounds

FIXIT

Non-centrosymmetric Pca2₁ orthorhombic III phase is ferroelectric

Stress/strain play a major role in the stabilization of this polar structure of HfO₂.

The polar phase has been stabilized for a large variety of solid solution combination („dopant“) HfO₂ (Zr, Si, Al, Gd, Y, Sr, La...)

HfO₂(ZrO₂) system is the most studied one, with a composition close to Hf_{0.5}Zr_{0.5}O₂

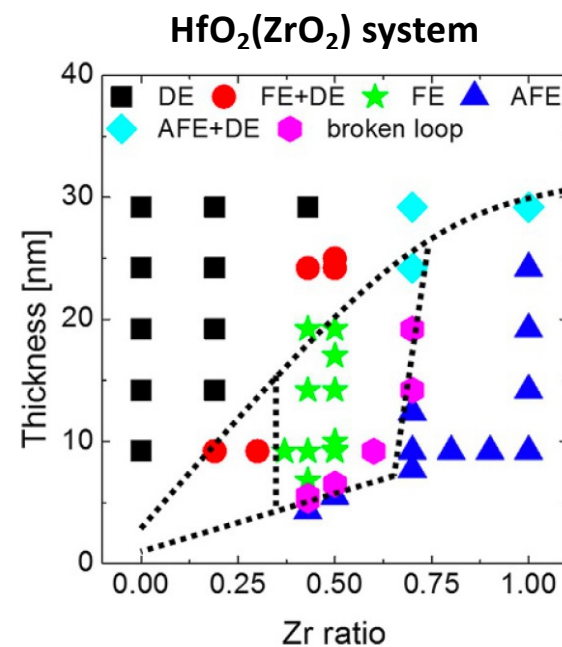
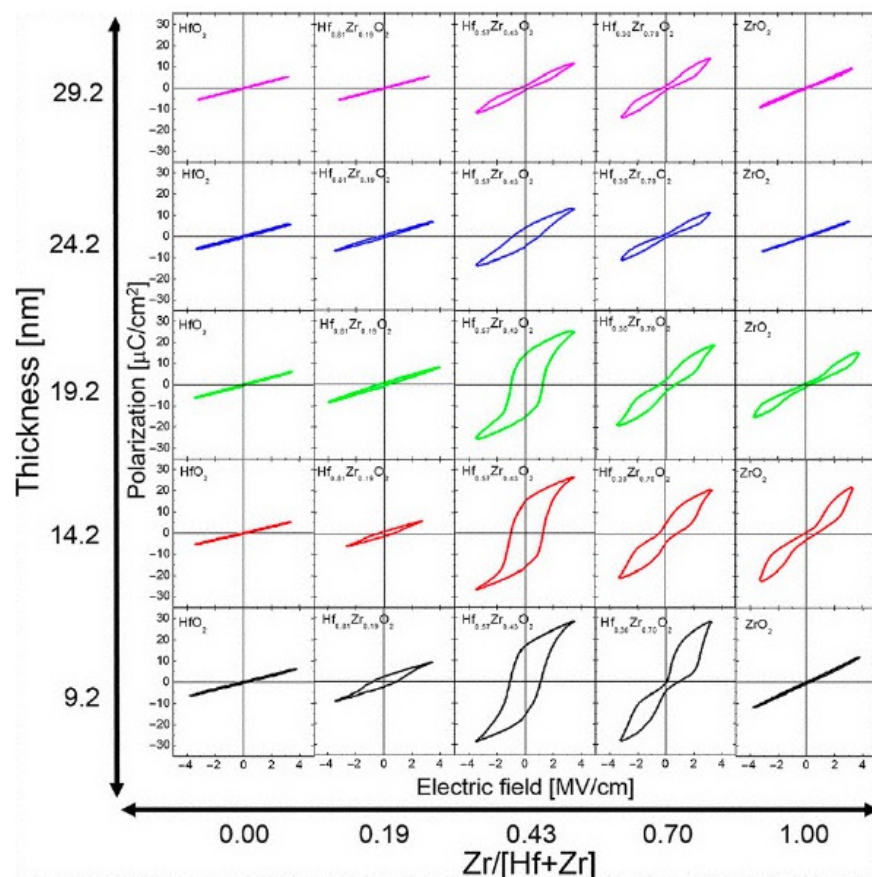
E.H. Kisi, J. Am. Ceram. Soc., 81 [3] 741–45 (1998)



HfO₂-based compounds

FIXIT

Dependence of ferroelectricity on composition and thickness



Narrow range of optimized properties

HfO₂-based compounds

FIXIT

Non-centrosymmetric Pca2₁ orthorhombic III phase is ferroelectric

Stress/strain play a major role in the stabilization of this polar structure of HfO₂.

The polar phase has been stabilized for a large variety of solid solution combination („dopant“) HfO₂ (Zr, Si, Al, Gd, Y, Sr, La...)

HfO₂(ZrO₂) system is the most studied one, with a composition close to Hf_{0.5}Zr_{0.5}O₂

A major difference with previously described compounds: these polycrystalline films require „wake-up“ to reach full polarization

Fully CMOS compatible, no need for epitaxial films (films are polycrystalline with ~10-20 nm size grains)

E.H. Kisi, J. Am. Ceram. Soc., 81 [3] 741–45 (1998)



HfO₂-based compounds

FIXIT

- Fully CMOS compatible

	SBT FeFET	PZT FeFET	This work
Gate Stack	Pt/SBT/HfAlO	Al/PZT/Dy ₂ O ₃	TiN/HfSiO/SiO ₂
FE/IF Thickness	400 nm/10 nm	250 nm/20 nm	8.5 nm/1.2 nm (5.5 nm/1.2 nm)
Thermal budget	800°C	700°C	1000°C
Memory Window	400 mV	800 mV	1000 mV
10y Memory Window	250 mV	?	650 mV
Programming Voltage	-6V/+6V	-8V/8V	-3V/4V

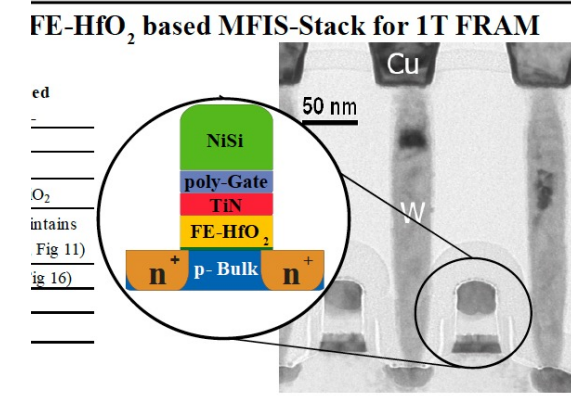
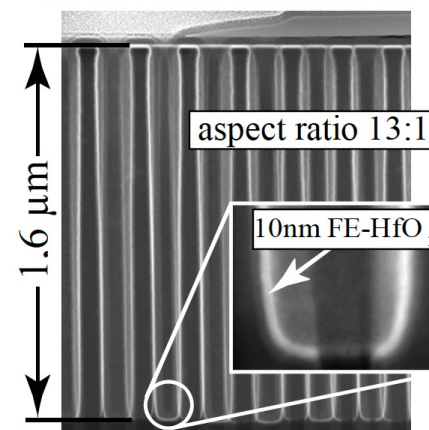
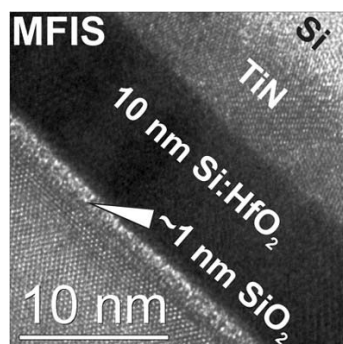


Figure 12 Comparison of FE-HfSiO based field effect transistors to, in our knowledge, the best previously published devices based on conventional ferroelectrics SBT and PZT [3].



Ferroelectric Hafnium Oxide: A CMOS-compatible and highly scalable approach to future ferroelectric memories
 J. Müller, T.S. Böske^a, S. Müller^a, E. Yurchuk^a, P. Polakowski, J. Paul, D. Martin^a, T. Schenk^a, K. Khullar^a, A. Kersch^d, W. Weinreich, S. Riedel, K. Seidel, A. Kumar^f, T.M. Arruda^f, S.V. Kalinin^f, T. Schlösser^c, R. Boschke^c, R. van Bentum^c, U. Schröder^a, T. Mikolajick^{a,b}
 Fraunhofer IPMS-CNT, ^aNaMLab gGmbH, ^bIHM TU-Dresden, ^cGLOBALFOUNDRIES, Dresden, Germany, ^dFH-München, München, Germany, ^eBosch Solar Energy, Erfurt, Germany, ^fORNL, Oak Ridge, TN, U.S.A. (2013)
 Email: johannes.mueller@ieee.org

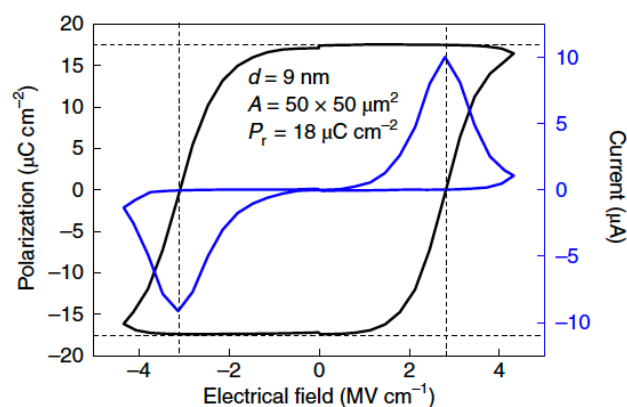
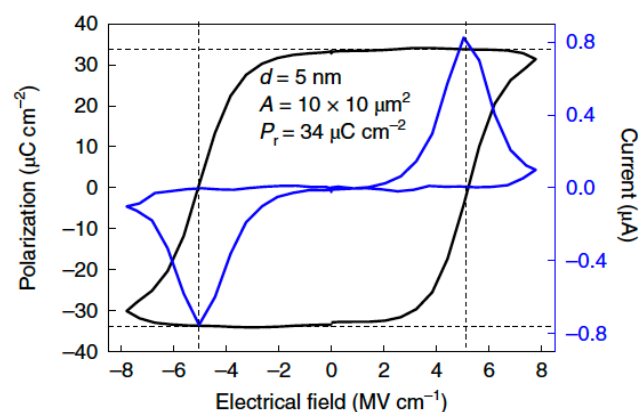
T. S. Böske et al., IEDM (2011)

J. Muller et al, IEEE EDL (2012)

A rhombohedral ferroelectric phase in epitaxially strained Hf_{0.5}Zr_{0.5}O₂ thin films

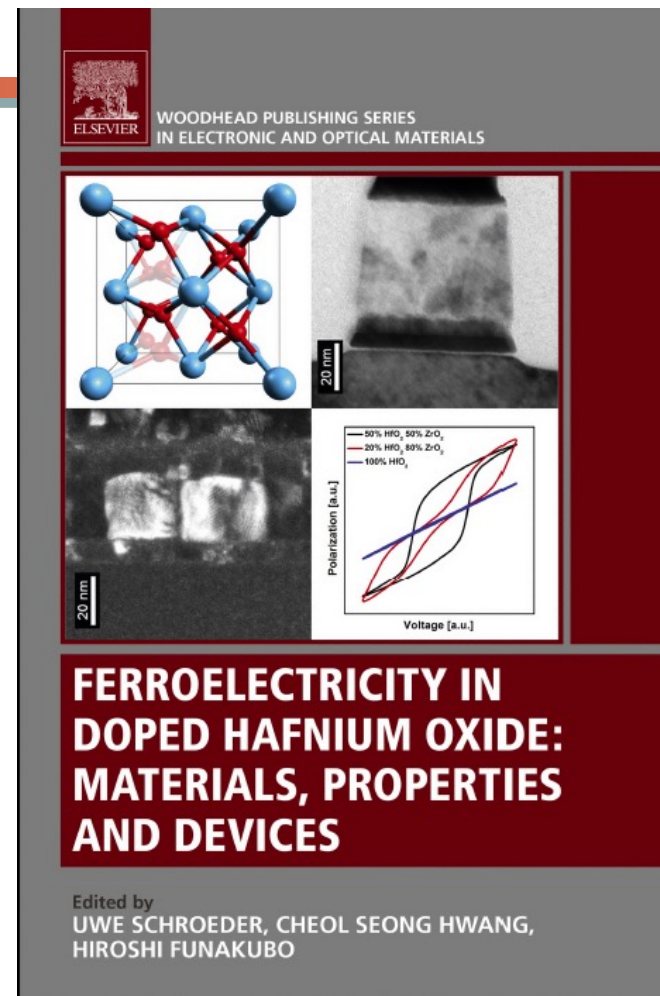
Yingfen Wei¹, Pavan Nukala^{1,2}, Mart Salverda¹, Sylvia Matzen³, Hong Jian Zhao^{1,4}, Jamo Momand¹, Arnoud S. Everhardt¹, Guillaume Agnus³, Graeme R. Blake¹, Philippe Lecoeur³, Bart J. Kooi¹, Jorge Íñiguez⁴, Brahim Dkhil² and Beatriz Noheda^{1*}

Hf_{0.5}Zr_{0.5}O₂ thin films on La_{0.7}Sr_{0.3}MnO₃/SrTiO₃



HfO₂-based compounds

FIXIT



Ferroelectrics and phase transitions

Thermodynamic description

FIXIT

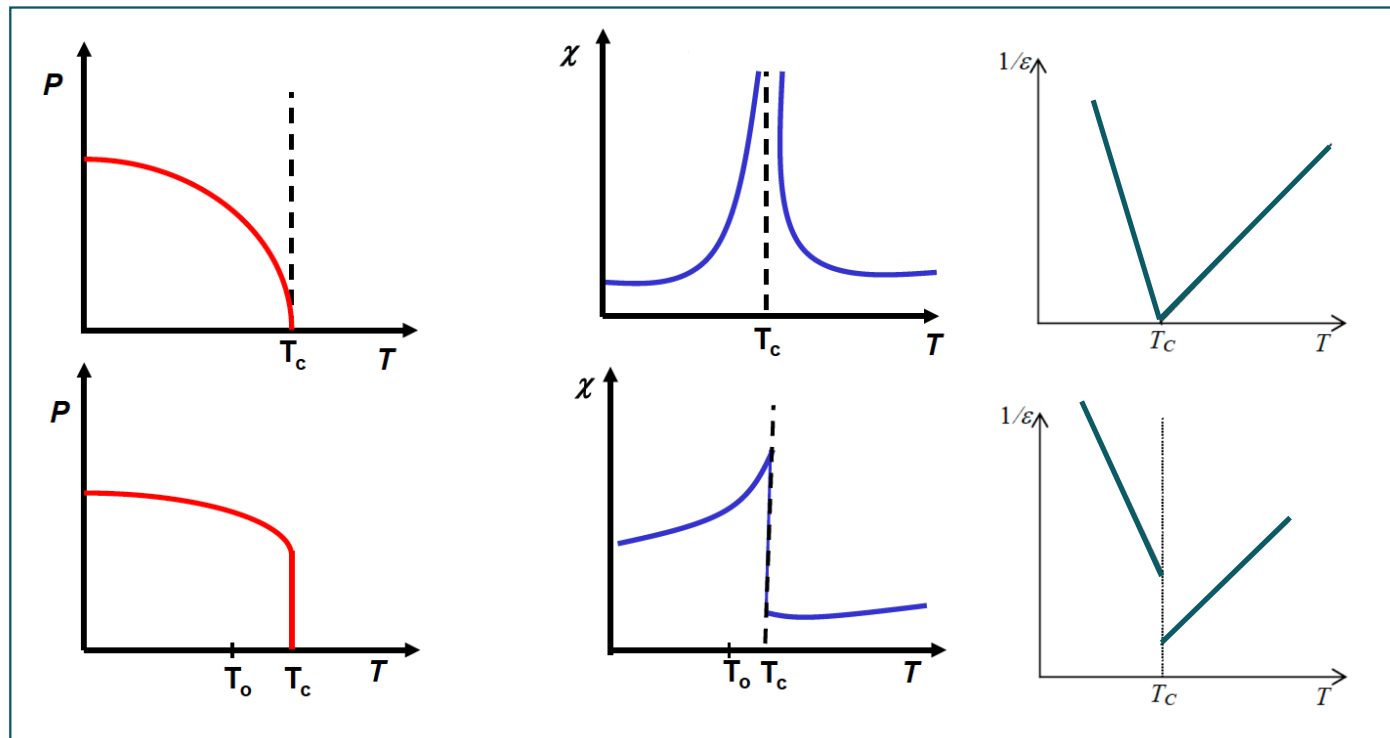


Ferroelectrics and phase transitions

Thermodynamic description

FIXIT

There is a **phase transition at a temperature T_c above which the phase is paraelectric ($P_s = 0$).**



Second-order phase transition

First-order phase transition

Thermodynamic description

FIXIT

Phenomenological or macroscopic theory (treat the material as a continuum without considering the underlying atomic structure)

The stable phase of a system is the one that minimizes its **Gibbs free energy** G

For a ferroelectric system: $G = U - TS - \eta\sigma - ED = H - TS$

Phase transition arises from the competition between the different terms that can evolve with P or T

For a system with free mechanical boundary conditions (no stress applied: $\sigma = 0$ - constant volume V of the system) and no external field applied ($E = 0$), the quantity to be minimized becomes the **Helmholtz free energy** F :

$$F = U - TS$$

where U is the internal energy, T is the temperature and S is the entropy

Thermodynamic description: Landau-Ginzburg-Devonshire phenomenological theory

FIXIT

There is no polarization ($P=0$) in the non-polar state and there is a polarization P below a transition temperature T_c .

For (proper) ferroelectrics, the polarization P is taken as the order parameter (or the displacement)

Note: for improper ferroelectrics (such as YMnO_3), P is not the order parameter!

- **Second-order phase transition:** there is a **continuous change in the order parameter**, from zero in the non-polar state to a non-zero value in the polar state.
- **First-order phase transition:** there is a discontinuous jump in the order parameter from zero in the non-polar state to a finite value at the transition temperature

Thermodynamic description: Landau-Ginzburg-Devonshire phenomenological theory

FIXIT

Following the **Landau-Ginzburg-Devonshire theory**, the free energy F of a ferroelectric material can be described as a Taylor expansion in terms of the order parameter, which is taken to be the **polarization P**

$$F(T) = F_0 + \frac{1}{2}A(T)P^2 + \frac{1}{4}BP^4 + \frac{1}{6}CP^6 + \dots \quad \text{at constant volume } V$$

Second-order phase transition ($B > 0$)

Hypothesis:

- The expansion around the high symmetry phase remains valid above and below the phase transition temperature (T_c), the polarization varies continuously across T_c (and thus takes small values close below T_c)
- The expression must be invariant under symmetry operations of both phases – since the paraelectric phase possesses a center of symmetry $\rightarrow$ no even terms in the expansion
- B and C are constant, $C > 0$ – only A is not a constant

For a given temperature, the spontaneous polarization values in the paraelectric ($P_s = 0$) and in the ferroelectric phases are the ones **that minimizes the free energy F** .

Second-order phase transition ($B > 0$)

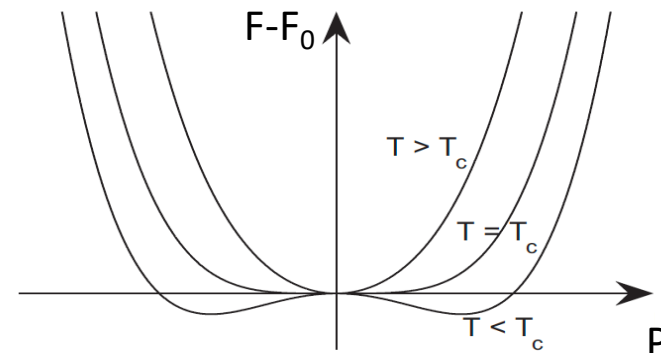
$$F(T) = F_0 + \frac{1}{2}A P^2 + \frac{1}{4}B P^4 + \frac{1}{6}C P^6 + \dots$$

- **When $T > T_c$** , the system is in the paraelectric phase, F should have its minimum value for $P = P_s = 0$
→ the free energy $F(P)$ exhibits a single well as a function of P with a minimum at $P = P_s = 0$, i.e. A must be positive → **$A(T) > 0$**
- **When $T < T_c$** , the system is in the ferroelectric phase and the minimum of F should be for **non zero values of P_s** (finite value)
→ The free energy $F(P)$ exhibits a double well as a function of P , i.e. A must be negative → **$A(T) < 0$**
- **When $T = T_c$** , when passing the transition, the A coefficient (supposed to be continuous) should pass through zero and change sign
→ **$A(T_c) = 0$**

Hence, A can be written as **$A = \alpha (T - T_c)$** with $\alpha > 0$

$F(P)$ is of the following form:

Note: For $P_s = 0$ to represent a minimum of the free energy (and a stable state) at $T = T_c$, B must be positive (or zero)



Second-order phase transition ($B > 0$)

$$F(P, T) = F_0 + \frac{1}{2} A(T) P^2 + \frac{1}{4} B P^4 + \frac{1}{6} C P^6$$

B being assumed to be non-zero, the higher order (in P^6) term can be neglected:

$$F = F_0 + \frac{1}{2} A P^2 + \frac{1}{4} B P^4 \quad \begin{array}{l} A = \alpha (T - T_c) \\ B > 0 \end{array}$$

$T < T_c$ The stable spontaneous polarization P_S states are the ones that minimizes F

$$\frac{\partial F}{\partial P} = A P_S + B P_S^3 = 0 \quad \text{and} \quad \frac{\partial^2 F}{\partial P^2} = A + 3 B P_S^2 > 0 \quad \longrightarrow \quad P_S^2(T) = -\frac{A}{B} = \frac{\alpha(T_c - T)}{B}$$

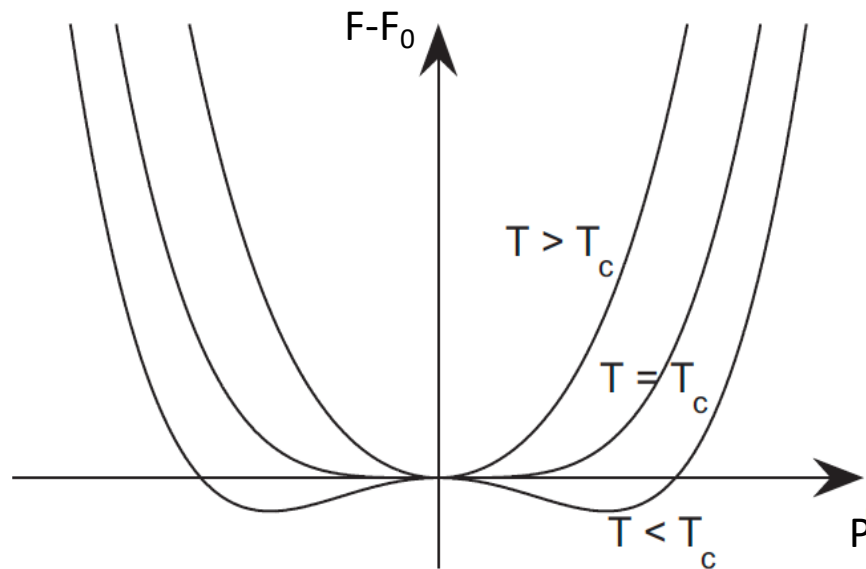
$$P_S(T) = \pm \sqrt{\frac{\alpha}{B}} \sqrt{(T_c - T)}$$

Landau-Ginzburg-Devonshire phenomenological theory

FIXIT

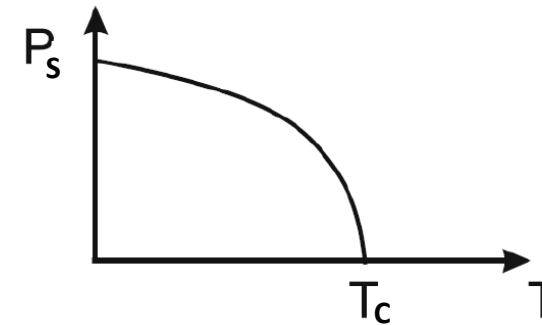
Second-order phase transition ($B > 0$)

$$F = \frac{1}{2} \alpha (T - T_c) P^2 + \frac{1}{4} B P^4 \quad \alpha > 0$$



$$P_S = 0 \quad \text{for } T \geq T_c$$

$$P_S(T) = \pm \sqrt{\frac{\alpha}{B}} \sqrt{(T_c - T)} \quad \text{for } T \leq T_c$$



Landau-Ginzburg-Devonshire phenomenological theory

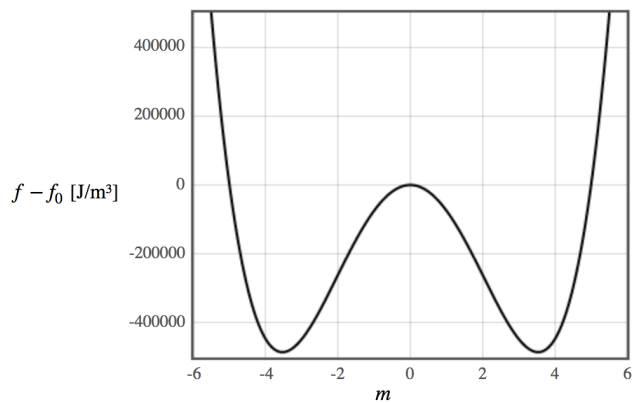
FIXIT

Second-order phase transition ($B > 0$)

T_c for BaTiO_3 is $\sim 120^\circ\text{C}$

BaTiO_3

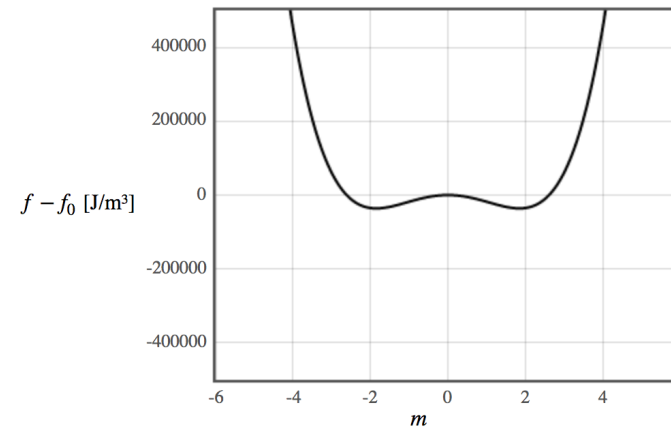
$T = 340 \text{ K}$



$\alpha_0 = 1406.8$
 $\beta = 6167$
 $T = 340$
 $T_c = 395$
 $f_0(T) = -109.39 \cdot T \cdot T + 25184 \cdot T \cdot (\log(T))$
submit

BaTiO_3

$T = 380 \text{ K}$



$\alpha_0 = 1406.8$
 $\beta = 6167$
 $T = 380$
 $T_c = 395$
 $f_0(T) = -109.39 \cdot T \cdot T + 25184 \cdot T \cdot (\log(T))$
submit

m is the order parameter

https://lampx.tugraz.at/~hadley/ss2/landau/second_order.php



Funded by
the European Union

First-order phase transition ($B < 0$)

$$F = F_0 + \frac{1}{2} A P^2 + \frac{1}{4} B P^4 + \frac{1}{6} C P^6$$

$$A = \gamma (T - T_c)$$

There is discontinuous jump of P from 0 to a finite value. This can happen if **B is negative** and then, **for stability, C must be positive.**

The spontaneous polarization P_S at T is the one that minimizes F

$$\frac{\partial F}{\partial P} = A P_S + B P_S^3 + C P_S^5 = 0 \quad \longrightarrow \quad A + B P_S^2 + C P_S^4 = 0$$

and

$$\frac{\partial^2 F}{\partial P^2} = A + 3 B P_S^2 + 5 C P_S^4 > 0$$

also

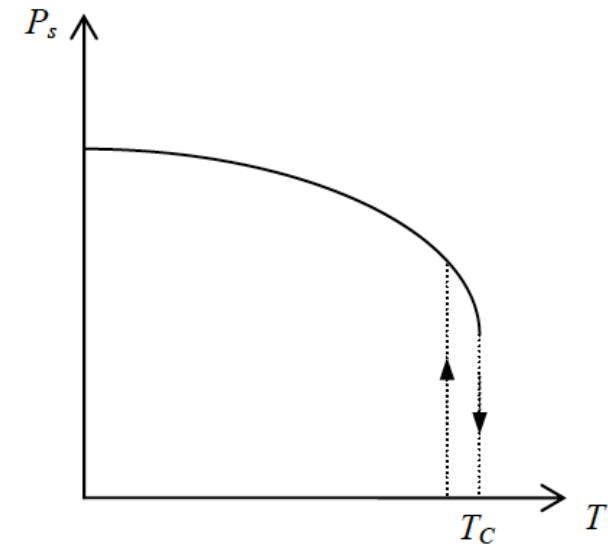
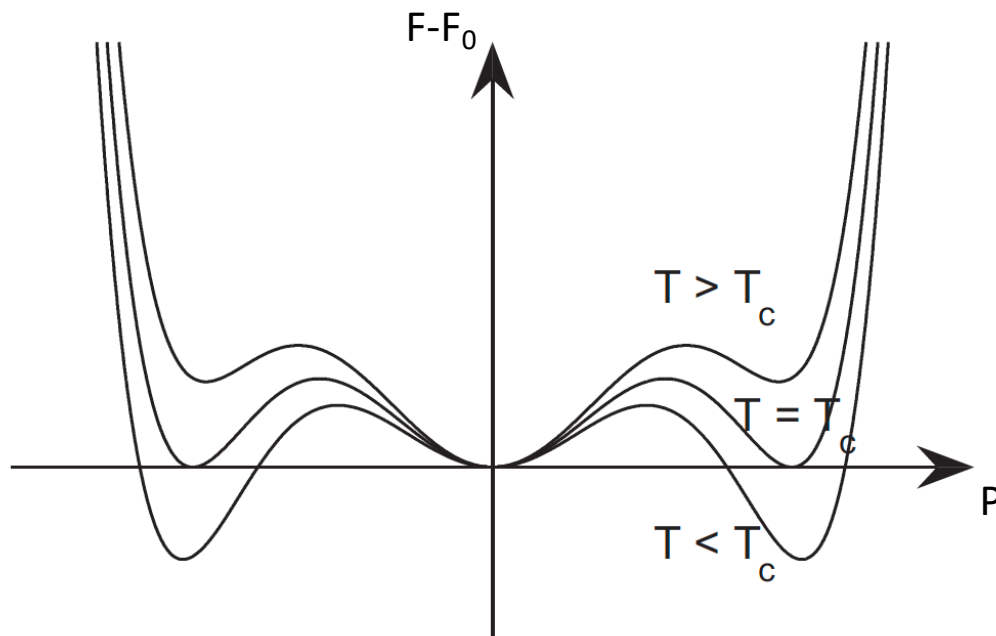
$$F(T = T_c) - F_0 = 0 = \frac{1}{2} A P_S^2 + \frac{1}{4} B P_S^4 + \frac{1}{6} C P_S^6$$

Solutions: not so easy as for second order phase transitions

Landau-Ginzburg-Devonshire phenomenological theory

FIXIT

First-order phase transition ($B < 0$)

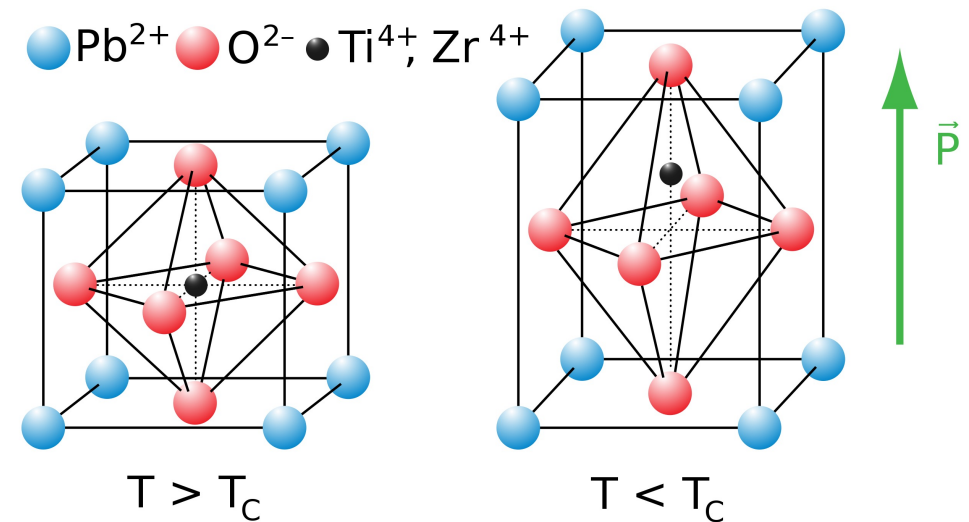


Microscopic approach for the ferroelectricity of perovskite compounds

FIXIT

With the discovery of ferroelectricity in BaTiO_3 (1945) and in other perovskite compounds, the theory of the microscopic origin of ferroelectricity had to be completely revised (it was by then believed that H-bonds were required - the ferroelectricity in the previously known ferroelectrics, Rochelle salt and KDP, was thought to be an order-disorder phenomenon associated with the hydrogen bonds).

The atomistic origin of ferroelectricity in ABO_3 perovskites involves the movements of ions in the unit cell.



By Pinin - Own work, Public Domain, <https://commons.wikimedia.org/w/index.php?curid=11103109>

Microscopic approach for the ferroelectricity of perovskite compounds

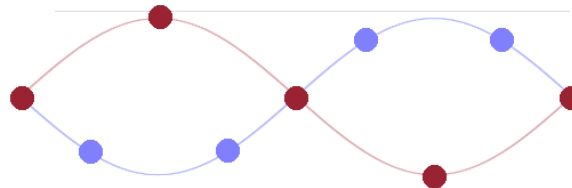
FIXIT

The “soft mode” model for ferroelectricity

W. Cochran, Adv. Phys., Crystal stability and the theory of ferroelectricity, 9, 387 (1960)

“The phenomenon of ferroelectricity in pseudo-cubic crystals is discussed in terms of the normal modes of vibration. It is shown that the parameters which determine the lattice vibrations of a diatomic ionic crystal may be chosen in such a way that the crystal will exhibit ferroelectric properties, and that **ferroelectric or anti-ferroelectric transitions may be regarded as the result of an instability of the crystal for a certain normal mode of vibration**. The theory is extended to apply to other cubic crystals, including barium titanate, and the concepts of ‘ionic polarizability’ and ‘a polarizability catastrophe’ are discussed in terms of lattice dynamics.”

Softening of the lowest energy transverse optical (TO) phonon mode(s) i.e. lattice mode vibrations involving ions soften and lead to the displacive instability



Microscopic approach for the ferroelectricity of perovskite compounds

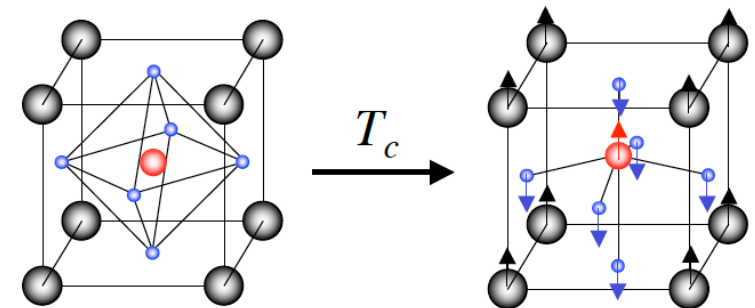
FIXIT

The “soft mode” model for ferroelectricity

- The soft mode is a transverse optic mode and is at the center of the Brillouin zone
- The frequency of the mode goes to zero to freeze in static off-centre displacements of atoms, which gives rise to the ferroelectric polarization. Atoms stay off-centre because the restoring force fails to bring the atoms back to the equilibrium positions due to “softening” of the spring constants.
- Soft mode model accounts for **displacive phase transitions**

Cooperative off-centre displacements of atoms

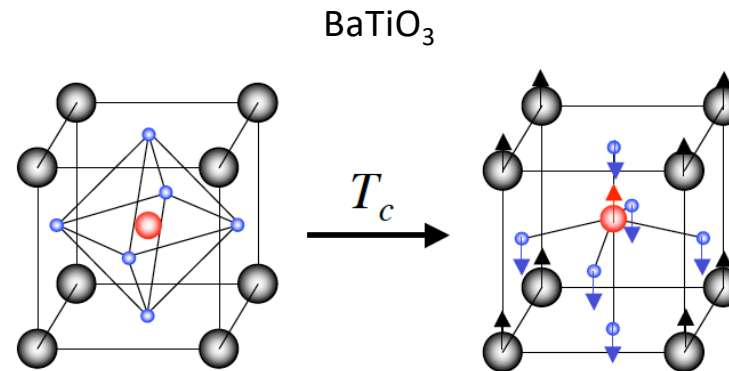
Competition between short range forces (B cation /nearest neighbors) **and the long range Coulomb** (dipole-dipole) interaction in the compound.



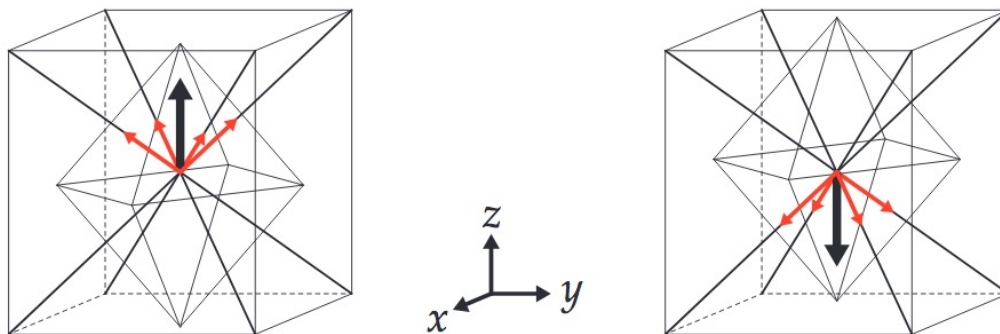
Microscopic approach for the ferroelectricity of perovskite compounds

FIXIT

The “soft mode” model for ferroelectricity



Displacement along the $\langle 111 \rangle$ directions of the cubic perovskite



In the tetragonal phase, P is along $\langle 001 \rangle$

Domains in ferroelectrics

FIXIT

At least two polarization orientations are stable and can be switched between each other by application of an electric field.

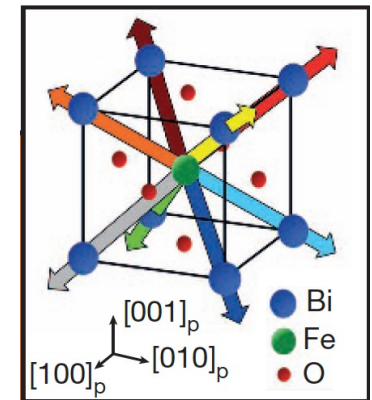
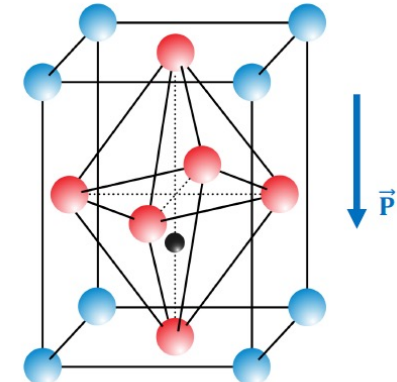
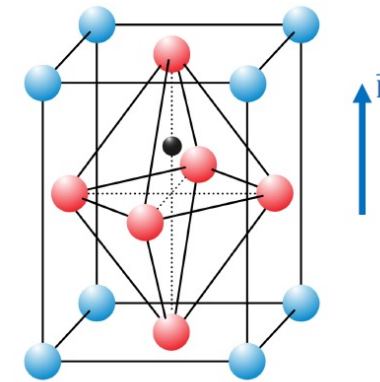
These polarizations are equivalent in energy and therefore may occur equally upon cooling from the high symmetry phase (paraelectric) to the ferroelectric phase

→ Domains will form

From a cubic to a tetragonal phase (BaTiO_3): polarization along the 2 equivalent directions $\langle 001 \rangle$ of the crystal → Domains of opposite directions (**180° domains**)

From a cubic to a rhomboedral phase : polar order along the 8 equivalent directions $\langle 111 \rangle$ of the crystal → Domains with diagonal long axes that are **71°** , **109°** , and **180°** apart.

In addition, the polarization is strongly coupled to piezoelectricity (strain) in perovskite ferroelectrics

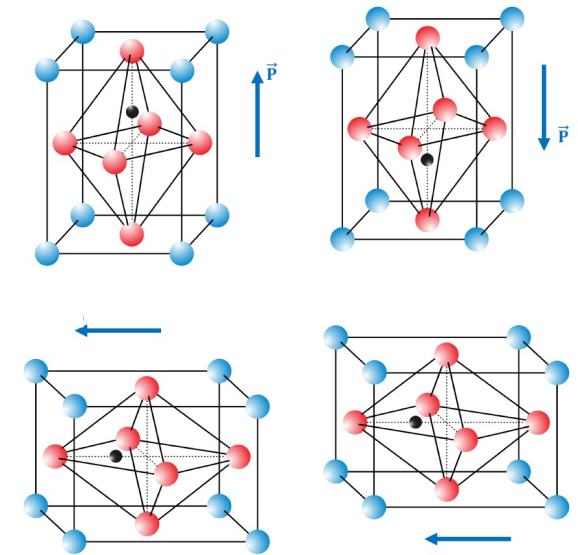
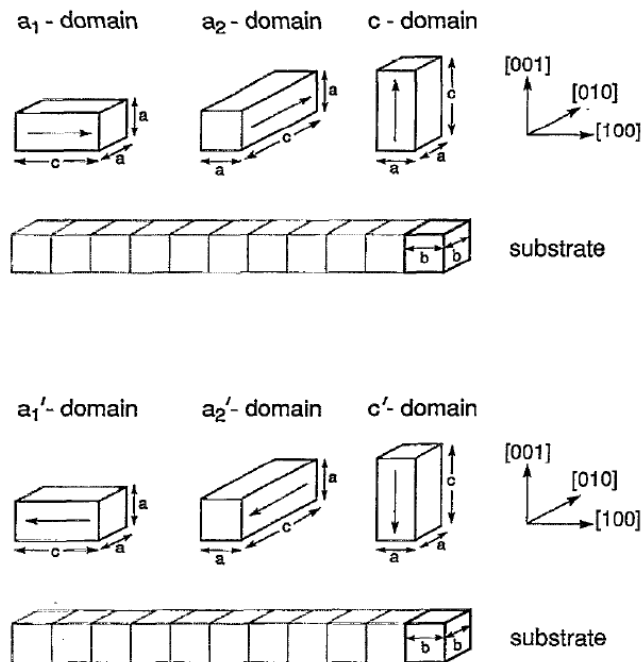
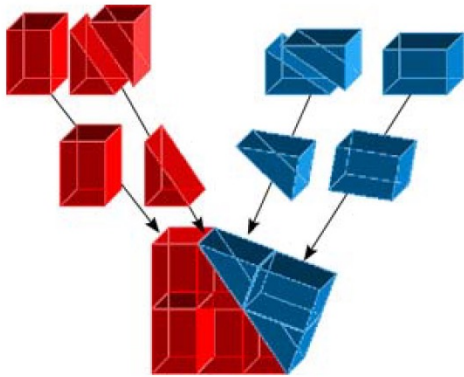


Domains in ferroelectrics

FIXIT

In addition, the polarization is strongly coupled to piezoelectricity (strain) in perovskite ferroelectrics

→ Twinning will lead to the presence of domains perpendicular to each others



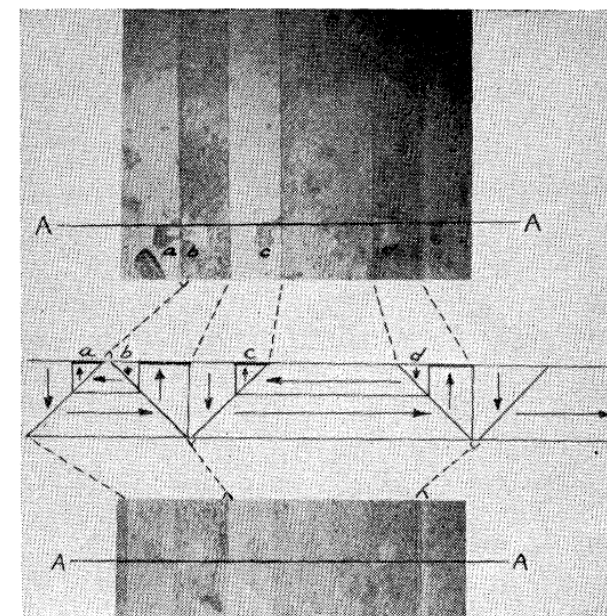
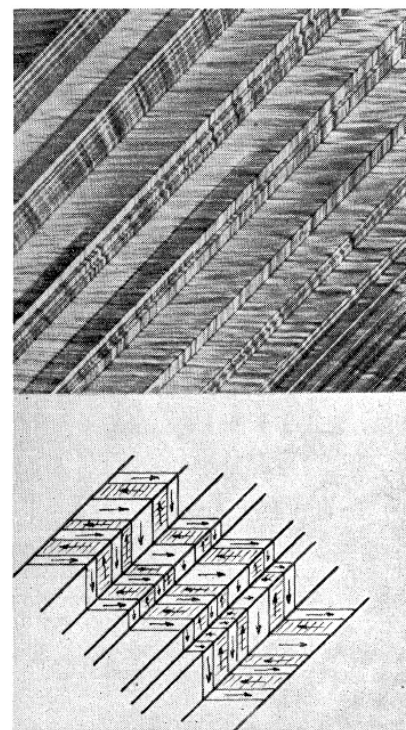
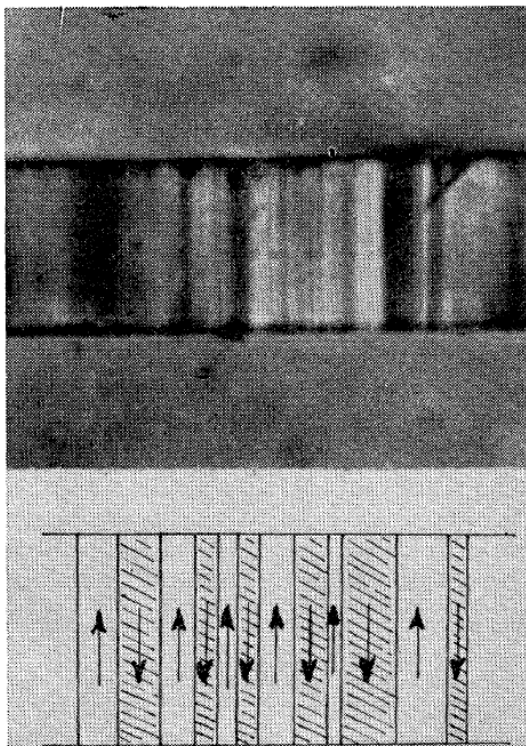
P.-E. Janolin, J Mater Sci (2009) 44:5025–5048

Catalan *et al*, Rev. Mod. Phys, 84, 119 (2012)

Perovskite ferroelectrics: BaTiO₃

FIXIT

Domains imaged on etched BaTiO₃ single crystals



It was observed that ferroelectric domains in BaTiO₃ crystals are always so arranged that there is no build-up of a space charge on the domain walls.

J.A. Hooton and W.J. Merz, Phys. Rev. 98, 409 (1955)

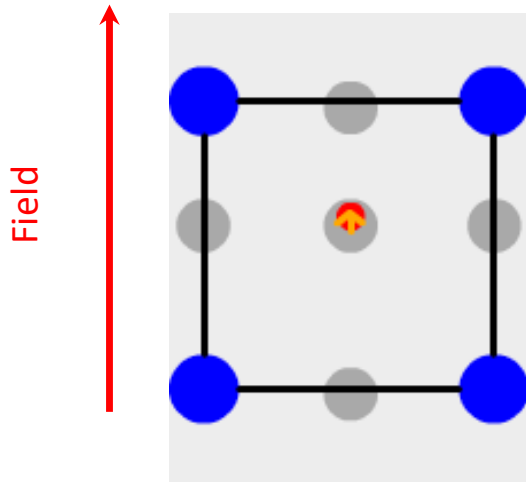


Funded by
the European Union

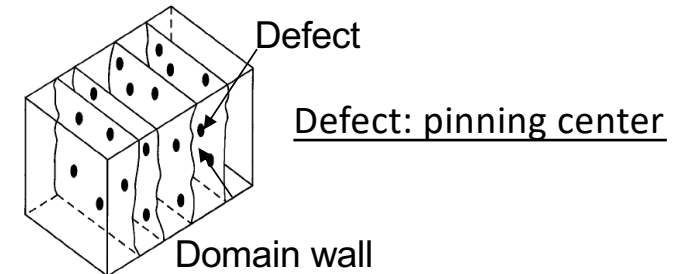
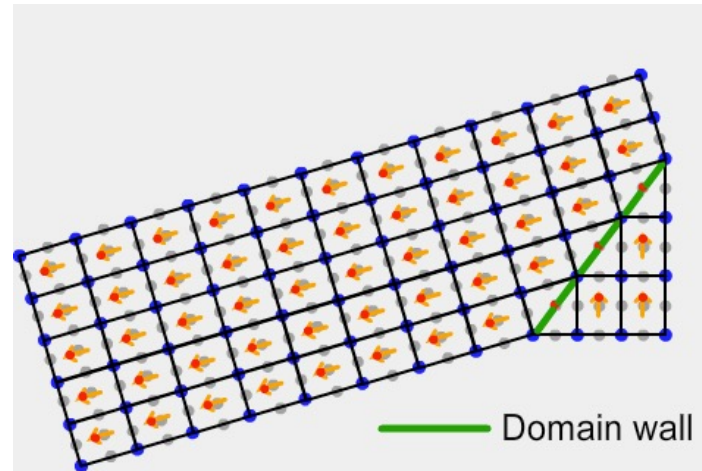
Domains contribution to the ferroelectricity – Intrinsic and Extrinsic Piezoelectricity

FIXIT

Intrinsic – deformation of lattice



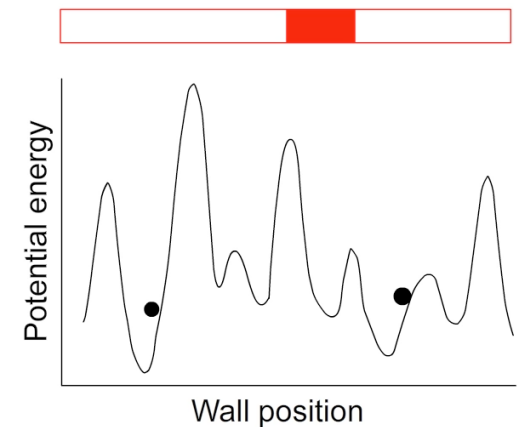
Extrinsic – domain wall or phase boundary motion



D. Damjanovic, *NATO Science Series 3. High Technology*
76 (2000) 123

DW motion:

- Contributes to the RT permittivity of capacitors
- Provides up to 75% of the piezoelectric response of soft piezoelectric ceramics
- Controls aging of properties
- Governs the dynamics and the stability of stored domain states, as well as the ability to reset the state



Courtesy Prof. S. Trolor-McKinstry



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the European Union



PennState

Ferroelectrics thin films:

Domains, domain walls

Strain and size effects



(r)evolution in the past 20 years

- Unit cell control of the growth of thin films and of their interfaces
- First principle calculation
- New probes (scanning probe microscopy, advanced microscopy methods...)
- AI and big data analysis



Better understanding and engineering of properties:

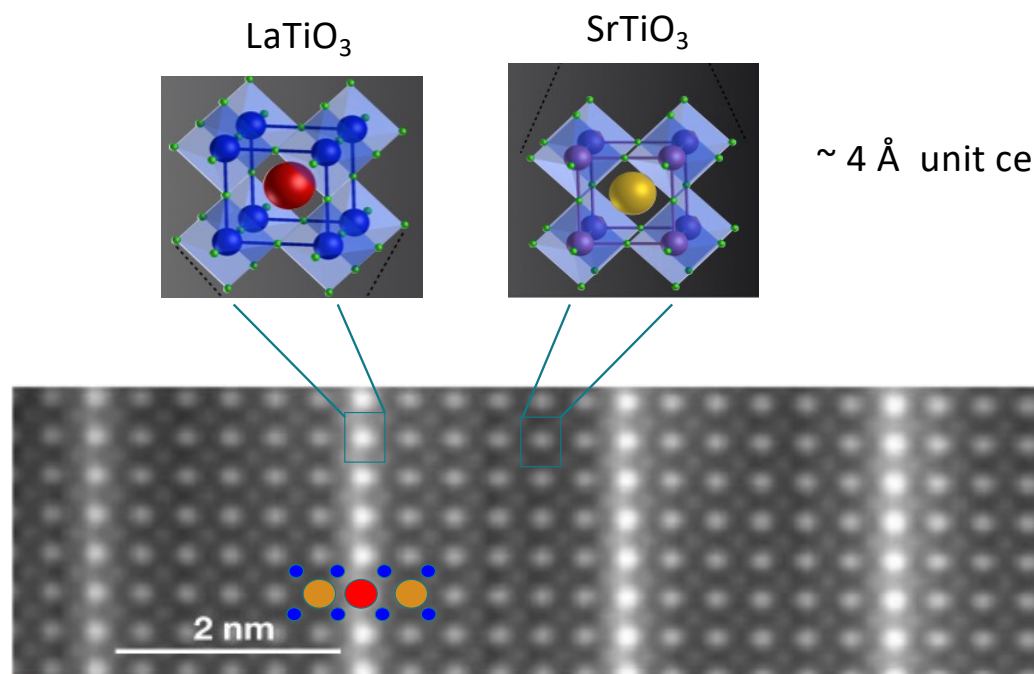
- Size effects
- Strain effects (role of substrate, buffer...)
- Coupling at interfaces / new phenomena at interfaces
- Domain structure and dynamics
- Role of boundary conditions (mechanical, electrical...)



Epitaxy of ferroelectrics

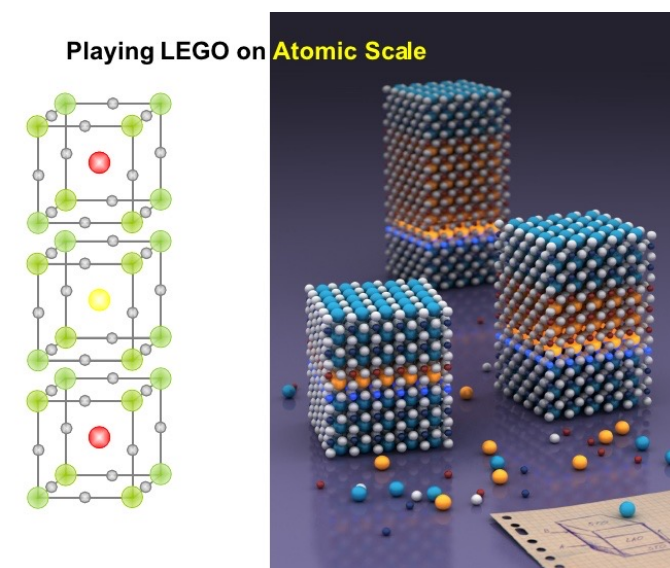
FIXIT

Huge progress since the 2000's in the epitaxy of oxides with control of the growth at the unit cell



Ohtomo *et al.* Nature (2002)

LaTiO₃/SrTiO₃ superlattice
(inserting one plane of La-O in SrO-TiO₂)



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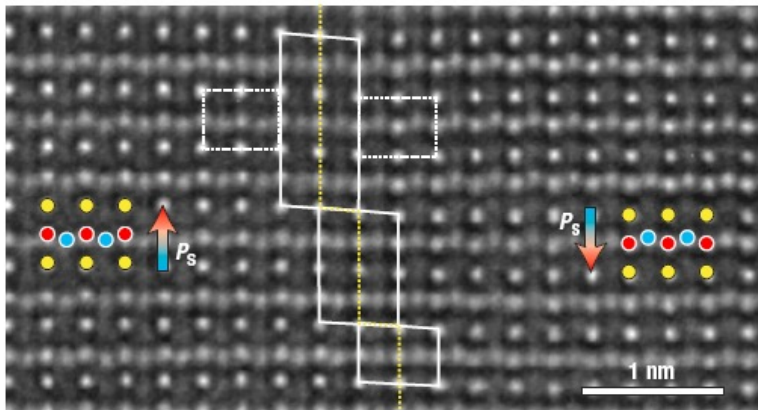
Structural characterization of ferroelectrics

FIXIT

Progress in microscopes and analytic tools (Cs-corrected microscopes...)

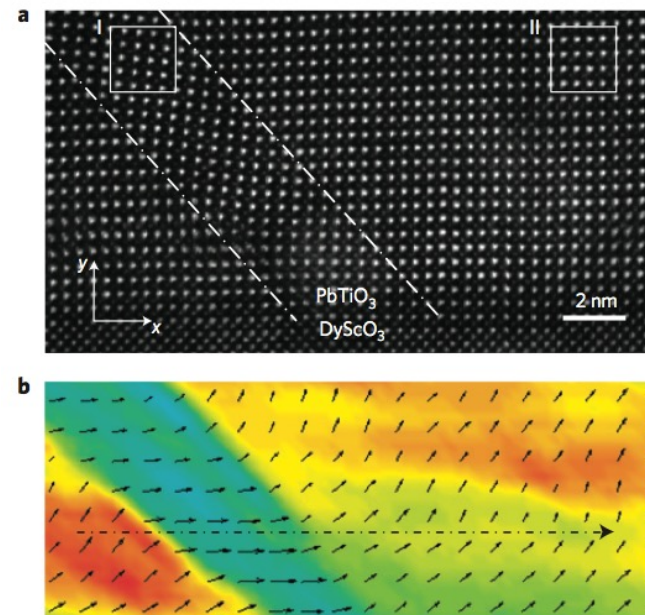
- Geometrical phase analysis , electron holography → strain
- Imaging of the atomic positions of atomic columns using HAADF-STEM
- 4D STEM methods

$\text{Pb}(\text{Zr,Ti})\text{O}_3$ on SrTiO_3



C.-L. Jia *et al*, Nature Materials 7, 57 (2008)

Mapping of the polarization



G. Catalan *et al.*, Nat. Mater. (2011)



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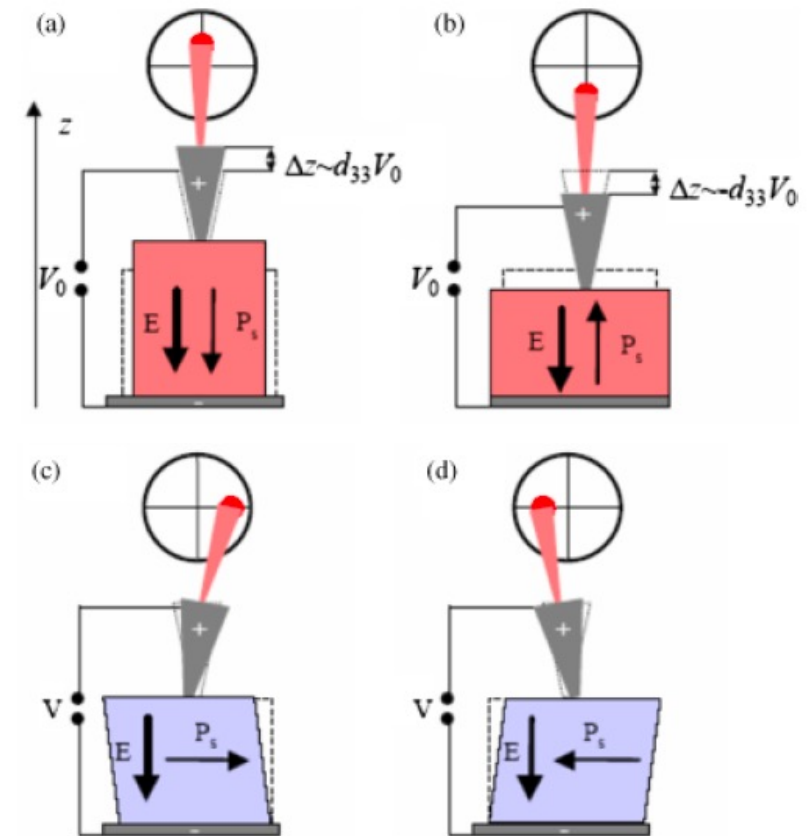
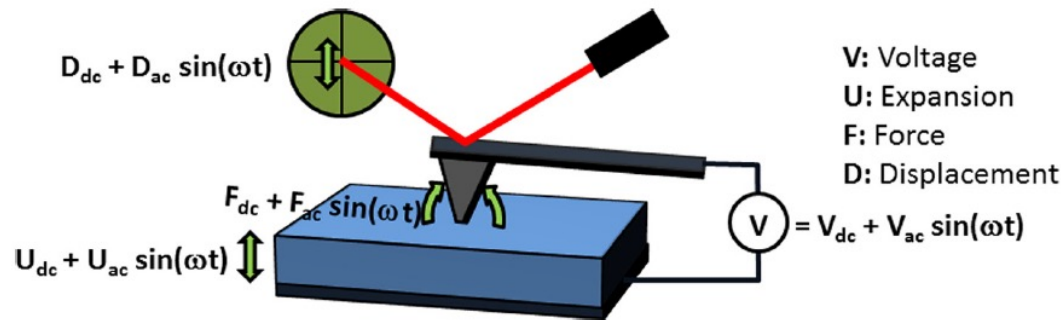
Piezoelectric force microscopy (PFM)

FIXIT

A ferroelectric material is piezoelectric – hence it deforms under an applied electric field

Application of a small a.c. periodic electric bias (via the tip) and detection (via the tip as well) of the cantilever mechanical motion due to the piezoelectric strain generated in the ferroelectric sample.

The cantilever motion can be a vertical displacement, torsion or bending.



- A. Gruverman et al., Ferroelectrics 184, 11 (1996)
 S. V. Kalinin, B. J. Rodriguez, S. Jesse, J. Shin, A. P. Baddorf, P. Gupta, H. Jain, D. B. Williams, and A. Gruverman, Vector Piezoresponse Force Microscopy, Microsc. Microanal. 12, 206–220 (2006)
 A. Gruverman, M. Alexe and D. Meier, Nat. Comm.10, 1661 (2019)
 Owoong Kwon, Daehee Seol, Huimin Qiao, and Yunseok Kim, Recent Progress in the Nanoscale Evaluation of Piezoelectric and Ferroelectric Properties via Scanning Probe Microscopy, Adv. Sci. , 1901391 (2020)
 N. Balke et al., J. Am. Ceram. Soc., 92 [8] 1629–1647 (2009)
 R.K. Vasudevan et al., Appl. Phys. Rev. 4, 021302 (2017)



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the European Union

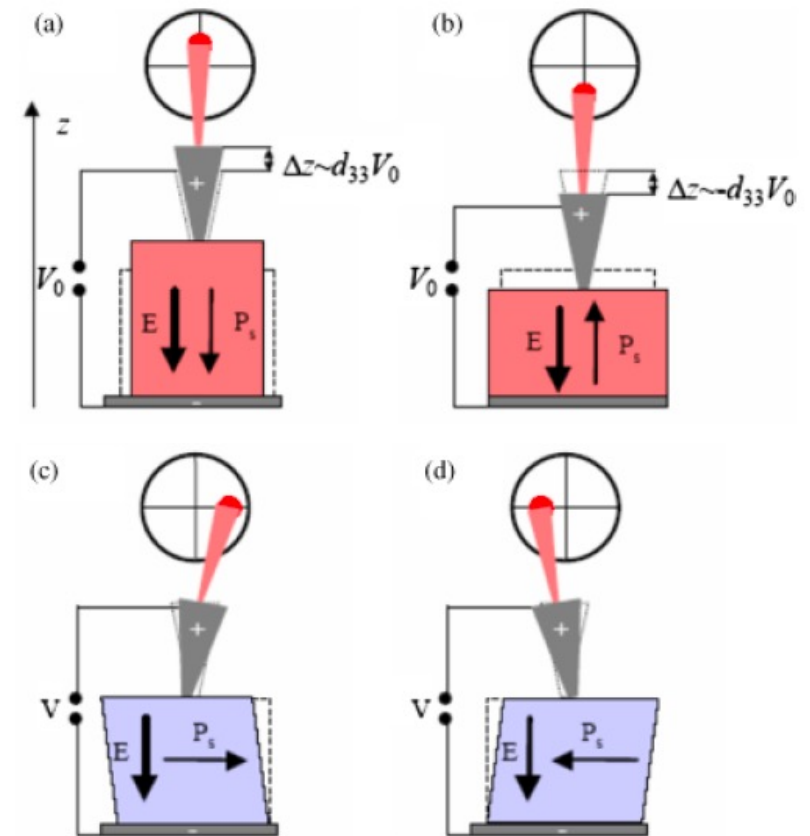
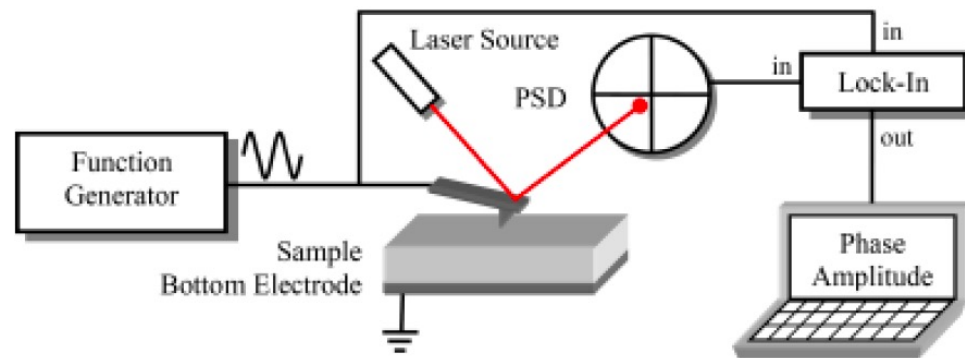
Piezoelectric force microscopy (PFM)

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The cantilever motion can be a vertical displacement, torsion or bending.



N. Balke et al., J. Am. Ceram. Soc., 92 [8] 1629–1647 (2009)

R.K. Vasudevan et al., Appl. Phys. Rev. 4, 021302 (2017)



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Piezoelectric force microscopy (PFM)

FIXIT

Single frequency PFM:

The excitation frequency is maintained constant during imaging: amplitude and phase of the cantilever response are determined using a lock-in amplifier.

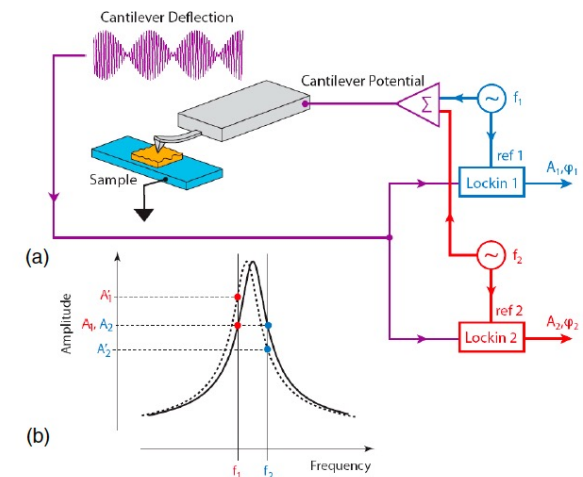
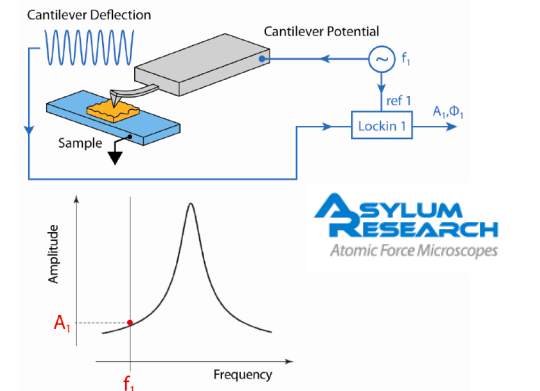
An excitation voltage with frequency near the contact resonance **lead to better sensitivity (amplification effect) BUT** can sometimes lead to large topographic cross-coupling

The amplitude and phase of the local response are a convolution of material response to the external field **and** cantilever response to the material-dependent local force, which cannot be separated unambiguously

Dual AC Resonance Tracking Piezo Force Microscopy

N. Balke et al., J. Am. Ceram. Soc., 92 [8] 1629–1647 (2009)

B.J. Rodriguez et al., Nanotechnology 18, 475504 (2007)



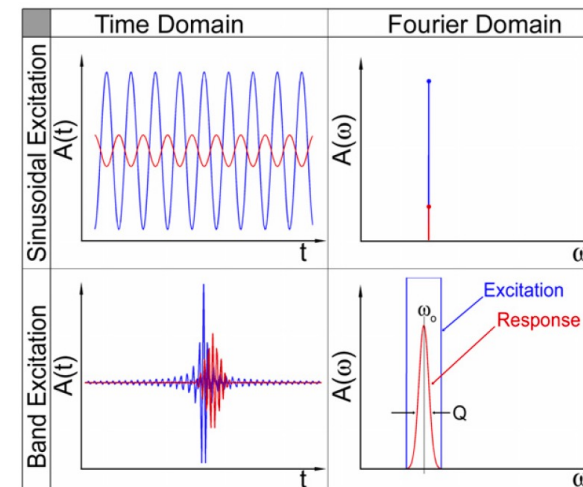
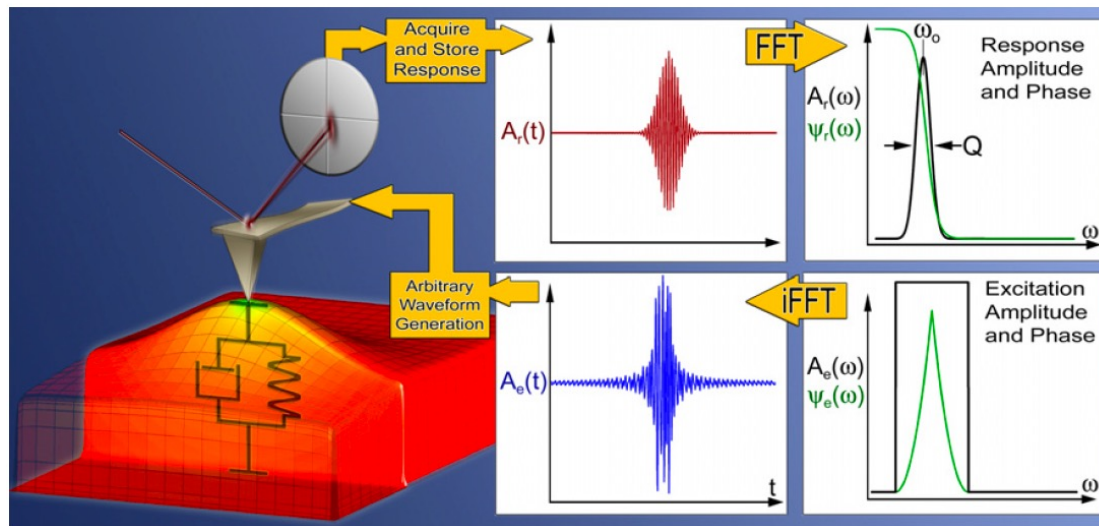
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Piezoelectric force microscopy (PFM)

FIXIT

Band excitation PFM

Exciting and monitoring the electromechanical response within a continuous frequency band



Quantitative measurements of the energy dissipation through the determination of the Q-factor of the cantilever-sample system

S. Jesse and S. K. Kalinin, J. Phys. D: Appl. Phys. 44 (2011) 464006 (16pp)

S. Jesse, S. V. Kalinin, R. Proksch,, A. P. Baddorf and B. J. Rodriguez, Nanotechnology 18 (2007) 435503



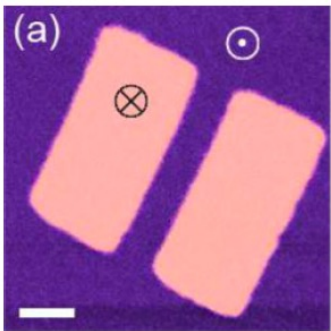
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PFM spectroscopy mode

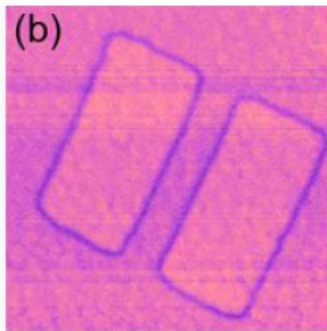
FIXIT

Tetragonal PZT thin film

Vertical PFM phase map

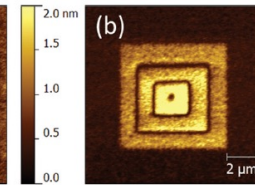
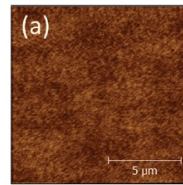


Vertical PFM amplitude map

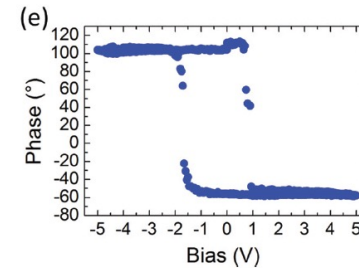
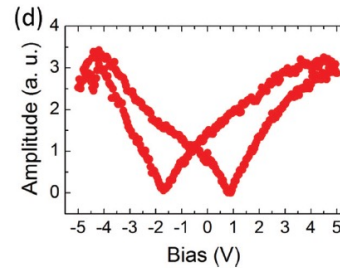
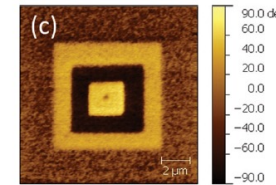


Tetragonal BaTiO₃ thin film

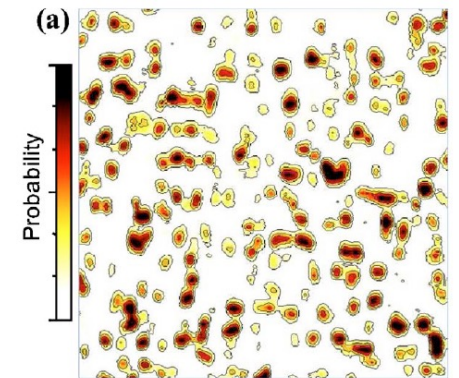
VPFM phase map



VPFM amplitude map



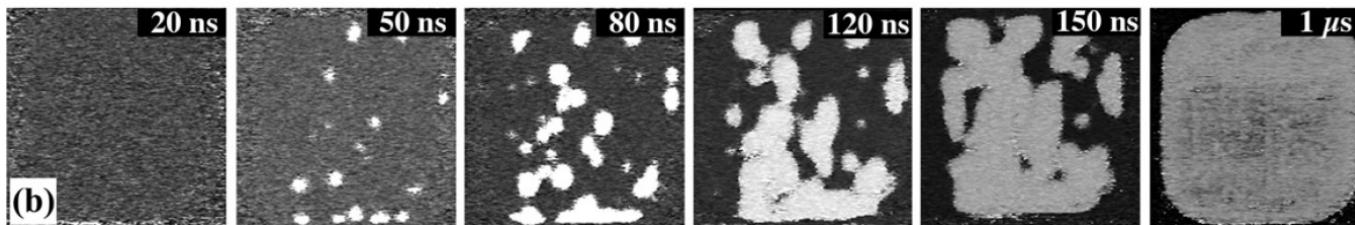
Epitaxial PZT capacitor



Probability of domain nucleation

Epitaxial PZT capacitor

Domain configurations with out-of-plane polarization developing at different stages of polarization reversal



- L. Mazet *et al.*, J. Appl. Phys. 116, 214102 (2014)
- L. Mazet *et al.*, Sci. Technol. Adv. Mater. 16 (2015) 036005
- D. Denning *et al.*, International Materials Reviews 61, 46 (2016)
- D.J. Kim *et al.*, Appl. Phys. Lett. 91, 132903 (2007)
- A. Gruverman *et al.*, J. Phys.: Condens. Matter 20, 342201 (2008).



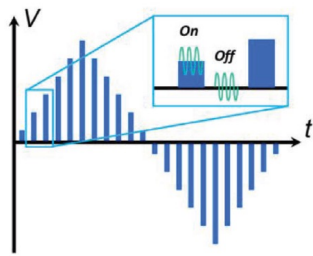
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Switching spectroscopy mode (SS-PFM)

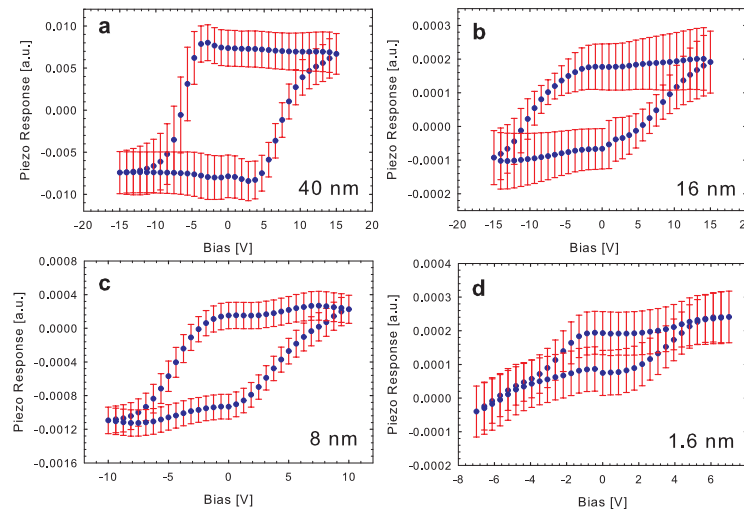
FIXIT

Local measurement of hysteresis loop by PFM

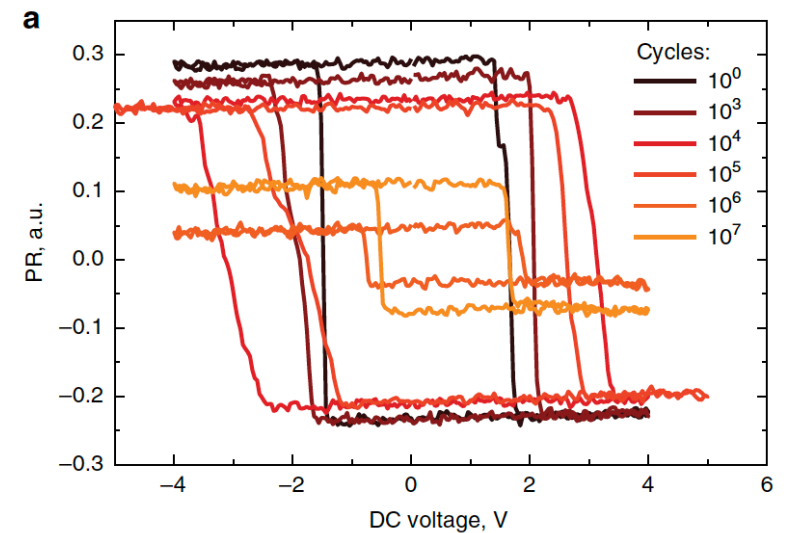
The PFM hysteresis loop is typically measured at a fixed point by applying a pulse-type triangular voltage waveform



Switching of BaTiO₃ epitaxial films on Si(001)



Study of fatigues in ferroelectric capacitors



S. Jesse, Appl. Phys. Lett. 88, 062908 (2006)
C. Dubourdieu *et al.*, Nature Nanotechnology (2013)
Anton V. Ievlev *et al.*, Nature Comm. 10, 3064 (2019)



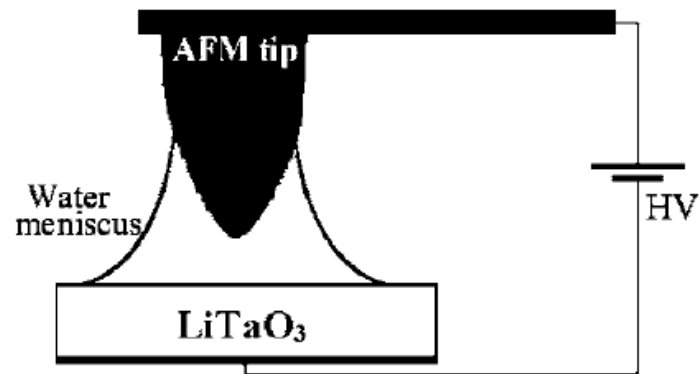
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Piezoelectric force microscopy (PFM)

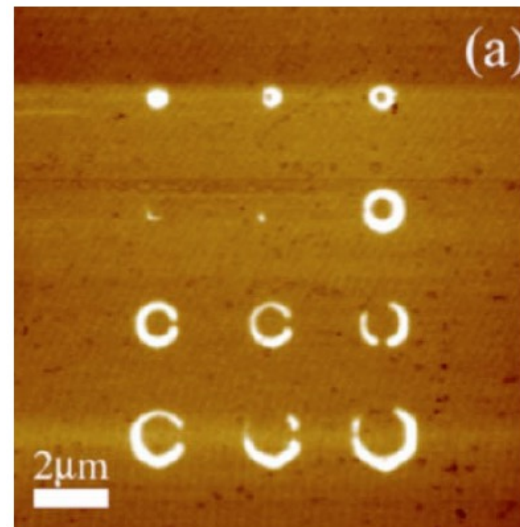
FIXIT

Artefacts

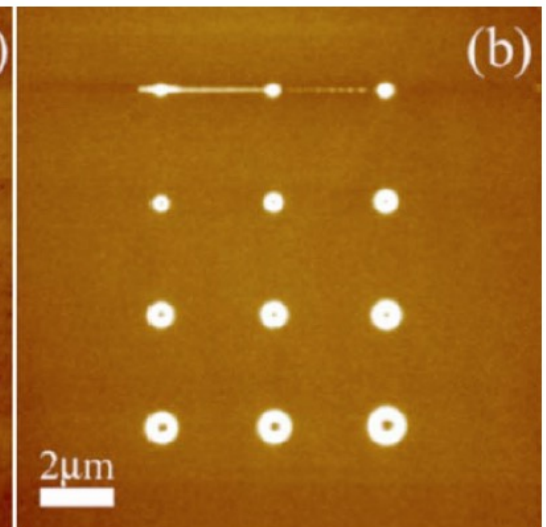
A **water meniscus** is formed between an AFM tip and sample surface under ambient conditions.



ambient conditions



low 2 ppm water humidity



- Role of humidity in nanoscale domain inversion

D. Dahan et al., Appl. Phys. Lett. 89, 152902 (2006)

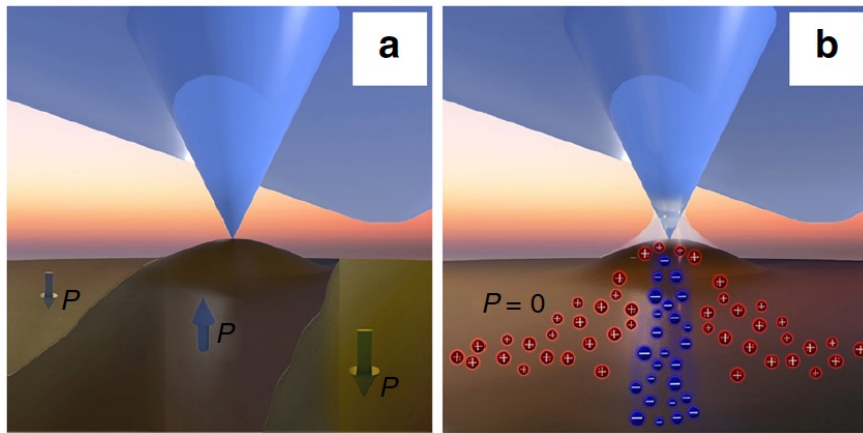


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Piezoelectric force microscopy (PFM)

FIXIT

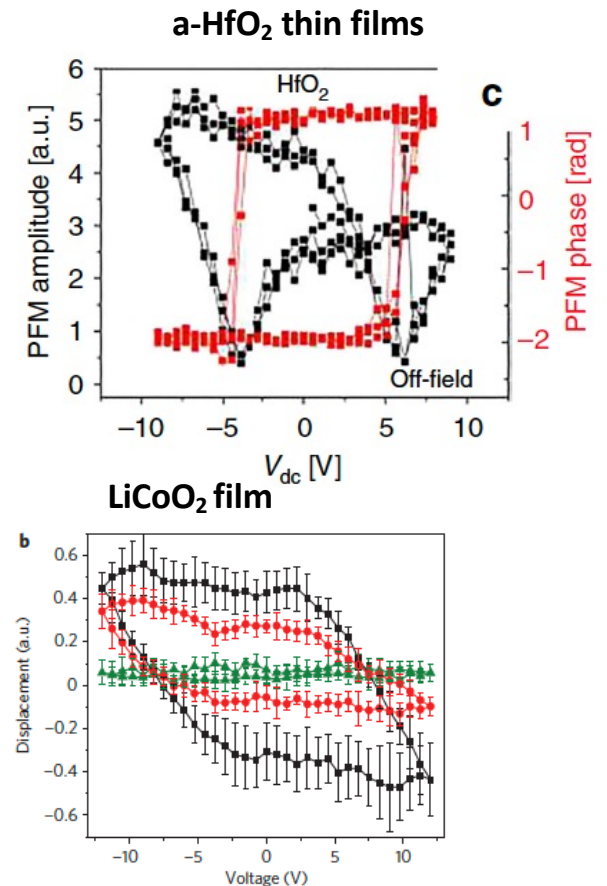
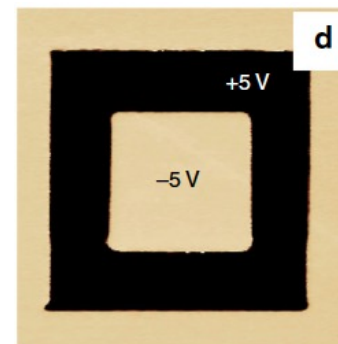
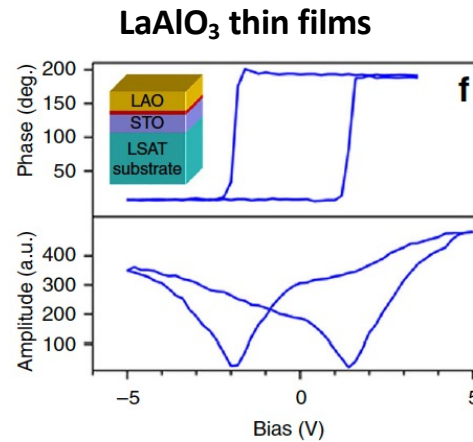
Ferroelectric and non-ferroelectric contributions in PFM



Non ferroelectric thin films may have the same response as the one typical for FE!

N. Balke et al., Nat. Nano 5, 749 (2010)

A. Gruverman, M. Alexe and D. Meier, Nat. Comm.10, 1661 (2019)

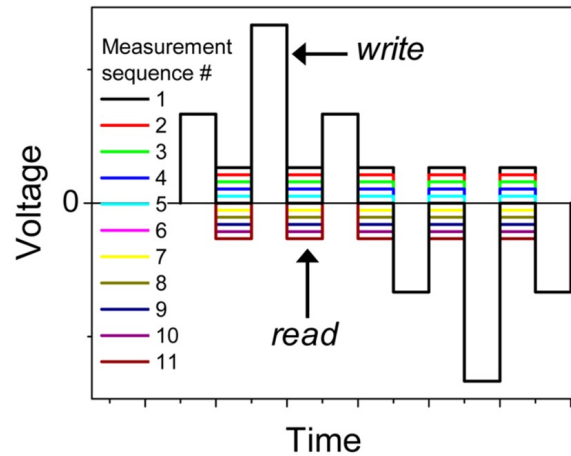


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Contact Kelvin Probe Microscopy (cKPFM)

FIXIT

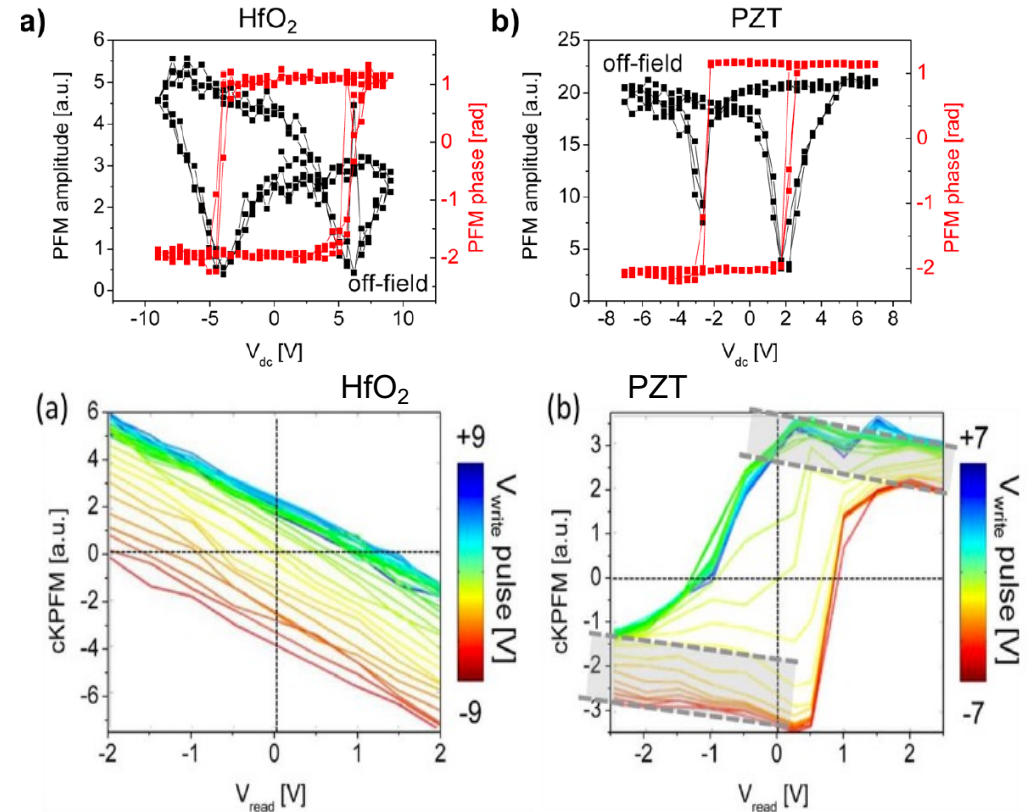
Method developed to distinguish between FE response and electrostatic force (charge injection, ...)



Opening of a loop for ferroelectric materials while response is linear for dielectrics

N. Balke *et al.*, ACS Nano 8, 10229, 2014

N. Balke *et al.*, ACS Nano 9, 6484, 2015



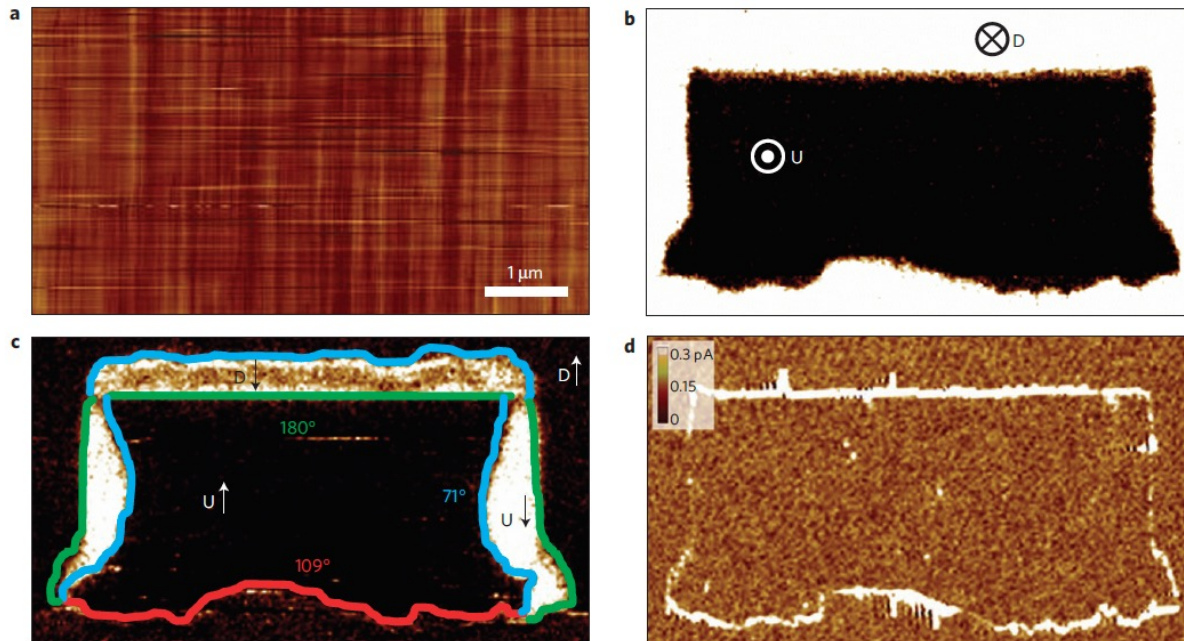
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Conductive AFM(CAFM)

FIXIT

Used to test the local electrical properties of a material.

Probing the conductivity of domain walls



J. Seidel et al., Nature Materials 8, 229 (2009)

F. Hui and M. Lanza, Scanning probe microscopy for advanced, Nanoelectronics, Nature Electronics 2, 221 (2019)



Funded by
the European Union

PFM and CAFM: evidence of new phenomena

FIXIT

Tunneling Electroresistance Effect in Ferroelectric Tunnel Junctions at the Nanoscale

A. Gruverman,^{*,†} D. Wu,[‡] H. Lu,[†] Y. Wang,[†] H. W. Jang,[§] C. M. Folkman,[§]
M. Ye. Zhuravlev,^{†,||} D. Felker,[§] M. Rzchowski,[§] C.-B. Eom,[§] and E. Y. Tsymlant

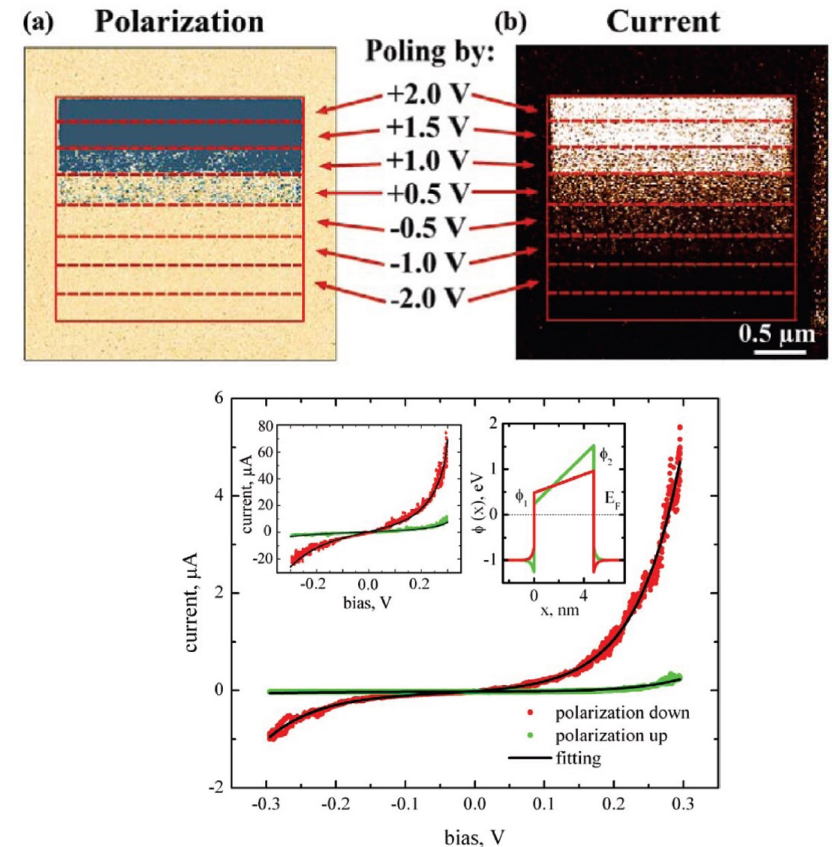
University of Nebraska, Lincoln, Nebraska 68588, North Carolina State University, Raleigh, North Carolina 27695, University of Wisconsin-Madison, Wisconsin 53706, and Kurnakov Institute for General and Inorganic Chemistry, RAS, Moscow, Russia

NANO
LETTERS

2009
Vol. 9, No. 10
3539-3543

A. Gruverman, D. Wu, H. Lu, Y. Wang, H. W. Jang, C. M. Folkman, M. Ye. Zhuravlev, D. Felker, M. Rzchowski, C.-B. Eom, and E. Y. Tsymlant, Tunneling Electroresistance Effect in Ferroelectric Tunnel Junctions at the Nanoscale, Nano Lett. 9, 3539 (2009)

V. Garcia, S. Fusil, K. Bouzehouane, S. Enouz-Vedrenne, N. D. Mathur, A. Barthelemy & M. Bibes, Giant tunnel electroresistance for non-destructive readout of ferroelectric states, Nature 460, 81 (2009)



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PFM and CAFM: evidence of new phenomena

FIXIT

NANO LETTERS

Letter

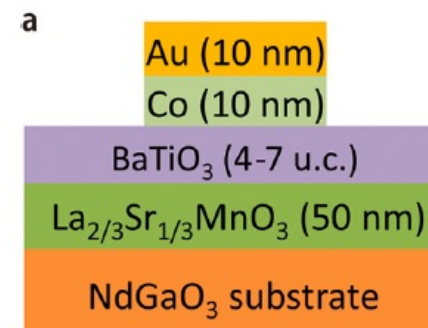
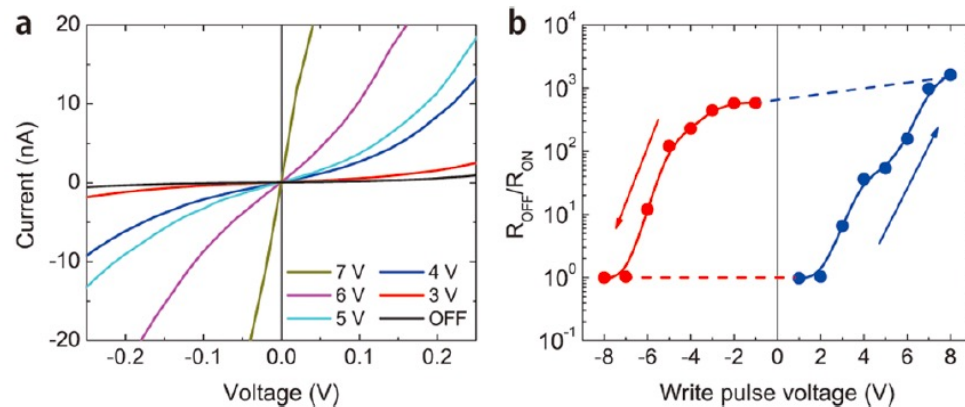
pubs.acs.org/NanoLett

Ferroelectric Tunnel Memristor

D. J. Kim,[†] H. Lu,[†] S. Ryu,[‡] C.-W. Bark,[‡] C.-B. Eom,[‡] E. Y. Tsymbal,[†] and A. Gruverman^{*,†}

[†]Department of Physics and Astronomy & Nebraska Center for Materials and Nanoscience, University of Nebraska-Lincoln, Lincoln, Nebraska 68588, United States

[‡]Department of Materials Science and Engineering, University of Wisconsin-Madison, Madison, Wisconsin 53706, United States



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the European Union

Ferroelectrics thin films:

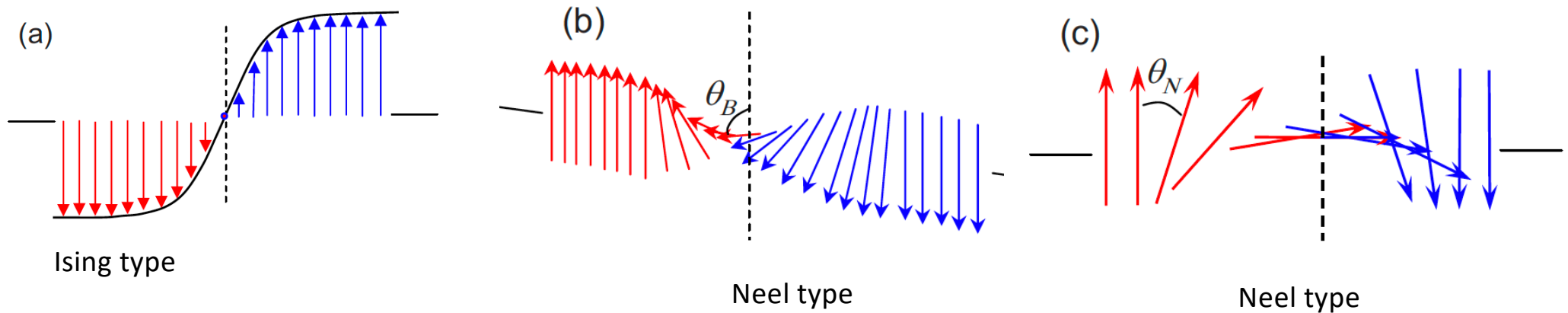
Domains, domain walls

Strain and size effects



Domains in ferroelectrics

FIXIT



- In ferroelectrics, there is a strong coupling of polarization and strain (piezoelectricity)
- Domains walls were thought to be only of Ising type until ~15 years ago
- Ferroelectric polarization (direction, amplitude) and domain formation are determined by the boundary conditions which determine the paths to screen the charge and the ability to switch them

D. Lee et al, Phys. Rev. B 80, 060102(R) (2009)



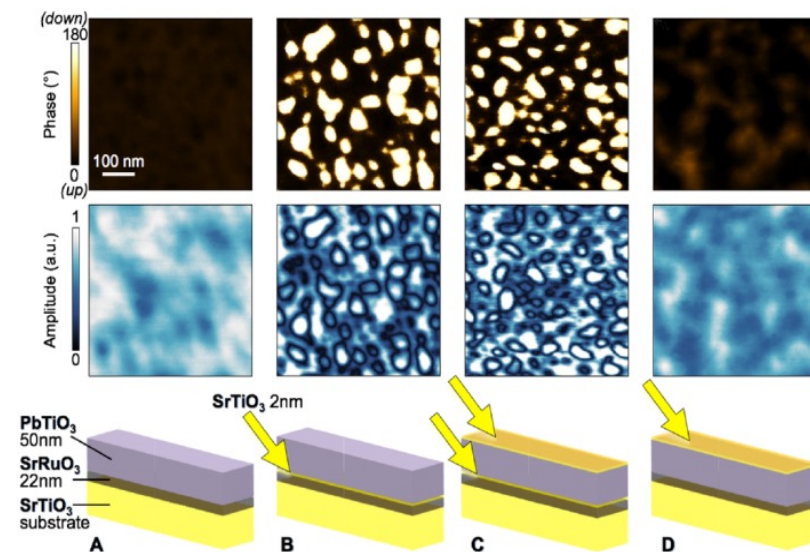
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Depolarization field and domains

FIXIT

- Polarization induces bound charges at surface or interfaces that must be compensated
- Ferroelectric polarization (direction, amplitude) and domain formation are determined by the boundary conditions which determine the ability and the paths to screen the charge

Boundary conditions: **electrical, mechanical, chemical boundary conditions**



Strong change in the domain pattern by inserting a SrTiO₃ film on top or below the ferroelectric layer or on both sides of it

Sergei V Kalinin, Yunseok Kim, Dillon D Fong and Anna N Morozovska, Surface-screening mechanisms in ferroelectric thin films and their effect on polarization dynamics and domain structures, Rep. Prog. Phys. 81 (2018) 036502 (74pp)
C. Lichtensteiger *et al.* Nano Letters (2014)



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Depolarization field and domains

FIXIT

- Polarization induces bound charges at surface or interfaces that must be compensated
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Boundary conditions: **electrical, mechanical, chemical boundary conditions**

Materials
Views

www.MaterialsViews.com

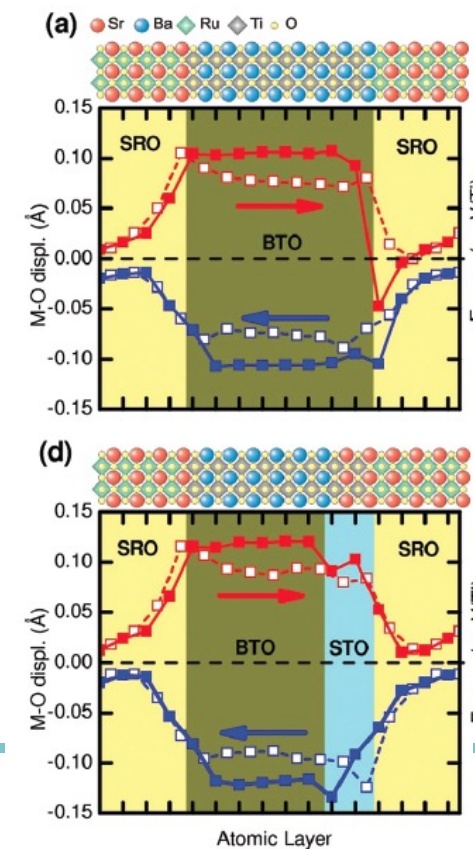
Enhancement of Ferroelectric Polarization Stability by Interface Engineering

2012

Gruverman et al.

Increase of polarization at BaTiO_3 interface by insertion of SrTiO_3 layer

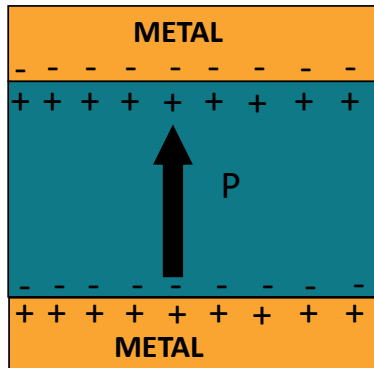
ADVANCED
MATERIALS
www.advmat.de



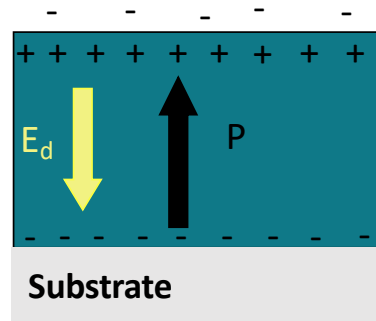
Funded by
the European Union

Depolarization field

FIXIT



Perfect screening
(if perfect metal)



Incomplete charge screening at the interface with a semiconductor or an insulator (or a bad metal)

→ Large effective E_d in thin films

The thinner the film, the larger the depolarization field

The depolarization field changes

- The magnitude of the polarization
- Transition temperature
- Coercive field
- Order of the phase transition

PHYSICAL REVIEW B

VOLUME 8, NUMBER 7

1 OCTOBER 1973

Phase Transition, Stability, and Depolarization Field in Ferroelectric Thin Films

I. P. Batra, P. Wurfel,* and B. D. Silverman
IBM Research Laboratory, San Jose, California 95193



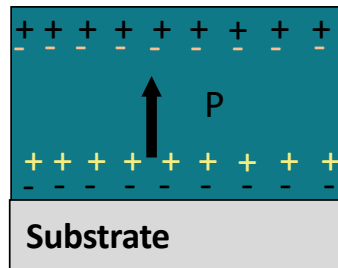
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Depolarization field

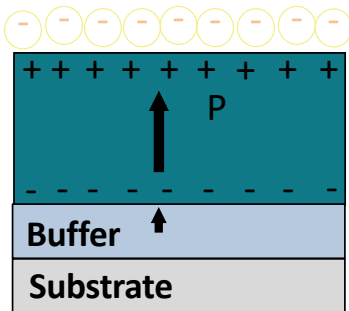
Domain formation

FIXIT

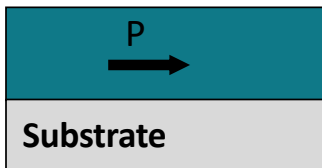
Finite conductivity



Atmospheric adsorbates

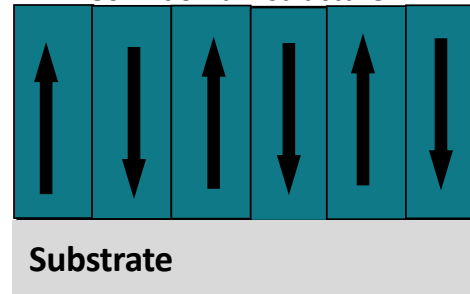


Distortion of lattice for polarization continuity



Polarization rotation

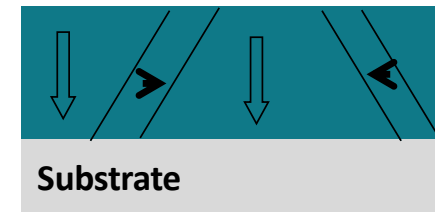
180° domain structure



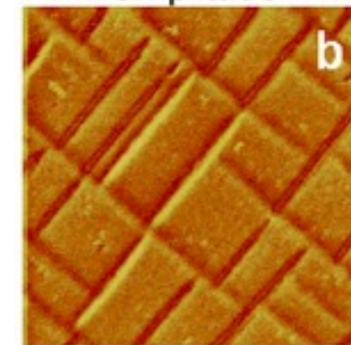
$P = 0$

Substrate

Mixed domain structure



PFM - PZT on $\text{SrTiO}_3\text{:Nb}$



L. Klein, *et al*, JVST A (2010)

Surface screening of spontaneous polarization (bound charges) in ferroelectrics is typically realized by the mobile charges adsorbed from the ambient in the case of high or normal humidity

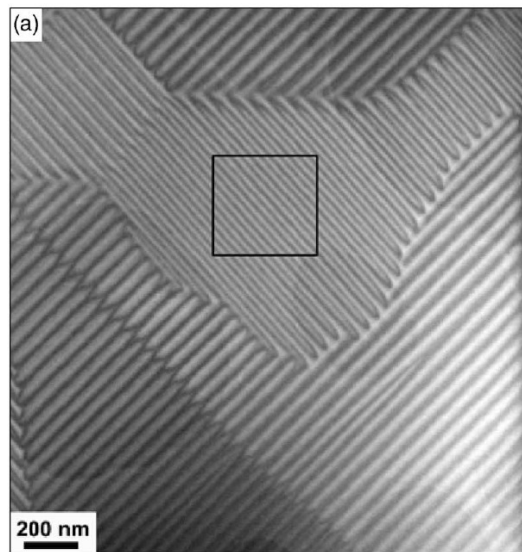


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Domains and domain walls

FIXIT

Single crystalline BaTiO₃ lamella



The domains are **narrow, periodic** and **self-organized**.

Schilling et al, PRB 2006



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Depolarization field

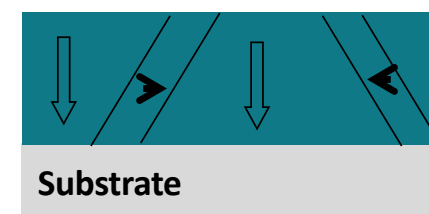
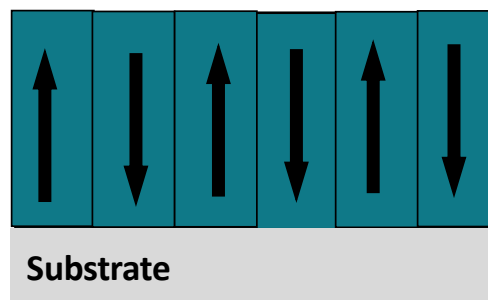
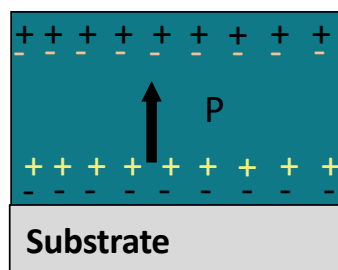
Domain formation

FIXIT

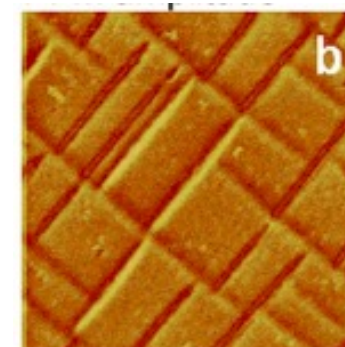
180° domain structure

Mixed domain structure

Finite conductivity

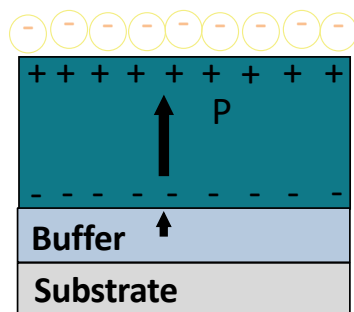


PFM - PZT on SrTiO₃:Nb

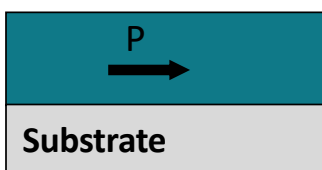


L. Klein, *et al*, JVST A (2010)

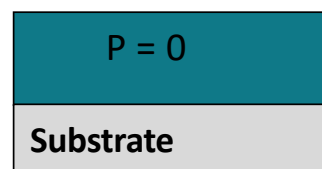
Atmospheric adsorbates



Distortion of lattice for polarization continuity



Polarization rotation



Surface screening of spontaneous polarization (bound charges) in ferroelectrics is typically realized by the mobile charges adsorbed from the ambient in the case of high or normal humidity

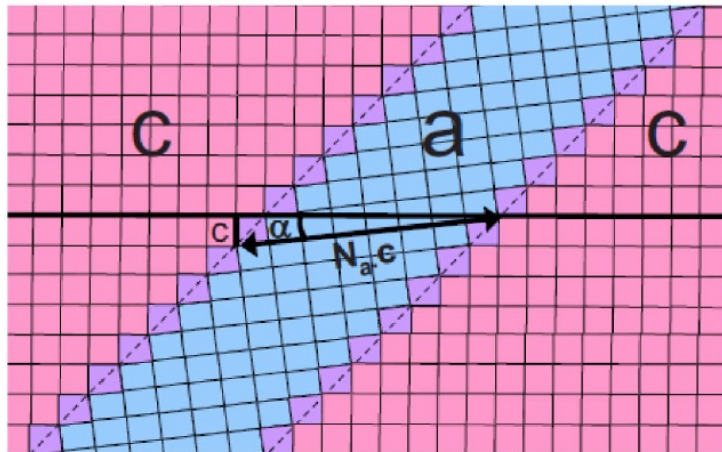


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Domains in ferroelectrics

FIXIT

In an epitaxial tetragonal film: domain width depends on substrate (strain)



P.-E. Janolin, J Mater Sci (2009) 44:5025–5048

B. Noheda

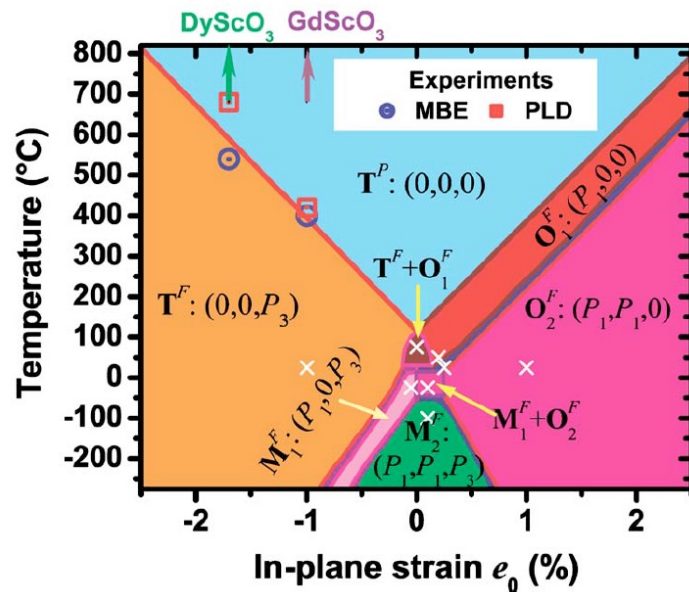


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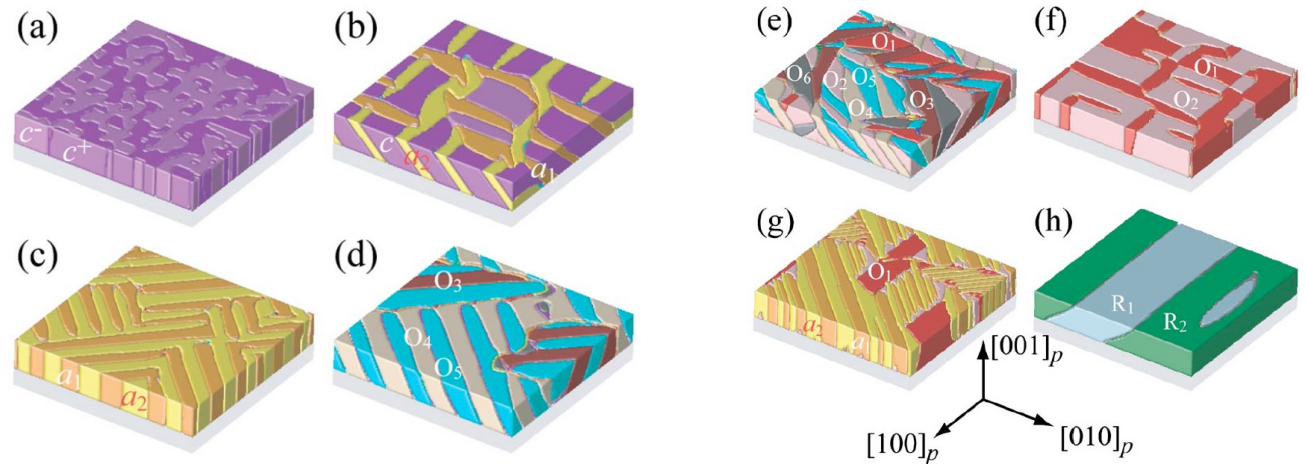
Domains in ferroelectrics

FIXIT

Temperature-strain phase diagram for BaTiO₃



Phase field modelling for the conditions shown on the left



- Rich pattern of possible domain type and configurations

V. G. Koukhar et al., Phys. Rev. B 64, 214103 (2001)

Y. L. Li and L.Q. Chen, Appl. Phys. Lett. 88, 072905 (2006)



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the European Union

Ferroelectrics and strain engineering

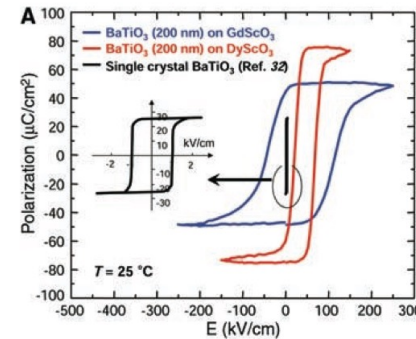
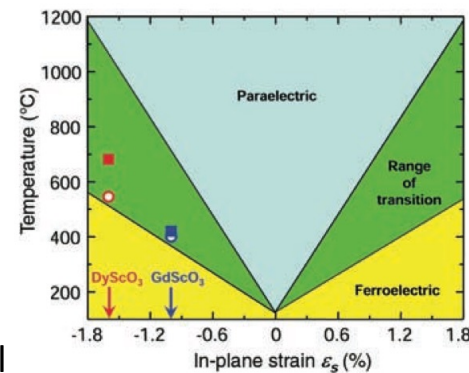
FIXIT

Enhancement of Ferroelectricity in Strained BaTiO_3 Thin Films

K. J. Choi,¹ M. Biegalski,² Y. L. Li,² A. Sharan,² J. Schubert,³
R. Uecker,⁴ P. Reiche,⁴ Y. B. Chen,⁵ X. Q. Pan,⁵ V. Gopalan,²
L.-Q. Chen,² D. G. Schlom,² C. B. Eom^{1*}

Science 306, 1005 (2004)

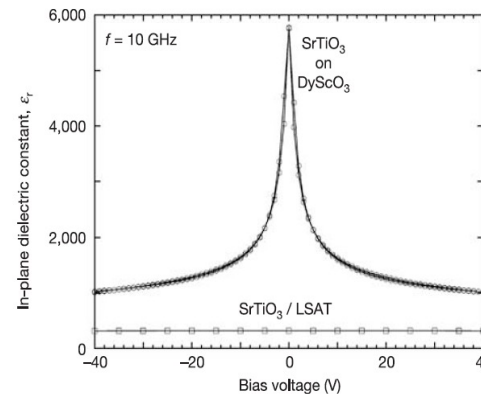
$T_c = 540^\circ \text{C}$ on DyScO_3 !!
(compared to 120°C in bulk crystal)



Room-temperature ferroelectricity in strained SrTiO_3

J. H. Haeni¹, P. Irvin², W. Chang³, R. Uecker⁴, P. Reiche⁴, Y. L. Li¹,
S. Choudhury¹, W. Tian⁵, M. E. Hawley⁶, B. Craig⁷, A. K. Tagantsev⁸,
X. Q. Pan⁵, S. K. Streiffer⁹, L. Q. Chen¹, S. W. Kirchoefer³, J. Levy²
& D. G. Schlom¹

Nature 430, 758 (2004)

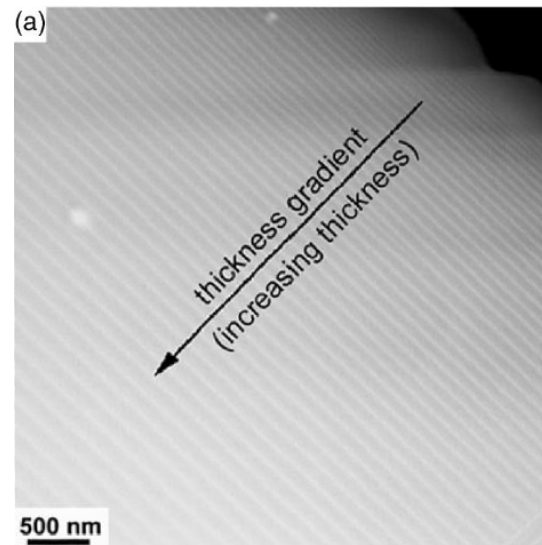
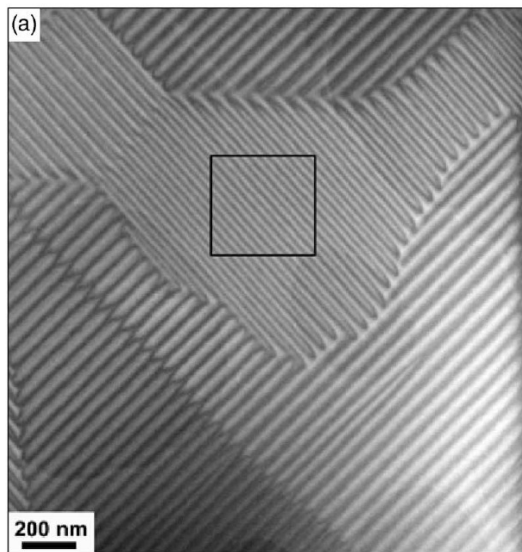


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Domains and domain walls

FIXIT

Single crystalline BaTiO_3 lamella



The domains periodicity increases towards increasing thickness

Schilling et al, PRB 2006



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Domain size: Kittel's law

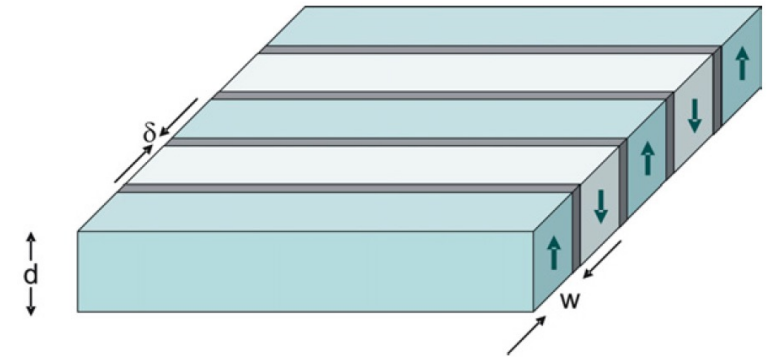
FIXIT

Domain size is determined by the competition between the energy of the domains and the energy of the domain walls

Domain energy : $E = U \cdot w$ U is the volume energy density of the domain

The energy gained by reducing domain size is balanced by the fact that this requires increasing the number of domain walls, which are themselves energetically costly.

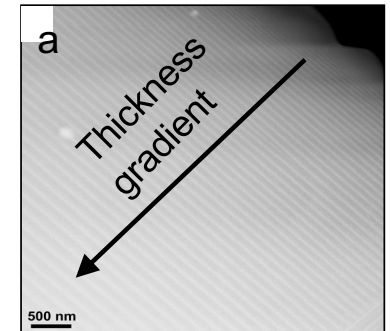
Wall energy : $E = \sigma d/w$, σ is the energy density per unit area of the wall



$$w = \sqrt{\frac{\sigma}{U}} d$$

$$w \sim \sqrt{d}$$

Open boundary conditions



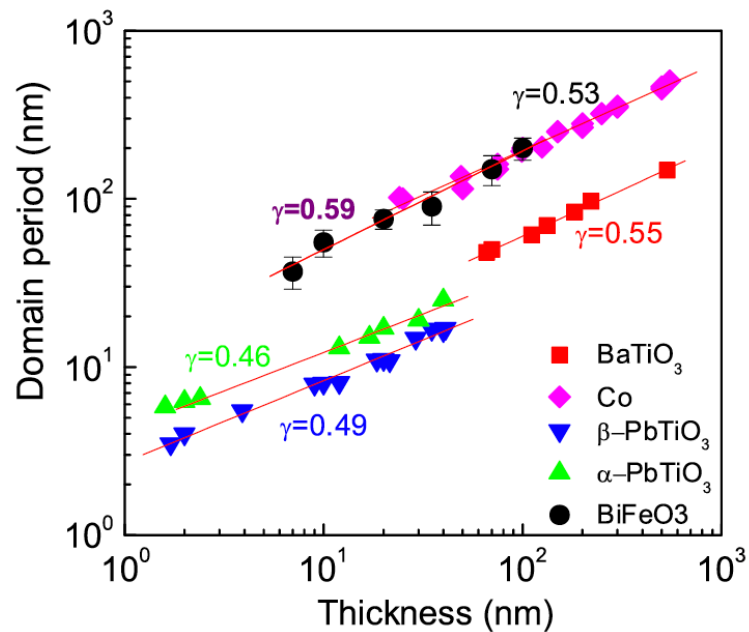
Schilling *et al*, Phys. Rev. B (2006)

J. F. Scott 2006 J. Phys.: Condens. Matter 18 R361
G. Catalan *et al.*, Rev. Modern Phys. 84, 119 (2012)

Landau and Lifshitz (1935)
Kittel (1946)

Domains and domain walls

FIXIT



$$w = A d^\gamma$$

The Kittel's law describe reasonably well the behaviour of ferroelectrics
Ferroelectric domains in BiFeO₃ are large (similar to magnetic domains)

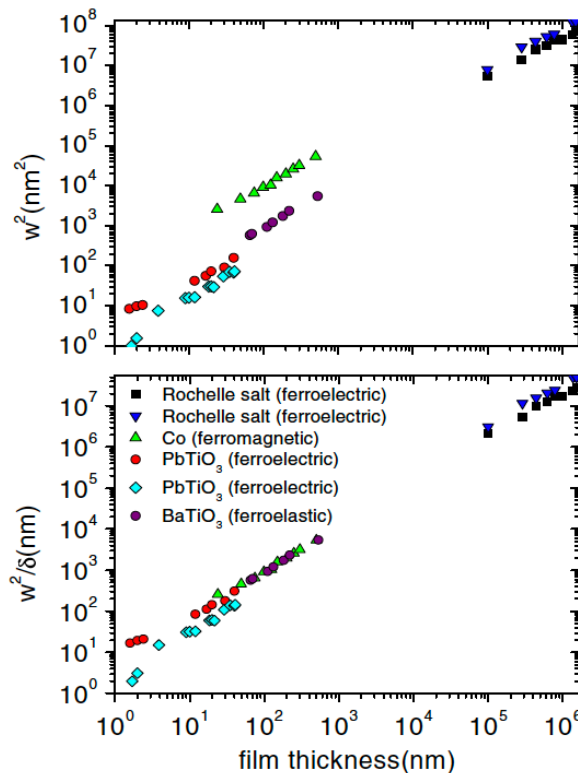
G. Catalan *et al*, Phys. Rev. Lett. 2008



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Domains and domain walls

FIXIT



Open boundary conditions!

$$\frac{w^2}{d\delta} = G \sim 2.5$$

where G is an a-dimensional parameter

- The domain size of **all ferroics** can be described with a **single universal curve** where domain wall thickness is the scaling parameter
- Allows to estimate the wall thickness when domain size is measured (typically, $\delta=1-10\text{nm}$)
- Conversely, one can use it to determine optimum crystal thickness to stabilize a given domain period

For film thickness $d=100\text{nm}$, $\delta/w = 6-20\%$

Very thin films can have a considerable fraction of their volume occupied by domain walls, and therefore the functional properties of the films may be affected by those domain walls.

J. F. Scott 2006 J. Phys.: Condens. Matter 18 R361

G. Catalan et al, J. Phys. Cond. Mat. (2007)

G. Catalan et al, J. Mat. Sci. (2009)

De Guerville, et al. Mater. Sci. Eng. B (2005)

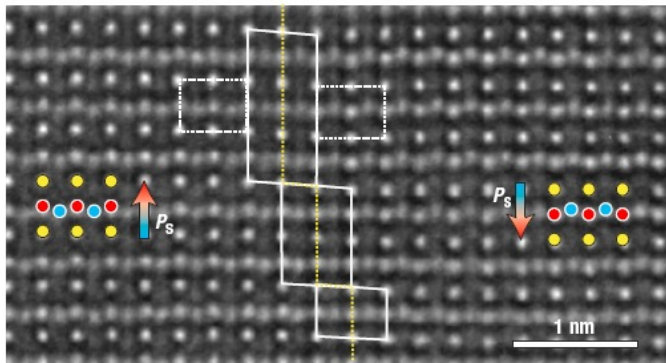


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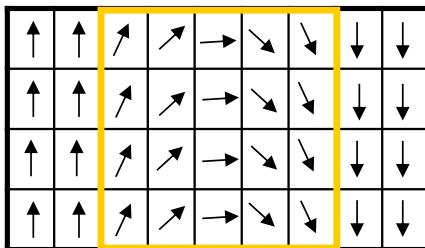
Imaging of domains and domain walls

FIXIT

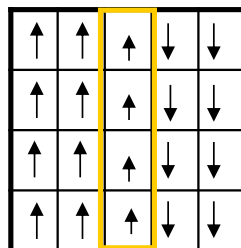
Domain walls are very thin: few unit cells (abrupt change in polarization)



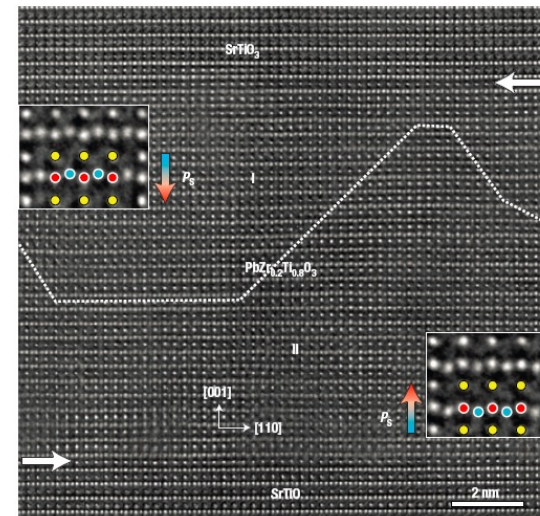
Magnetic domains



Ferroelectric domains



Head-to-head domains → charged domains



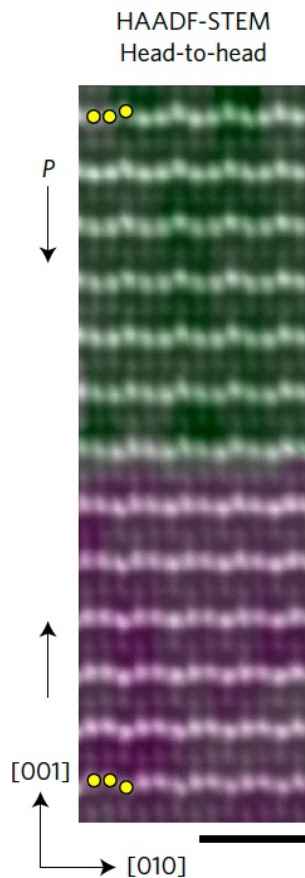
C.-L. Jia *et al*, Nature Materials 7, 57 (2008)



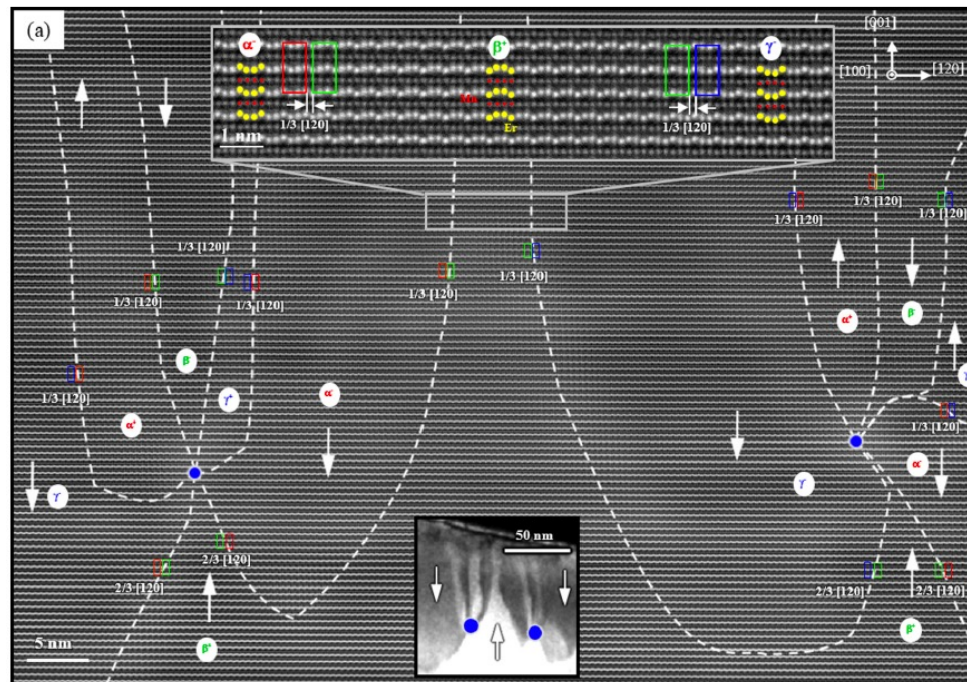
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Imaging of domains and domain walls

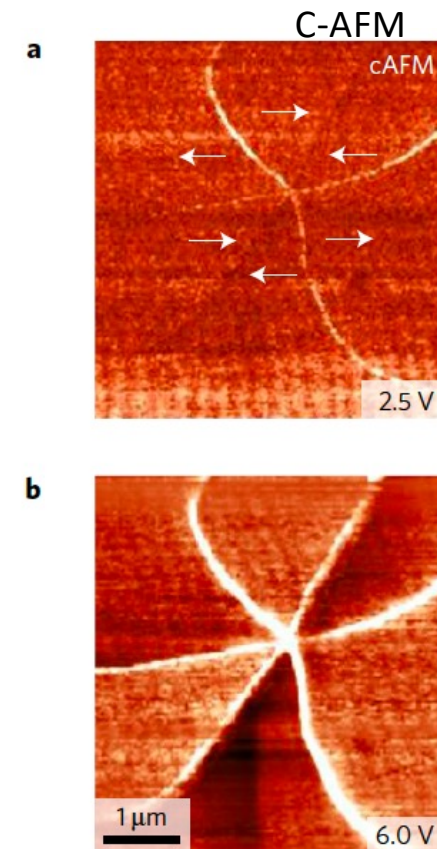
FIXIT



Hexagonal manganites



M.-G. Han *et al*, Phys. Rev. Mater. 2, 064004 (2018)



J.A. Mundy *et al.*, Nat. Mater. 16, 622 (2017)

05.08.24

From: <http://www.princeton.edu/~cavalab/tutorials/public/structures/perovskites.html>



Funded by T. Atsumi, T. Oghushi, N. Kamegashira
the European Union and Compounds 238 (1996) 35

95

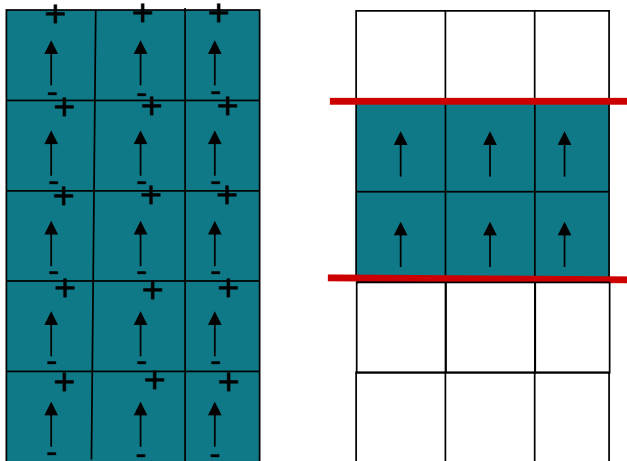
Size: how does it affect ferroelectricity?

FIXIT

Ferroelectricity is a collective effect: balance between short range and dipole-dipole forces

→ expected to be strongly affected by **finite-size effects**.

Ferroelectricity in thin films is closely related to the **boundary conditions** (electrical, mechanical, chemical...)



Questions:

- What is the **critical thickness** for ferroelectricity ?
- Role of the **chemical, electrical and mechanical boundary conditions on ferroelectricity**
(substrate, type of electrodes → screening, depolarization field)



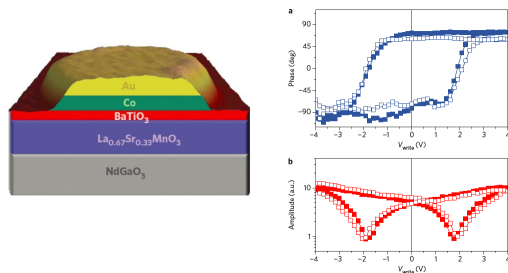
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Size effects

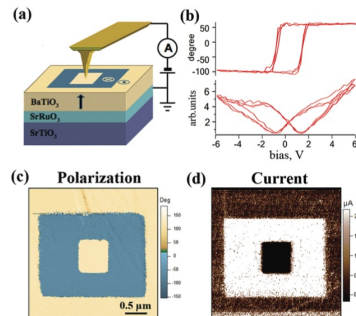
FIXIT

Ferroelectricity in ultrathin films is closely related to the **boundary conditions** (electrical, mechanical...)

BaTiO₃ 20 Å (5 ML) on La_{0.7}Sr_{0.33}MnO₃ electrode

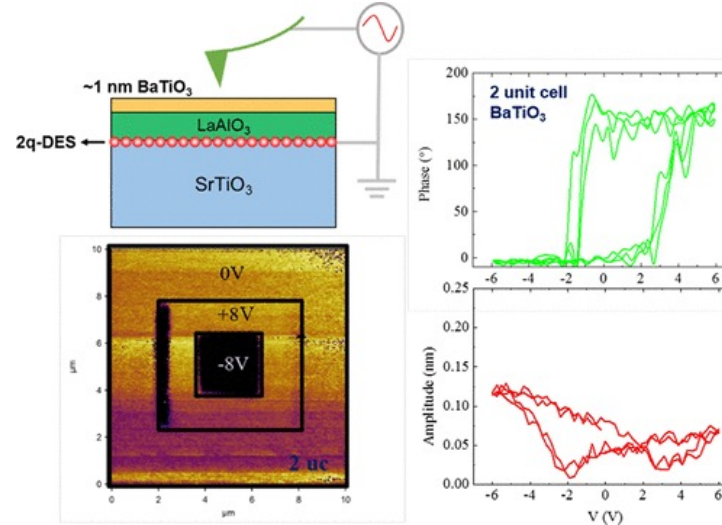


BaTiO₃ 6 ML – 24 ML on SrRuO₃ electrode



Ferroelectricity down to 2 nm

~1 nm ultrathin Semiconducting BaTiO₃ Films



Ferroelectricity down to ~1 nm

V. Garcia *et al.* Nature Materials (2009)

A. Chanthbouala *et al.* Nature Materials (2011)

S.R. Lee *et al.* Nano Lett. 2019, 19, 4, 2243–2250

A. Gruverman *et al.* Nano Letters (2009)

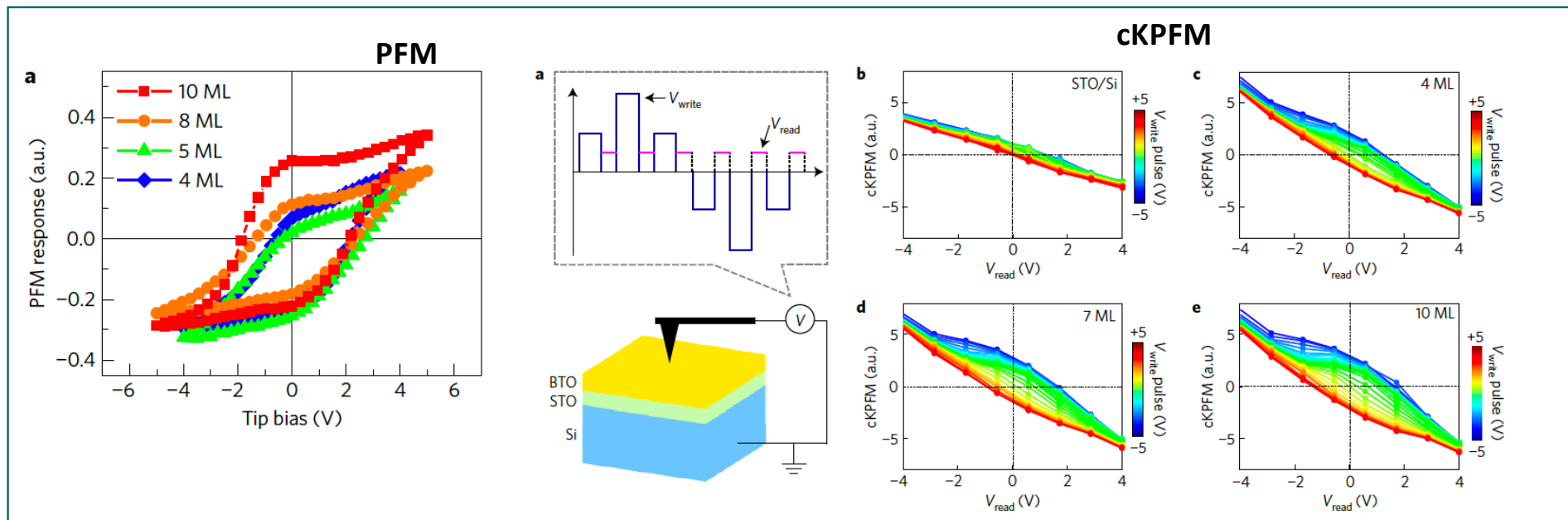


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Size effects

FIXIT

Ultrathin epitaxial BaTiO₃ on epi SrTiO₃ on silicon



Ferroelectricity down to 1.6 nm

Mixed ferro-ionic states for ultrathin films

S. M. Yang *et al.*, Nat. Phys. 13, 812 (2017)

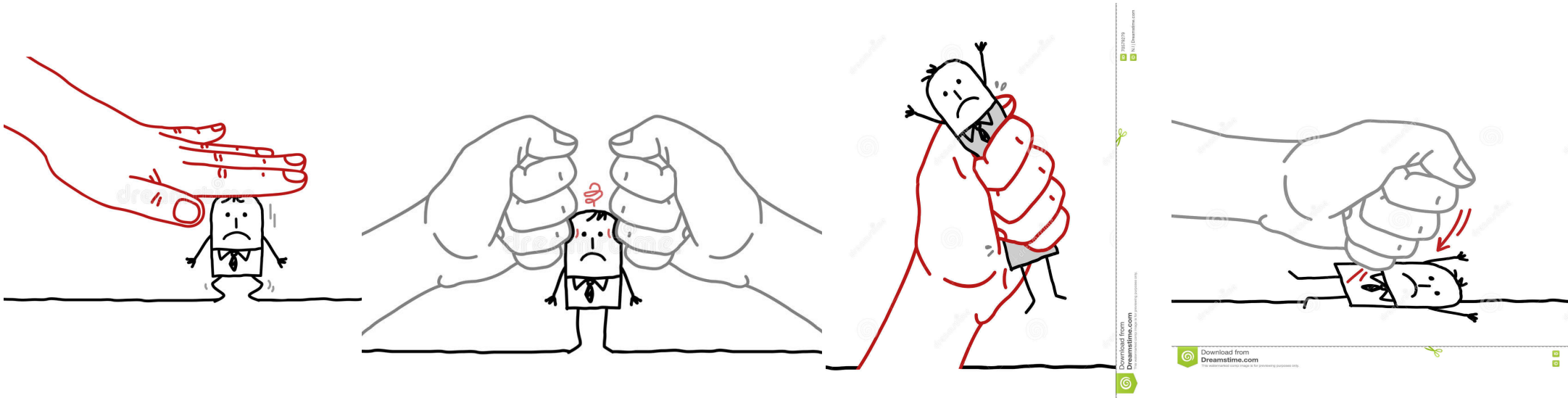


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What happen under confinement?

FIXIT

Confinement means small space and usually a lot of stress: one tends to react differently!

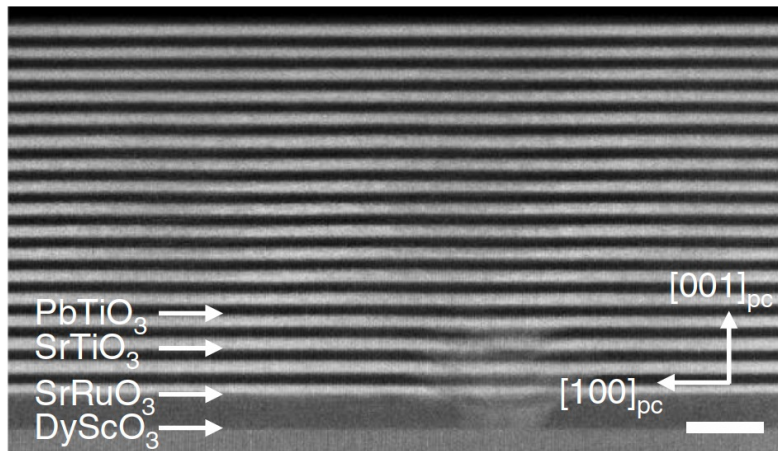


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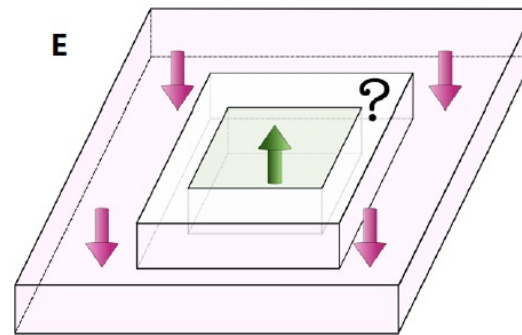
What happen under confinement?

Few nm in size
FIXIT

Ultrathin films in a superlattice



Nanodot embedded in a paraelectric matrix



Domain and domain wall will tend to have similar sizes when domain size decreases down to few nm!

→ Difference between domains and DW may become blurred

The symmetry of domain walls is different from the symmetry of the domains, and hence so are the properties.

→ Emerging properties

S. Das et al., Nature (2019)

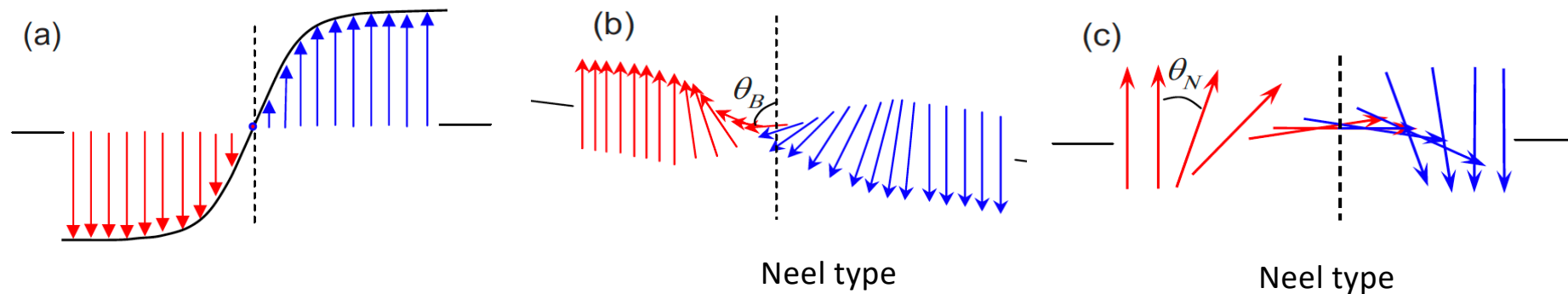
M.A. Peireira Gonçalves et al., Sci. Adv. (2019)



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What happen under confinement?

FIXIT



Exotic polar topological textures appear with rotating electric dipoles, similarly to spins in a magnetic material

It was predicted by modelling for several years and experimental hints were there but it was unambiguously proved in 2011 by STEM images

D. Lee et al, Phys. Rev. B 80, 060102(R) (2009)



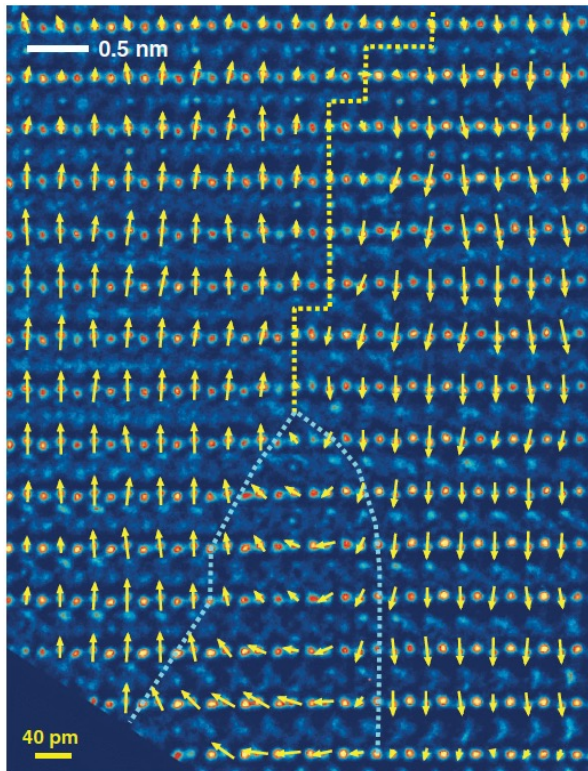
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What happen under confinement?

FIXIT

PZT film

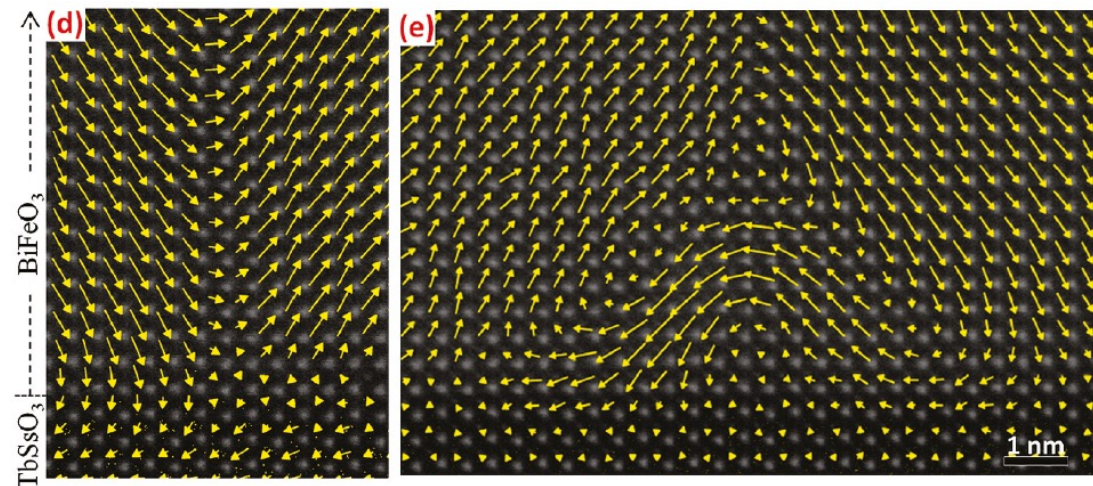
Map of the displacement atomic vectors



Jia et al., Science 331, 1420 (2011)

Continuous rotation of the dipole directions

BiFeO₃ film on TbScO₃



C.T. Nelson et al., Nano Lett., 11, 828 (2011)

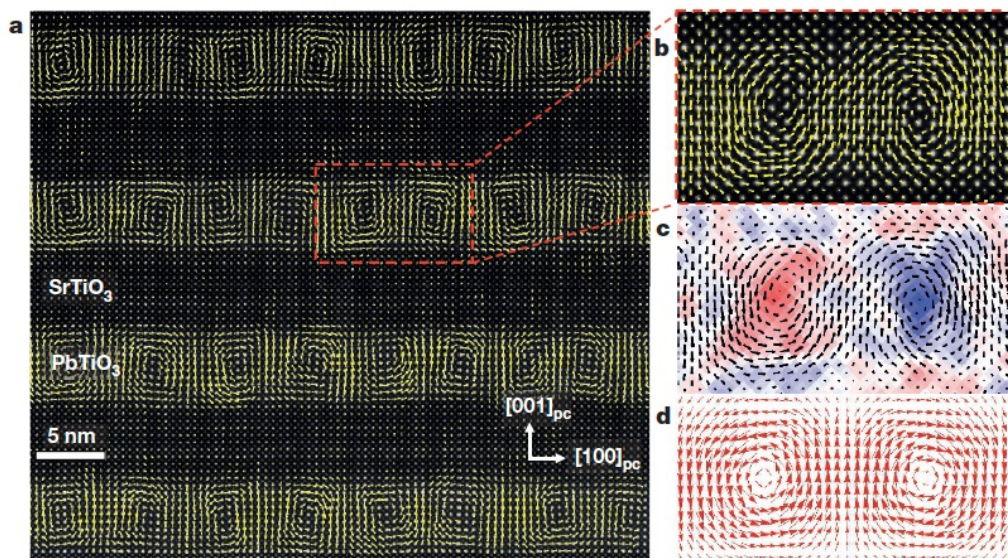


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What happen under confinement?

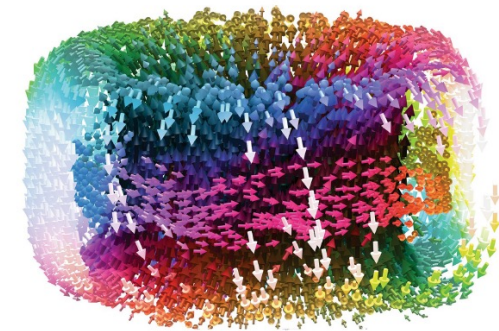
FIXIT

Vortices or skyrmions form in (PZT/SrTiO₃)superlattices depending on the thickness



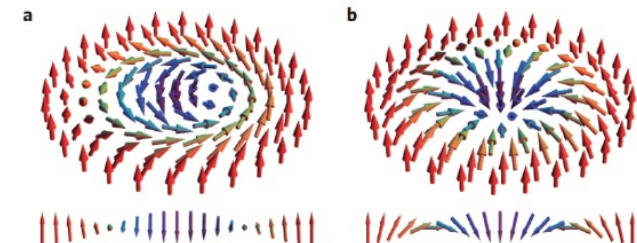
A.K. Yadav et al., Nature (2019)
Nature electronics, 2, 173 (2019)
M.A. Peireira Gonçalves et al., Sci. Adv. (2019)

Polar skyrmions
FERROELECTRIC MATERIALS
Electric skyrmions found
Nature 568, 368–372 (2019)



Credit: Xiaoxing Cheng, Pennsylvania State University; C.T. Nelson, Oak Ridge National Laboratory; and Ramamoorthy Ramesh, Berkeley Lab

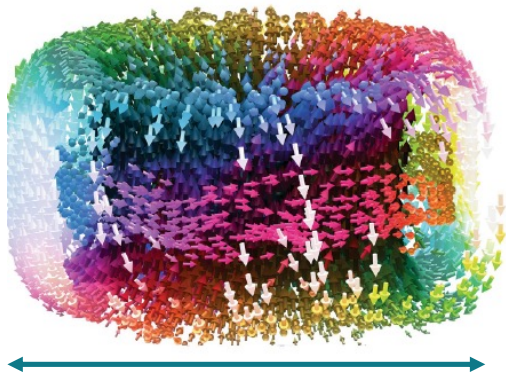
Magnetic skyrmions



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What happen under confinement?

FIXIT



$\sim 10 \text{ nm}$

Polar skyrmions/hopfions are chiral textures (topologically protected)

Is it possible to move them under an electrical field or other excitations?

Can we “write” and „erase“ them at will?

Can such topological textures (or topological defects) be stabilised in ferroelectric HfO_2 ?



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1920 - 2020: 100-year anniversary

2021... exciting time to work on ferroelectrics!

Thank you for your attention